CITATION REPORT
List of articles citing

Candela-class high-brightness InGaN/AlGaN double-heterostructure blue-light-emitting diodes

DOI: 10.1063/1.111832
Applied Physics Letters, 1994, 64, 1687-1689.

Source: https://exaly.com/paper-pdf/25230928/citation-report.pdf
Version: 2024-04-23

#	Paper	IF	Citations
2322	High-brightness green light-emitting diodes. **1994**, 30, 1178-1180		12
2321	Recent developments in SiC-based visible emitters.		1
2320	Comparison of Hydride Vapor Phase Epitaxy of GaN Layers on Cubic GaN/(100)GaAs and Hexagonal GaN/(111)GaAs Substrates. **1994**, 33, 6448-6453		12
2319	High-brightness InGaN/AlGaN double-heterostructure blue-green-light-emitting diodes. **1994**, 76, 8189-8191		364
2318	Design and applications of large area RDRs. **1994**, 7, 12-17		5
2317	Deposition of III-N thin films by molecular beam epitaxy. **1994**, 25, 661-674		11
2316	Reactive ion etching of gallium nitride using hydrogen bromide plasmas. **1994**, 30, 1895-1897		57
2315	ECR plasma etching of GaN, AlN and InN using iodine or bromine chemistries. **1994**, 30, 1985-1986		18
2314	III-V Nitrides For Optical Emitters.		
2313	.		4
2312	A GaN UV Light Emitting Diode.		
2311	.		0
2310	Atomic geometry and electronic structure of native defects in GaN. **1994**, 50, 8067-8070		692
2309	Ain Grown by Metalorganic Molecular Beam Epitaxy. **1994**, 363, 213		
2308	Electronic and Optoelectronic Devices Based on GaN-AlGaN Heterostructures. **1994**, 339, 163		1
2307	Blue ZnSe quantum-well diode laser. **1994**, 30, 2131-2133		24
2306	Electrical Properties of Nichia AlGaN/InGaN/GaN Blue LEDs in a Wide Current/Temperature Range. **1995**, 395, 937		1

(1995-1995)

2305	Light Emission Properties of GaN-Based Double Heterostructures and Quantum Wells. **1995**, 395, 949	2
2304	High Resistivity InAIN by Nitrogen or Oxygen Implantation. **1995**, 378, 485	3
2303	Deep Level Defects in GaN Characterized by Capacitance Transient Spectroscopies. **1995**, 378, 491	5
2302	Atomic Hydrogen in GaN. **1995**, 378, 503	6
2301	Defect Studies in n-Type GaN Grown by Molecular Beam Epitaxy. **1995**, 378, 527	2
2300	Anion Exchange Reactions and initial GaN Epitaxial Layer Formation Under Nitrogen Plasma Exposure of a GaAs Surface. **1995**, 388, 259	2
2299	Thin Film Epitaxial Oxide Optical Waveguides. **1995**, 392, 189	26
2298	Growth Kinetics and Structural Quality in GaN Epitaxy by Low Pressure MOVPE. **1995**, 395, 207	15
2297	AlGaInN Quaternary Alloys by MOCVD. **1995**, 395, 219	3
2296	The Effect of a GaN Nucleation Layer on GaN Film Properties Grown by Metalorganic Chemical Vapor Deposition. **1995**, 395, 231	9
2295	Halide Vapor Phase Epitaxy of Gallium Nitride Films on Sapphire and Silicon Substrates. **1995**, 395, 243	34
2294	Structural Defects in Heteroepitaxial and Homoepitaxial GaN. **1995**, 395, 351	34
2293	Lattice-Matching Growth of InGaAIN Systems. **1995**, 395, 39	9
2292	Strain Effects in GaN on Sapphire: Towards a Quantitative Comprehension. **1995**, 395, 411	13
2291	Electronic Structure of a Nitrogen Vacancy in Cubic Gallium Nitride. **1995**, 395, 509	
2290	Properties of GaN Epitaxial Layer Grown by MOVPE on MgAl2O4 Substrate. **1995**, 395, 61	
2289	Light Generating Carrier Recombination and Impurities in Wurtzite GaN/Al2O3 Grown by MOCVD. **1995**, 395, 633	29
2288	Theory of Point Defects and Complexes in GaN. **1995**, 395, 645	60

2287	Spin-Dependent Transport in GaN Light Emitting Diodes. **1995**, 395, 657	3
2286	Magnetic Resonance Studies of Recombination Processes in GaN-Based Light Emitting Diodes. **1995**, 395, 673	
2285	Plasma Chemistry Dependent ECR Etching of GaN. **1995**, 395, 751	12
2284	Ion Implantation Doping and High Temperature Annealing of GaN. **1995**, 395, 801	3
2283	Fabrication and Properties of AlGaN/GaInN Double Heterostructure Grown on 6H-SiC(0001)Si. **1995**, 395, 869	2
2282	Room-Temperature Life Test of Nichia AlGaN/InGaN/GaN Blue Light Emitting Diodes. **1995**, 395, 931	3
2281	Fabrication of Novel III-N and III-V Modulator Structures by ECR Plasma Etching. **1995**, 405, 115	
2280	InGaN Light-Emitting Diodes with Quantum-Well Structures. **1995**, 395, 879	5
2279	Light-Emitting Devices Based on Gallium Nitride and Related Compound Semiconductors. **1995**, 395, 889	21
2278	. **1995**, 11, 19-23	15
2277	The InGaAlN System as a Competitor of ZnSe. **1995**, 187, 471-476	
2276	Dry etching and implantation characteristics of III-N alloys. **1995**, 31, 309-317	14
2275	Metal-organic chemical vapor deposition growth of GaN. **1995**, 29, 58-60	3
2274	Auger investigation of group III nitride films grown by molecular beam epitaxy. **1995**, 146, 340-343	13
2273	GaN based IIIV nitrides by molecular beam epitaxy. **1995**, 150, 887-891	34
2272	The growth and properties of group III nitrides. **1995**, 150, 892-896	60
2271	Effects of V/III supply ratio on improvement of crystal quality of zincblende GaN grown by gas source molecular beam epitaxy using RF-radical nitrogen source. **1995**, 150, 897-901	10
2270	Molecular beam epitaxy of gallium nitride by electron cyclotron resonance plasma and hydrogen azide. **1995**, 150, 912-915	19

(1995-1995)

2269	Implantation and redistribution of dopants and isolation species in GaN and related compounds. **1995**, 38, 1329-1333	42
2268	Chemically assisted ion beam etching of gallium nitride. **1995**, 24, 229-234	27
2267	The growth and properties of mixed group V nitrides. **1995**, 24, 263-268	27
2266	Basic studies of gallium nitride growth on sapphire by metalorganic chemical vapor deposition and optical properties of deposited layers. **1995**, 24, 1531-1534	48
2265	The Strain Energy Densities of Hexagonal and Tetragonal Epitaxial Media. **1995**, 34, L1616-L1619	5
2264	High-Efficiency ZnCdSe/ZnSSe/ZnMgSSe Green Light-Emitting Diodes. **1995**, 2, 167-170	12
2263	Optical characterization of GaN films by photoreflectance and photocurrent measurement. **1995**, 78, 7424-7426	8
2262	Degradation of blue AlGaN/InGaN/GaN LEDs subjected to high current pulses. **1995**,	8
2261	Novel compound semiconductor devices based on III-V nitrides.	
2260	Identification of the 1.19-eV luminescence in hexagonal GaN. **1995**, 52, 16508-16515	30
2259	Study of Schottky barriers on n-type GaN grown by LP-MOCVD.	
2258	Crystal Structure and Orientation of AlxIn$_{{bf 1}-ninmb{x}}$N Epitaxial Layers Grown on (0001) mbAl$_{bf 2}$O$_{bf 3}$ Substrates. **1995**, 34, 4653-4657	21
2257	Stimulated Emission by Current Injection from an AlGaN/GaN/GaInN Quantum Well Device. **1995**, 34, L1517	132
2256	AlN-GaN quarter-wave reflector stack grown by gas-source MBE on (100) GaAs. **1995**, 31, 68-69	42
2255	Hydrogen incorporation in GaN, AlN, and InN during Cl2/CH4/H2/Ar ECR plasma etching. **1995**, 31, 836-837	23
2254	Short period superlattice II-VI blue light emitting diodes. **1995**, 31, 1015-1016	4
2253	Acceptor binding energy in GaN and related alloys. **1995**, 10, 101-104	62
2252	Direct Patterning of the Current Confinement Structure for p-Type Column-III Nitrides by Low-Energy Electron Beam Irradiation Treatment. **1995**, 34, 1190-1193	14

2251	Growth and Optical Properties of GaN Grown by MBE on Novel Lattice-Matched Oxide Substrates. **1995**, 395, 535	26
2250	Electronic structure and phase stability of GaAs1-xNx alloys. **1995**, 51, 10568-10571	251
2249	MgO/SiO/sub 2/ dielectric multilayer reflectors for GaN-based ultra-violet surface emitting lasers.	
2248	High-Brightness InGaN Blue, Green and Yellow Light-Emitting Diodes with Quantum Well Structures. **1995**, 34, L797-L799	1270
2247	. **1995**, 83, 1306-1355	472
2246	Light emitting diode-based nanosecond ultraviolet light source for fluorescence lifetime measurements. **1995**, 66, 5469-5472	61
2245	Polarized Raman spectra in GaN. **1995**, 7, L129-L133	233
2244	High-luminosity blue and blue-green gallium nitride light-emitting diodes. **1995**, 267, 51-5	341
2243	Hydrogen in GaN: Novel aspects of a common impurity. **1995**, 75, 4452-4455	390
2242	Optically detected magnetic resonance of GaN films grown by organometallic chemical-vapor deposition. **1995**, 51, 13326-13336	294
2241	Band gap of GaN films grown by molecular-beam epitaxy on GaAs and GaP substrates. **1995**, 78, 1838-1842	28
2240	Impurity-related photoluminescence from InGaN LED material.	
2239	Threshold characteristics of blue to ultraviolet light emitting semiconductor lasers based on the AlGaN material system.	
2238	On degradation of ZnSe-based blue-green diode lasers. **1995**, 77, 4150-4152	33
2237	Growth and characterization of InGaN/GaN double heterostructure LEDs grown by MOCVD.	
2236	Superbright Green InGaN Single-Quantum-Well-Structure Light-Emitting Diodes. **1995**, 34, L1332-L1335	780
2235	. **1995**, 1, 784-791	49
2234	III-V nitride-based light-emitting diodes. **1996**, 5, 496-500	25

2233	Optical properties of wurtzite GaN grown by low-pressure metalorganic chemical-vapor deposition. **1996**, 79, 3691-3696	43
2232	Growth of Group III Nitrides. A Review of Precursors and Techniques. **1996**, 8, 9-25	258
2231	N incorporation in InP and band gap bowing of InNxP1. **1996**, 80, 1934-1936	93
2230	Oscillator strengths for optical band-to-band processes in GaN epilayers. **1996**, 54, 7678-7681	76
2229	Single quantum well light emitting diodes demonstrated as excitation sources for nanosecond phase-modulation fluorescence lifetime measurements. **1996**, 67, 3795-3798	60
2228	Formation Energies and Electronic Structures of Native Defects in GaN. **1996**, 13, 867-869	4
2227	Thermal stability of W ohmic contacts to n-type GaN. **1996**, 80, 278-281	106
2226	Nanostructured GaN: Microstructure and optical properties. **1996**, 54, 17763-17767	10
2225	Problems and prospects in the analysis of epitaxial growth of the wide bandgap Group-III nitrides. **1996**, 6, 113-122	
2224	Shortest wavelength semiconductor laser diode. **1996**, 32, 1105	407
2223	Physical properties of GaAs on glass. **1996**, 62, 237-240	1
2222	Modeling of optical gain in InGaN-AlGaN and In/sub x/Ga/sub 1-x/N-In/sub y/Ga/sub 1-y/N quantum-well lasers. **1996**, 32, 859-864	20
2221	Excitonic emissions from hexagonal GaN epitaxial layers. **1996**, 79, 2784-2786	149
2220	Free and bound excitons in thin wurtzite GaN layers on sapphire. **1996**, 11, 712-716	98
2219	Recent progress in quantum structure materials, physics and devices. **1996**, 1, 17-20	
2218	Magneto-optical studies of GaN and GaN/AlxGa1N: Donor Zeeman spectroscopy and two dimensional electron gas cyclotron resonance. **1996**, 79, 8007-8010	102
2217	Theory of GaN(101-bar0) and (112-bar0) surfaces. **1996**, 53, R10477-R10480	309
2216	Experimental analysis of room-temperature optical gain in GaInN-GaN and GaN-AlGaN double heterostructures and quantum wells.	2

2215	Photoluminescence studies of band-edge transitions in GaN epitaxial layers grown by plasma-assisted molecular beam epitaxy. **1996**, 79, 2675-2683	50
2214	A Light Emitting Diode Improves Evanescent Excitation of a Fiber Optic Cocaine Biosensor. **1996**, 29, 29-33	7
2213	Recent progress of crystal growth, conductivity control and light emitters of group III nitride semiconductors.	4
2212	Strain effect on electronic and optical properties of GaN/AlGaN quantum-well lasers. **1996**, 80, 6868-6874	73
2211	The Morphology and Cathodoluminescence of GaN Thin Films. **1996**, 1, 1	12
2210	Recent developments in visible light sources. **1996**, 354, 779-791	5
2209	Identification of a Cubic Phase in Epitaxial Layers of Predominantly Hexagonal GaN. **1996**, 1, 1	10
2208	Microstructure, growth mechanisms and electro-optical properties of heteroepitaxial GaN layers on sapphire (0001) substrates. **1996**, 1, 1	25
2207	Luminescence Spectra Of Superbright Blue and Green InGaN/AlGaN/GaN Light-Emitting Diodes. **1996**, 1, 1	34
2206	Growth of Epitaxial Gan Films Using ZnO Buffer Layer by Pulsed Laser Deposition. **1996**, 421, 389	6
2205	Growth of High Quality (In,Ga,Al)N/GaN Heterostructure Materials and Devices by Atmospheric Pressure MOCVD. **1996**, 423, 23	1
2204	Electronic Structure of Beryllium, Magnesium and Silicon Impurity in Cubic Gallium Nitride. **1996**, 423, 631	
2203	Progress and future prospects of group III nitride semiconductors.	
2202	Strain Effects on Optical Gain Properties of GaN/AlGaN Quantum Well Lasers. **1996**, 421, 171	
2201	Studies of Degradation in Nichia AlGaN/InGaN/GaN Blue Light Emitting Diodes Under Close to Normal Operating Conditions. **1996**, 421, 183	1
2200	Characterization of Er-Doped IIIV Nitride Epilayers Prepared by MOMBE. **1996**, 422, 193	9
2199	Dry Etch Damage in InN, InGaN and InAlN. **1996**, 423, 163	1
2198	Optical Spectroscopy of Dry-Etched GaN-Nanostructures. **1996**, 423, 169	

2197	P- and N-Type Implantation Doping of GaN with Ca and O. **1996**, 423, 189	
2196	Gallium Nitride Thick Films Grown by Hydride Vapor Phase Epitaxy. **1996**, 423, 221	26
2195	TEM and PL characterisation of MBE-grown epitaxial GaN/GaAs. **1996**, 423, 311	10
2194	GaN Growth by Nitrogen ECR-CVD Method. **1996**, 423, 377	
2193	Theoretical Prediction of Zinc Blende Phase GaN Avalanche Photodiode Performance Based on Numerically Calculated Electron and Hole Impact Ionization Rate Ratio. **1996**, 423, 45	6
2192	Effect of Si Doping on the Structure of GaN. **1996**, 423, 487	15
2191	Photoreflectance Study of Gan Film Grown by Metalorganic Chemical Vapor Deposition. **1996**, 423, 735	
2190	Optical Characterization of GaN Films Grown on (0001) Sapphire Substrate. **1996**, 423, 747	1
2189	Patterning of LiGaO2 and LiAlO2 by Wet and Dry Etching. **1996**, 449, 1041	6
2188	Structural and Optical Properties of Nitride-Based Heterostructure and Quantum-Well Structure. **1996**, 449, 1143	38
2187	Design Consideration of GaN-Based Surface Emitting Lasers. **1996**, 449, 1151	4
2186	Realization and Characterization of Optically Pumped GaInN-DFB Lasers. **1996**, 449, 1197	1
2185	High Quality Photoconductive Ultraviolet GaN/6H-SiC Detector and Its Properties. **1996**, 449, 1215	1
2184	Growth of Cubic GaN by MBE and Its Properties. **1996**, 449, 173	1
2183	MBE Growth of IIIV Nitride Films and Quantum-Well Structures Using Multiple RF Plasma Sources. **1996**, 449, 271	9
2182	Metalorganic vapor phase epitaxial growth of GaInN/GaN hetero structures and quantum wells. **1996**, 449, 3	21
2181	Nano-Tubes in GaN. **1996**, 449, 417	22
2180	STM Observation of Nitrided-Ga on Si. **1996**, 449, 447	2

2179	Spontaneous and Stimulated Recombination in the Nitrides. **1996**, 449, 641	3
2178	Effect of the Nitridation of the Sapphire (0001) Substrate on the GaN Growth. **1996**, 449, 67	3
2177	Magnetic Resonance Studies of GaN-Based Single Quantum Well Leds. **1996**, 449, 757	2
2176	Optical Dielectric Response of Gallium Nitride Studied by Variable Angle Spectroscopic Ellipsometry. **1996**, 449, 805	5
2175	Relaxations at GaN (101 0) and (110) Surfaces. **1996**, 449, 953	3
2174	Chlorine-Based Plasma Etching of GaN. **1996**, 449, 969	30
2173	.	1
2172	The Growth of InGaN/(Al)GaN Quantum Well Structures in a Multi-Wafer High Speed Rotating Disk Reactor. **1996**, 1, 1	2
2171	k. **1996**, 54, 2491-2504	819
2170	MBE growth and properties of ZnO on sapphire and SiC substrates. **1996**, 25, 855-862	183
2169	Structural characterization of bulk GaN crystals grown under high hydrostatic pressure. **1996**, 25, 1545-1550	77
2168	MBE growth and properties of GaN and AlxGa1�N on GaN/SiC substrates. **1996**, 25, 793-797	12
2167	Residual impurities in GaN/Al2O3 grown by metalorganic vapor phase epitaxy. **1996**, 25, 799-803	38
2166	Ion implantation and rapid thermal processing of Ill-V nitrides. **1996**, 25, 839-844	41
2165	Magnetic resonance studies of GaN based light emitting diodes. **1996**, 25, 851-854	2
2164	The formation and microstructures of Si-based blue-light emitting porous �SiC. **1996**, 119, 505-509	6
2163	InGaAlN and II�VI Systems for Blue�Green Light-Emitting Devices. **1996**, 8, 469-479	73
2162	InGaN-based blue/green LEDs and laser diodes. **1996**, 8, 689-692	31

2161	Raman determination of phonon deformation potentials in □GaN. **1996**, 100, 207-210	164
2160	Growth and fabrication of GaN?InGaN microdisk laser structures. **1996**, 39, 311-313	8
2159	Optical and electrical characterization of GaN layers grown on silicon and sapphire substrates. **1996** , 40, 81-84	2
2158	Optical phonons in GaN. **1996**, 219-220, 493-495	53
2157	Process development for III□V nitrides. **1996**, 38, 138-146	5
2156	Optical properties of indium nitride in vacuum ultraviolet region. **1996**, 79, 9-12	13
2155	Microwave plasma assisted LCVD growth and characterization of GaN. **1996**, 100-101, 643-646	8
2154	Growth and characterization of GaN layers on SiC substrates. **1996**, 166, 601-606	8
2153	Growth mechanisms in excimer laser photolytic deposition of gallium nitride at 500□C. **1996**, 160, 201-206	16
2152	Model calculations for n-CdZnS light emitter grown on p-GaN hole injector. **1996**, 159, 502-505	7
2151	Growth study of chemical beam epitaxy of GaNxP1 □x using NH3 and tertiarybutylphosphine. **1996**, 164, 180-184	4
2150	III-N light emitting diodes fabricated using RF nitrogen gas source MBE. **1996**, 164, 154-158	12
2149	The microstructure of gallium nitride monocrystals grown at high pressure. **1996**, 169, 235-242	47
2148	Progress and prospects of group-III nitride semiconductors. **1996**, 20, 361-525	414
2147	Yellow Luminescence and Hydrocarbon Contamination in MOVPE-Grown GaN. **1996**, 158, 587-597	15
2146	Phase Fluorometric Optical Carbon Dioxide Gas Sensor for Fermentation Off-Gas Monitoring. **1996**, 12, 266-271	31
2145	R&D of compound semiconductor materials in Japan energy. **1996**, 27, xv-xx	
2144	Structural and Optical Characterization of High-Quality Cubic GaN Epilayers Grown on GaAs and 3C□SiC Substrates by Gas-Source MBE Using RHEED In Situ Monitoring. **1996**, 449, 435	10

2143	Applications of Electron Microscopy in Collaborative Industrial Research. **1996**, 21, 17-23	5
2142	Application of Electroceramic Thin Films to Optical Waveguide Devices. **1996**, 21, 53-58	27
2141	Native defects and impurities in GaN. **1996**, 25-44	43
2140	Evidence for Shallow Acceptor Levels in MBE Grown GaN. **1996**, 1, 1	17
2139	Photoreflectance Study of GaN Films on Sapphire Substrate. **1996**, 13, 153-156	4
2138	Directly modulated diode laser frequency doubled in a KTP waveguide as an excitation source for CO2 and O2 phase fluorometric sensors. **1996**, 1, 124-30	7
2137	Composition and structure of the GaN{0001-bar}-(1 x 1) surface. **1996**, 54, 14652-14663	56
2136	Coloring and Bleaching Reactions of Photochromic Molecules by using a Single GaN-based Light Emitting Diode. **1996**, 35, L1532-L1534	9
2135	Comparative Raman studies of cubic and hexagonal GaN epitaxial layers. **1996**, 79, 4137	78
2134	Reactive molecular beam epitaxy of wurtzite GaN: Materials characteristics and growth kinetics. **1996**, 79, 7657-7666	79
2133	Epitaxial growth and optical transitions of cubic GaN films. **1996**, 54, R8381-R8384	135
2132	Characteristics of light-emitting diodes based on GaN p-n junctions grown by plasma-assisted molecular beam epitaxy. **1996**, 79, 2779-2783	58
2131	Structural properties of cubic GaN epitaxial layers grown on SiC. **1996**, 80, 6322-6328	8
2130	Numerical simulation of wide band-gap AlGaN/InGaN light-emitting diodes for output power characteristics and emission spectra. **1996**, 79, 2755-2761	13
2129	Optical properties of GaN epilayers on sapphire. **1996**, 80, 5352-5360	125
2128	Inversion Domain and Stacking Mismatch Boundaries in GaN. **1996**, 77, 103-106	217
2127	Growth of High-Quality AlN and AlN/GaN/AlN Heterostructure on Sapphire Substrate. **1996**, 35, L1013-L1015	46
2126	Full-Color Fluorescent Display Devices Using a Near-UV Light-Emitting Diode. **1996**, 35, L838-L839	129

2125	First-Principles Calculations on Mg Impurity and Mg-H Complex in GaN. **1996**, 35, L807-L809		33
2124	Biexciton Luminescence from GaN Epitaxial Layers. **1996**, 35, L787-L789		36
2123	Reduction of Threshold Current Density of Wurtzite GaN/AlGaN Quantum Well Lasers by Uniaxial Strain in (0001) Plane. **1996**, 35, L953-L955		40
2122	Physics and Device Science in II-VI Semiconductor Visible Light Emitters. **1996**, 49, 205-286		7
2121	Effect of strain on GaN exciton spectra. **1996**, 11, 1026-1029		23
2120	Photocurrent Studies of Ultraviolet Detector Based on Gallium Nitride Epilayer. **1996**, 13, 874-877		4
2119	Characterisation of Pd Schottky barrier on n-type GaN. **1996**, 32, 68		47
2118	Low-temperature luminescence study of GaN films grown by MBE. **1996**, 11, 366-371		42
2117	Photoluminescence Properties of GaN Grown under Ion Flux Reduced Condition by Plasma Enhanced Molecular Beam Epitaxy. **1996**, 35, L644-L647		11
2116	Transmission Electron Microscopy of Sublimation-Grown GaN Single Crystal and GaN Homoepitaxial Film. **1996**, 35, L1318-L1320		3
2115	Exciton spectra and spin - orbit splitting in GaN epitaxial films. **1997**, 12, 64-68		6
2114	Effects of Dissolved Oxygen on Anodic Etching of n-Type GaN Films Using a Sodium Hydroxide Electrolyte. **1997**, 36, L955-L958		9
2113	Yellow luminescence in n-type GaN epitaxial films. **1997**, 56, 6942-6946		107
2112	Electrical and structural analysis of high-dose Si implantation in GaN. *Applied Physics Letters*, **1997**, 70, 2729-2731	3.4	97
2111	Internal structure and oscillator strengths of excitons in strained □GaN. **1997**, 55, 2530-2534		72
2110	Surface morphology and optical characterization of GaN grown on □Al2O3 (0001) by radio-frequency-assisted molecular beam epitaxy. *Applied Physics Letters*, **1997**, 70, 3023-3025	3.4	4
2109	Compositional inhomogeneity and immiscibility of a GaInN ternary alloy. *Applied Physics Letters*, **1997**, 71, 906-908	3.4	90
2108	Energy-gap narrowing in a current injected InGaN/AlGaN surface light emitting diode. *Applied Physics Letters*, **1997**, 71, 2424-2426	3.4	15

2107	Persistent photoconductivity in n-type GaN. **1997**, 82, 899-901		105
2106	GaN and AlxGa1⊠N molecular beam epitaxy monitored by reflection high-energy electron diffraction. *Applied Physics Letters*, **1997**, 71, 1816-1818	3.4	100
2105	Temperature dependence of the energies and broadening parameters of the interband excitonic transitions in wurtzite GaN. **1997**, 55, 9251-9254		85
2104	Study of surface-emitted stimulated emission in GaN. *Applied Physics Letters*, **1997**, 71, 729-731	3.4	18
2103	Surface composition and structure of GaN epilayers on sapphire. **1997**, 107, 9577-9584		24
2102	Influence of defects on the electrical and optical characteristics of blue light-emitting diodes based on III⊠V nitrides. **1997**, 81, 2442-2444		64
2101	The process and efficiency of ultraviolet generation from gallium nitride blue light emitting diodes. *Applied Physics Letters*, **1997**, 71, 1385-1387	3.4	12
2100	Optical anisotropy of excitons in strained GaN epilayers grown along the <101□0> direction. **1997**, 56, 12446-12453		50
2099	Photoluminescence decay dynamics in an InGaN/GaN/AlGaN single quantum well. **1997**, 81, 1005-1007		6
2098	Study of open-core dislocations in GaN films on (0001) sapphire. *Applied Physics Letters*, **1997**, 70, 2434-2436	3.4	53
2097	Characteristics of InGaN/AlGaN light-emitting diodes on sapphire substrates. **1997**, 82, 5816-5821		51
2096	On the incorporation of Mg and the role of oxygen, silicon, and hydrogen in GaN prepared by reactive molecular beam epitaxy. **1997**, 82, 219-226		109
2095	The Evolution of Nitride Semiconductors. **1997**, 482, 103		28
2094	GaN and Related Materials for Device Applications. **1997**, 22, 17-21		59
2093	Implantation and Dry Etching of Group-III-Nitride Semiconductors. **1997**, 22, 36-43		53
2092	Defects and Interfaces in GaN Epitaxy. **1997**, 22, 51-57		74
2091	Blue-Green Light-Emitting Diodes and Violet Laser Diodes. **1997**, 22, 29-35		146
2090	AlGaN-Based Bragg Reflectors. **1997**, 2, 1		34

[1997-1997]

2089	Reactive Molecular-Beam Epitaxy for Wurtzite GaN. **1997**, 22, 22-28	8
2088	Growth models of GaN thin films based on crystal chemistry: hexagonal and cubic GaN on Si substrates. **1997**, 2999, 288	2
2087	The Composition Pulling Effect in MOVPE Grown InGaN on GaN and AlGaN and its TEM Characterization. **1997**, 2, 1	132
2086	Materials Chemistry and Bulk Crystal Growth of Group III Nitrides in Supercritical Ammonia. **1997**, 495, 367	19
2085	Brillouin scattering study of gallium nitride: elastic stiffness constants. **1997**, 9, 241-248	87
2084	Chapter 8 Group 111-V Nitride-Based Ultraviolet Blue-Green-Yellow Light-Emitting Diodes and Laser Diodes. **1997**, 391-443	7
2083	P-Type GaN Directly Grown by Low Pressure Metalorganic Vapor Phase Epitaxy. **1997**, 14, 637-640	2
2082	Metalorganic Vapor Phase Epitaxy Growth of a High-Quality GaN/InGaN Single Quantum Well Structure Using a Misoriented SiC Substrate. **1997**, 36, 1961-1965	5
2081	Metalorganic Vapor Phase Epitaxy of Thick InGaN on Sapphire Substrate. **1997**, 36, 3381-3384	41
2080	Initial Stages of Cubic GaN Growth on the GaAs(001) Surface Studied by Scanning Tunneling Microscopy. **1997**, 36, L1486-L1489	18
2079	Comparison of Electron and Hole Initiated Impact Ionization in Zincblende and Wurtzite Phase Gallium Nitride. **1997**, 468, 457	8
2078	Electrical and Optical Properties of InGaN/AlGaN Double Heterostructure Blue Light-Emitting Diodes. **1997**, 468, 469	
2077	The First Nitride Laser Diode on Silicon Carbide. **1997**, 482, 1139	3
2076	Resonant Raman Scattering in GaN/Al0.15 Ga0.85N and InyGa1-yN/GaN/AlxGa1-xN Heterostructures. **1997**, 468, 213	12
2075	Complete Characterization of AlxGa1-xN/InxGa1-xN/GaN Devices by Sims. **1997**, 468, 281	
2074	Characterisation of AlxGa1-xN Films Prepared by Plasma Induced Molecular Beam Epitaxy on C-Plane Sapphire. **1997**, 468, 305	
2073	Patterning of GaN in High-Density Cl2- and BCl3-Based Plasmas. **1997**, 468, 355	15
2072	Valence Band Physics in Wurtzite GaN. **1997**, 468, 445	1

2071	MOCVD Growth of High Output Power Ingan Multiple Quantum Well Light Emitting Diode. **1997**, 468, 481	10
2070	Quasi-Thermodynamic Analysis of Metalorganic Vapor Phase Epitaxy of GaN. **1997**, 468, 81	2
2069	A Kinetic Model for GaN Growth. **1997**, 482, 253	5
2068	Selective Area Growth of GaN by MOVPE and HVPE. **1997**, 482, 334	15
2067	Structural and Optical Properties of Group III-Nitride Quantum Wells Studied by (S)Tem and CL. **1997**, 482, 416	3
2066	The Effect of Si and Mg Doping in the Microstructure of Epitaxially Grown GaN. **1997**, 482, 440	3
2065	Transmission Electron Microscopy Study of Room Temperature Lasing Epitaxial ZnO Films on Sapphire. **1997**, 482, 481	4
2064	Low-Angle and High-Angle Grain Boundaries in AIN/GaN Layers Grown on (0001) Sapphire by MBE. **1997**, 482, 493	2
2063	Effects of Piezoelectric Fields in GaInN/GaN and GaN/AlGaN Heterostructures and Quantum Wells. **1997**, 482, 557	25
2062	The Effect of Low Temperature GaAs Nucleation on the Growth of GaN on Silicon (001) During MOVPE Process. **1997**, 482, 169	
2061	InGaN Quantum Dots Fabricated on AlGaN Surfaces-Growth Mechanism and Optical Properties-. **1997**, 482, 760	
2060	Doping, Activation of Impurities, and Defect Annihilation in GaN by High Pressure Annealing. **1997**, 482, 946	6
2059	Comparison of Dry-Etch Techniques for GaN, InN, and AlN. **1997**, 483, 103	
2058	Chapter 2 Metalorganic Chemical Vapor Deposition (MOCVD) of Group III Nitrides. **1997**, 50, 11-37	11
2057	Chapter 14 Applications of LEDs and LDs. **1997**, 50, 431-457	5
2056	Determination of the local microstructure of epitaxial AlN by x-ray absorption. **1997**, 82, 1166-1171	18
2055	MOVPE growth optimization of high quality InGaN films.. **1997**, 2, 1	28
2054	Chapter 5 Etching of III Nitrides. **1997**, 103-126	6

2053	Chapter 6 Indium-based Nitride Compounds. **1997**, 127-166		1
2052	CVPE growth of GaN films.		1
2051	ECR-MBE growth and high excitation properties of GaInN/GaN heterostructures. **1997**,		
2050	Implant activation and redistribution of dopants in GaN.		2
2049	Non-thermionic cathodes-solid state electron emitters based on GaN and LaB/sub 6/.		1
2048	Many-body effects on optical gain in strained hexagonal and cubic GaN/AlGaN quantum well lasers. *Applied Physics Letters*, **1997**, 71, 398-400	3.4	20
2047	Growth of High-Quality AlN, GaN and AlGaN with Atomically Smooth Surfaces on Sapphire Substrates. **1997**, 36, L1565-L1567		45
2046	Single crystal growth of SiC and electronic devices. **1997**, 22, 111-197		30
2045	Structural and optical analysis of epitaxial GaN on sapphire. **1997**, 12, 637-644		7
2044	Identification of the cubic and hexagonal polytypes of GaN with X-ray absorption measurements. **1997**, 6, 1539-1541		1
2043	Gas source molecular beam epitaxy of wurtzite GaN on sapphire substrates using GaN buffer layers. *Applied Physics Letters*, **1997**, 71, 240-242	3.4	76
2042	Long range order in AlxGa1□N films grown by molecular beam epitaxy. *Applied Physics Letters*, **1997**, 71, 72-74	3.4	113
2041	Effect of hydrogen on the indium incorporation in InGaN epitaxial films. *Applied Physics Letters*, **1997**, 70, 461-463	3.4	118
2040	Raman and photoluminescence studies of biaxial strain in GaN epitaxial layers grown on 6H□iC. **1997**, 82, 5097-5102		315
2039	Radiative carrier lifetime, momentum matrix element, and hole effective mass in GaN. *Applied Physics Letters*, **1997**, 70, 631-633	3.4	180
2038	Optical constants of epitaxial AlGaN films and their temperature dependence. **1997**, 82, 5090-5096		477
2037	Chapter 1 Materials Issues in High-Brightness Light-Emitting Diodes. **1997**, 1-45		15
2036	Chapter 2 Overview of Device Issues in High-Brightness Light-Emitting Diodes. **1997**, 47-63		12

2035	Chapter 7 Organometallic Vapor-Phase Epitaxy of Gallium Nitride for High-Brightness Blue Light-Emitting Diodes. **1997**, 357-390		8
2034	A band-structure model of strained quantum-well wurtzite semiconductors. **1997**, 12, 252-263		231
2033	Impurity dependence on hydrogen and ammonia flow rates in InGaN bulk films. *Applied Physics Letters*, **1997**, 71, 2023-2025	3.4	27
2032	Hybrid organic□inorganic semiconductor-based light-emitting diodes. **1997**, 82, 4126-4128		40
2031	Stimulated emission at 34 K from an optically pumped cubic GaN/AlGaN heterostructure grown by metalorganic vapor-phase epitaxy. *Applied Physics Letters*, **1997**, 71, 812-814	3.4	28
2030	High-brightness AlGaInP light emitting diodes. **1997**, 85, 1752-1764		39
2029	Determination of the Al mole fraction and the band gap bowing of epitaxial AlxGa1□N films. *Applied Physics Letters*, **1997**, 71, 1504-1506	3.4	257
2028	An ultraviolet nanosecond light pulse generator using a light emitting diode for test of photodetectors. **1997**, 68, 1365-1368		18
2027	Resonant Raman scattering in GaN/(AlGa)N single quantum wells. *Applied Physics Letters*, **1997**, 70, 363-365	3.4	66
2026	Bowing parameter of the band-gap energy of GaNxAs1□. *Applied Physics Letters*, **1997**, 70, 1608-1610	3.4	352
2025	Biaxial strain dependence of exciton resonance energies in wurtzite GaN. **1997**, 81, 417-424		215
2024	Life tests and failure mechanisms of GaN/AlGaN/InGaN light emitting diodes.		3
2023	Effects of surface treatments and metal work functions on electrical properties at p-GaN/metal interfaces. **1997**, 81, 1315-1322		196
2022	Low Resistance Contacts to P-Type GaN. **1997**, 468, 427		37
2021	Gallium-nitride-based materials for blue to ultraviolet optoelectronics devices. **1997**, 85, 1740-1749		76
2020	Fluorescence characteristics of Cu-ZSM-5 zeolites in reactive gas mixtures: mechanisms for a fiber-optic-based gas sensor. **1997**, 36, 3699-707		7
2019	Investigation of the Indium Atom Interdiffusion on the Growth of GaN/InGaN Heterostructures. **1997**, 36, 1728-1732		4
2018	Optical gain in optically pumped cubic GaN at room temperature. *Applied Physics Letters*, **1997**, 70, 1076-1077	3.4	34

2017	Stimulated emission at 300 K from photopumped GaN grown by plasma-assisted molecular beam epitaxy with an inductively coupled plasma source. *Applied Physics Letters*, **1997**, 70, 811-813	3.4	12
2016	Properties of GaN epitaxial layer grown on (111) MgAl2O4 substrate. **1997**, 41, 251-254		3
2015	Well-width dependent studies of InGaN-GaN single-quantum wells using time-resolved photoluminescence techniques. **1997**, 3, 731-738		15
2014	Reconstructions of the GaN(0001□) Surface. **1997**, 79, 3934-3937		309
2013	Optical Properties of Strained AlGaN and GaInN on GaN. **1997**, 36, L177-L179		293
2012	Wide bandgap light-emitting devices materials and doping problems. **1997**, 30, 131-135		17
2011	GaN based LED□ with different recombination zones. **1997**, 2, 1		13
2010	Characterization of Chemically Vapor Deposited GaN on Sic on a Simox Substrate. **1997**, 3, 487-488		
2009	Optical Fiber Components and Devices. **1997**, 267-318		2
2008	Evolution of the microstructure of oxide thin films. **1997**, 170, 799-802		28
2007	The influence of strain and mosaic structure on electrical and optical properties of GaN films on sapphire substrates. **1997**, 170, 367-371		2
2006	N incorporation in GaNxP1 □x and InNxP1 □x using a RF N plasma source. **1997**, 175-176, 145-149		10
2005	Group IVB refractory metal crystals as lattice-matched substrates for growth of the group III nitrides by plasma-source molecular beam epitaxy. **1997**, 178, 189-200		10
2004	Characteristics of InxGa1 □xN/GaN grown by LPMOVPE with the variation of growth temperature. **1997**, 182, 6-10		15
2003	InGaN quantum-well structure blue LEDs and LDs. **1997**, 72-74, 55-58		3
2002	Nitride-based semiconductors for blue and green light-emitting devices. **1997**, 386, 351-359		1389
2001	Physical properties of bulk single-crystal wafers of gallium nitride. **1997**, 39, 763-765		4
2000	Dependence of the injection current at lasing threshold on structure and losses in AlGaN/GaN lasers. **1997**, 44, 197-200		1

1999	Studies on nitridation of laser evaporated IIIV group elements with gaseous ammonia and thin film deposition. **1997**, 122, 415-419	13
1998	High dose Si- and Mg-implantation in GaN: Electrical and structural analysis. **1997**, 127-128, 467-470	21
1997	IIIV Nitride semiconductors for high-performance blue and green light-emitting devices. **1997**, 49, 18-23	28
1996	Nanometer-scale studies of nitride/arsenide heterostructures produced by nitrogen plasma exposure of GaAs. **1997**, 26, 1342-1348	3
1995	Tunneling current and electroluminescence in InGaN: Zn,Si/AlGaN/GaN blue light emitting diodes. **1997**, 26, 311-319	34
1994	Growth of zinc- blende GaN on GaAs (100) substrates at high temperature using low-pressure MOVPE with a Low V/lll molar ratio. **1997**, 26, 320-324	45
1993	Ion implantation doping of OMCVD grown GaN. **1997**, 26, 334-339	12
1992	Spectra of superbright blue and green InGaN/AlGaN/GaN light-emitting diodes. **1997**, 17, 2033-2037	9
1991	Metalorganic vapour phase epitaxy of GaN and GaInN/GaN heterostructures and quantum wells. **1997**, 35, 243-262	13
1990	Theoretical investigation of new MgS-ZnSe structures. **1997**, 43, 79-82	
1989	First laser diodes fabricated from IIIV nitride based materials. **1997**, 43, 258-264	25
1988	Optical gain in the nitrides: are there differences to other IIIV semiconductors?. **1997**, 43, 201-206	6
1987	GaN thin films produced by pulsed laser deposition. **1997**, 48, 239-243	11
1986	Optical properties of GaN epilayers grown on Si (111) and Si (001) substrates. **1997**, 50, 113-116	4
1985	Cathodoluminescence study of crystalline quality of (Al, In, Ga)N heterostructures. **1997**, 50, 245-250	2
1984	GaN thin films deposited by pulsed laser ablation in nitrogen and ammonia reactive atmospheres. **1997**, 50, 20-24	14
1983	Present and future aspects of blue light emitting devices. **1997**, 113-114, 689-697	6
1982	Dependence of electrical properties on work functions of metals contacting to p-type GaN. **1997**, 117-118, 373-379	30

1981	Estimation of the degradation of InGaN/AlGaN blue light-emitting diodes. **1997**, 37, 1239-1241	36
1980	Surface deformation of the InGaN thin films deposited on a sapphire substrate. **1997**, 295, 193-198	13
1979	MBE growth and characteristics of cubic GaN. **1997**, 306, 231-236	11
1978	III▯V nitride based light-emitting devices. **1997**, 102, 237-248	196
1977	Raman study of the optical phonons in AlxGa1▯xN alloys. **1997**, 104, 35-39	58
1976	Effects of isochronal thermal annealing and hydrogenation on photoluminescence from n-type GaN films grown by metalorganic vapor phase epitaxy. **1997**, 104, 143-146	
1975	Low pressure metalorganic vapor phase epitaxial growth of GaN/GaInN heterostructures. **1997**, 41, 141-144	30
1974	Morphology of twinned GaN grown on (11▯0) sapphire substrates. **1997**, 41, 227-229	5
1973	Stimulated emission from rectangular cross-sectional GaN optical waveguides by photo-pumping and stripe design of optical waveguides formed with a selectively grown buried heterostructure. **1997**, 41, 255-261	4
1972	GaN epitaxial growth on neodium gallate substrates. **1997**, 41, 263-266	21
1971	Photoconductive decay in LCVD/PECVD low temperature grown GaN. **1997**, 41, 279-281	2
1970	Influence of the molar ratio on the structural and electronic properties of MOVPE grown GaN. **1997** , 41, 315-317	25
1969	Electroluminescence from carbazole dimers. **1997**, 9, 1158-1161	66
1968	Photochemical Vapor Deposition of Wide Bandgap III-V Materials: Influence of Photochemically Generated Radicals on the Growth of Aluminum Nitride and Gallium Nitride Films. **1997**, 3, 209-217	6
1967	Study of GaN and InGaN films grown by metalorganic chemical vapour deposition. **1997**, 170, 344-348	32
1966	Microstructural characterisation of GaN(As) films grown on (001) GaP by molecular beam epitaxy. **1997**, 171, 321-332	26
1965	Optical and structural properties of GaN films grown on c-plane Al 2 O 3 by electron cyclotron resonance molecular beam epitaxy. **1997**, 173, 260-265	12
1964	Progress and prospect of group-III nitride semiconductors. **1997**, 175-176, 29-36	23

1963	Plasma-excited organometallic vapor phase epitaxy of GaN on (0 0 0 1)sapphire. **1997**, 173, 237-243	15
1962	Microstructure of GaN epitaxial films at different stages of the growth process on sapphire (0 0 0 1). **1997**, 173, 249-259	56
1961	GaN epitaxial growth on sapphire (0 0 0 1): the role of the substrate nitridation. **1997**, 178, 220-228	40
1960	Ion implantation in group III-nitride semiconductors: a tool for doping and defect studies. **1997**, 178, 157-167	65
1959	Growth and characterization of cubic GaN. **1997**, 178, 113-133	164
1958	Some properties of gallium nitride films grown on (0 0 0 1) oriented sapphire substrates by gas source molecular beam epitaxy. **1997**, 180, 27-33	5
1957	Influence of magnesium doping on the structural properties of GaN layers. **1997**, 181, 197-203	26
1956	Effect of growth temperature on the properties of p-type GaN grown by plasma-assisted molecular beam epitaxy. **1997**, 182, 241-246	8
1955	Hydride vapour phase epitaxy of GaN on molecular beam epitaxial GaN substrates. **1998**, 187, 29-34	6
1954	Growth characteristics of GaInN on (0 0 0 1)sapphire by plasma-excited organometallic vapor phase epitaxy. **1998**, 187, 178-184	3
1953	The formation of crystalline defects and crystal growth mechanism in InxGa1⊠N/GaN heterostructure grown by metalorganic vapor phase epitaxy. **1998**, 189-190, 24-28	55
1952	Hydride vapor-phase epitaxy growth of high-quality GaN bulk single crystal by epitaxial lateral overgrowth. **1998**, 189-190, 67-71	39
1951	Growth of hexagonal GaN thin films on Si(111) with cubic SiC buffer layers. **1998**, 189-190, 183-188	25
1950	The study of piezoelectric effect in wurtzite GaN/InGaN/AlGaN multilayer structures. **1998**, 189-190, 648-651	11
1949	MOVPE growth of GaN and LED on (111) MgAl2O4. **1998**, 189-190, 197-201	2
1948	Dislocation generation in GaN heteroepitaxy. **1998**, 189-190, 231-243	236
1947	Initial growth of GaN on sapphire(0001) using an amorphous buffer layer formed at room temperature by RF-MBE. **1998**, 189-190, 275-281	10
1946	Evaluation of nanopipes in MOCVD grown (0001) GaN/Al2O3 by wet chemical etching. **1998**, 191, 275-278	53

1945	Gallium diffusion through cubic GaN films grown on GaAs(1 0 0) at high-temperature using low-pressure MOVPE. **1998**, 191, 646-650	1
1944	Progress in crystal growth and future prospects of group III nitrides by metalorganic vapor-phase epitaxy. **1998**, 195, 248-251	9
1943	Study of the epitaxial lateral-overgrowth (ELO) process for GaN on sapphire. **1998**, 195, 333-339	22
1942	Growth and characterization of GaN on LiGaO2. **1998**, 195, 304-308	18
1941	Growth and characterization of (La,Sr)(Al,Ta)O3 single crystals as substrates for GaN epitaxial growth. **1998**, 194, 209-213	27
1940	Growth and applications of Group III-nitrides. **1998**, 31, 2653-2710	1113
1939	Current-voltage characteristics of GaN and AlGaN p-i-n diodes. **1998**, 32, 335-338	4
1938	Electric and photoelectric properties of n-GaxIn1 N/p-Si anisotypic heterojunctions. **1998**, 32, 412-416	7
1937	Substrate nitridation effect and low temperature growth of GaN on sapphire (0 0 0 1) by plasma-excited organometallic vapor-phase epitaxy. **1998**, 183, 62-68	20
1936	Properties of GaN epilayers with various growth conditions grown by gas source molecular beam epitaxy. **1998**, 191, 34-38	
1935	Magnetic resonance studies of GaN-based LEDs. **1998**, 189-190, 794-797	2
1934	MOCVD of BN and GaN thin films on silicon: new attempt of GaN growth with BN buffer layer. **1998** , 189-190, 439-444	52
1933	Characteristics of Mg-doped GaN epilayers grown with the variation of Mg incorporation. **1998**, 193, 300-304	20
1932	LiAlO2 single crystal: a novel substrate for GaN epitaxy. **1998**, 193, 127-132	60
1931	Synthesis, Structure, and Magnetic Properties of Sr39Co12N31. **1998**, 141, 1-9	25
1930	Correlation of microstructure with electrical behavior of Ti/GaN schottky contacts. **1998**, 27, 1236-1239	5
1929	High selectivity plasma etching of InN over GaN. **1998**, 27, 915-917	7
1928	Optical properties and recombination mechanisms in GaN and GaN:Mg grown by metalorganic vapor phase epitaxy. **1998**, 27, 222-228	10

1927	Growth and characterisation of GaN epitaxial layers. **1998**, 50, 211-214		2
1926	Highly excited luminescence in InGaN epitaxial films: Origins of the blue-green emission. **1998**, 76-77, 242-245		
1925	Effect of pressure on exciton energies of homoepitaxial GaN. **1998**, 108, 433-438		21
1924	Dependence on Al concentration of the optical phonons of AlxGa1N films. **1998**, 108, 765-768		10
1923	Deep traps in high resistivity AlGaN films. **1998**, 42, 831-838		56
1922	Comparison of plasma etch techniques for IIIV nitrides. **1998**, 42, 2259-2267		36
1921	Room temperature ultraviolet laser emission from ZnO nanocrystal thin films grown by laser MBE. **1998**, 54, 24-28		110
1920	The electron mobility and compensation in n-type GaN. **1998**, 13, 310-313		20
1919	Gallium nitride based materials and their application for light emitting devices. **1998**, 3, 45-50		7
1918	Photoluminescence study of nano-crystalline GaN and AlN grown by reactive sputtering. **1998**, 227-230, 1096-1100		21
1917	The interaction of Ga and N on SiC and LiGaO2 surfaces studied by synchrotron radiation photoemission. **1998**, 402-404, 87-91		4
1916	First-principles calculation of electron surface states of the zinc-blende GaN(110) surface. **1998**, 405, 54-61		11
1915	Wurtzite GaN-based heterostructures by molecular beam epitaxy. **1998**, 4, 537-549		31
1914	Reduction of Etch Pit Density in Organometallic Vapor Phase Epitaxy-Grown GaN on Sapphire by Insertion of a Low-Temperature-Deposited Buffer Layer between High-Temperature-Grown GaN. **1998**, 37, L316-L318		170
1913	Thermal stability of W and WSix contacts on p-GaN. *Applied Physics Letters*, **1998**, 73, 942-944	3.4	42
1912	Growth of wurtzite GaN films on /spl alpha/-Al/sub 2/O/sub 3/ substrates using light radiation heating metal-organic chemical vapor deposition.		1
1911	Ohmic contacts formed by electrodeposition and physical vapor deposition on p-GaN. *Applied Physics Letters*, **1998**, 73, 3402-3404	3.4	14
1910	Doping of group III nitrides. **1998**, 16, 1609-1614		58

1909	Study of electrical and optical properties of InGaN/AlGaN double heterostructure blue light emitting diodes.		
1908	Unexpected band-gap collapse in quaternary alloys at the group-III-nitride/GaAs interface: GaAlAsN. **1998**, 57, 3753-3756		9
1907	Study of flicker noise in III-V nitride based heterojunctions due to hot-electron stressing. **1998**,		
1906	Two-dimensional electron gas and persistent photoconductivity in AlxGa1⊠N/GaN heterostructures. **1998**, 58, 13793-13798		25
1905	The roles of structural imperfections in InGaN-based blue light-emitting diodes and laser diodes. **1998**, 281, 955-61		1532
1904	Second Harmonic Generation and Frequency Stabilization of a Diode Laser Using an External Ring Resonator. **1998**, 2, 1-4		
1903	Differences in Design Considerations between InGaN and Conventional High-Brightness Light-Emitting Diodes. **1998**, 2, 13-21		3
1902	Electron transport characteristics of GaN for high temperature device modeling. **1998**, 83, 4777-4781		255
1901	Adatom diffusion at GaN (0001) and (0001) surfaces. *Applied Physics Letters*, **1998**, 73, 487-489	3.4	400
1900	Molecular-beam epitaxy of gallium nitride on (0001) sapphire substrates using ammonia. **1998**, 83, 1379-1383		83
1899	Optical properties of AlxGa1⊠N/GaN heterostructures on sapphire by spectroscopic ellipsometry. *Applied Physics Letters*, **1998**, 72, 2202-2204	3.4	55
1898	Intense photoluminescence from self-assembling InGaN quantum dots artificially fabricated on AlGaN surfaces. *Applied Physics Letters*, **1998**, 72, 1736-1738	3.4	115
1897	Reflectivity study of hexagonal GaN films grown on GaAs: Surface roughness, interface layer, and refractive index. **1998**, 84, 1561-1566		32
1896	Group III nitride semiconductors for short wavelength light-emitting devices. **1998**, 61, 1-75		442
1895	Recent developments in molecular organic electroluminescent materials. **1998**, 125, 1-48		214
1894	Multicolored light emitters on silicon substrates. *Applied Physics Letters*, **1998**, 73, 1487-1489	3.4	72
1893	The infrared optical functions of AlxGa1⊠N determined by reflectance spectroscopy. *Applied Physics Letters*, **1998**, 73, 1472-1474	3.4	46
1892	Phase separation and ordering in InGaN alloys grown by molecular beam epitaxy. **1998**, 84, 1389-1395		200

1891	Chemistry and kinetics of the GaN formation by plasma nitridation of GaAs: An in situ real-time ellipsometric study. **1998**, 58, 15878-15888		55
1890	Optically detected electron-nuclear double resonance of epitaxial GaN. **1998**, 57, 8957-8965		14
1889	Ultraviolet and violet GaN light emitting diodes on silicon. *Applied Physics Letters*, **1998**, 72, 415-417	3.4	266
1888	Growth of epitaxial AlxGa1⊠N films by pulsed laser deposition. *Applied Physics Letters*, **1998**, 72, 1158-1160	3.4	47
1887	InGaN-BASED LASER DIODES. **1998**, 28, 125-152		36
1886	Growth model for GaN with comparison to structural, optical, and electrical properties. **1998**, 84, 1998-2010		129
1885	Amorphous silica nanowires: Intensive blue light emitters. *Applied Physics Letters*, **1998**, 73, 3076-3078	3.4	453
1884	The study on the optical properties of GaN detector on the 6H-SiC substrates.		
1883	Quantitative Transmission Electron Microscopy Investigation of the Relaxation by Misfit Dislocations Confined at the Interface of GaN/Al2O3(0001). **1998**, 37, 84-89		30
1882	Ohmic Contact to P-Type GaN. **1998**, 37, 1768-1771		26
1881	Epitaxial Growth of GaN by Helicon Wave Plasma Assisted Metal Organic Chemical Vapor Deposition Process. **1998**, 37, 6946-6950		2
1880	Adsorption of Al on GaN(110) Surface. **1998**, 05, 269-272		
1879	GaN-BASED LASER DIODES. **1998**, 09, 1007-1080		4
1878	Comparison and Investigation of Ohmic Characteristics in the Ni/AuZn and Cr/AuZn Metal Schemes. **1998**, 37, 4667-4671		6
1877	Surface plasmons at MOCVD-grown GaN. **1998**, 13, 1396-1400		18
1876	MBE growth and characterization of magnesium-doped gallium nitride. **1998**, 13, 927-935		13
1875	Miniband structures and effective masses of n-type -doping superlattices in GaN. **1998**, 13, 981-988		5
1874	Luminescence from growth topographic features in GaN:Si films. **1998**, 83, 462-465		17

1873	Relaxations of nonpolar zinc blende (110) surface of GaN, AlN, and BN. **1998**, 84, 1977-1980		6
1872	Selective inductively coupled plasma etching of group-III nitrides in Cl2- and BCl3-based plasmas. **1998**, 16, 1621-1626		48
1871	Theory of the (12_10) prismatic stacking fault in GaN. *Applied Physics Letters*, **1998**, 72, 2316-2318	3.4	49
1870	Photoluminescence of localized excitons in pulsed-laser-deposited GaN. *Applied Physics Letters*, **1998**, 73, 3390-3392	3.4	27
1869	Enhanced GaN decomposition in H2 near atmospheric pressures. *Applied Physics Letters*, **1998**, 73, 2018-2020	3.4	69
1868	Modeling of GaN hydride vapor phase epitaxy. **1998**, 16, 685-688		4
1867	Effect of ammonia flow rate on impurity incorporation and material properties of Si-doped GaN epitaxial films grown by reactive molecular beam epitaxy. **1998**, 84, 6680-6685		14
1866	Analytical solutions of the block-diagonalized Hamiltonian for strained wurtzite semiconductors. **1998**, 57, 15303-15314		72
1865	Optical gain in GaN epilayers. *Applied Physics Letters*, **1998**, 73, 199-201	3.4	24
1864	Gallium/aluminum interdiffusion between n-GaN and sapphire. **1998**, 84, 2355-2357		16
1863	Lattice location of Si in ion implanted GaN. *Applied Physics Letters*, **1998**, 73, 1406-1408	3.4	36
1862	Experimental determination of the N-p-partial density of states in the conduction band of GaN: Determination of the polytype fractions in mixed phase samples. **1998**, 83, 1437-1445		53
1861	Optical activation and diffusivity of ion-implanted Zn acceptors in GaN under high-pressure, high-temperature annealing. **1998**, 84, 1155-1157		30
1860	Al0.15Ga0.85N/GaN heterostructures: Effective mass and scattering times. **1998**, 57, 1374-1377		37
1859	Photoluminescence and reflectance studies of exciton transitions in wurtzite GaN under pressure. **1998**, 58, 6696-6699		25
1858	Clean and As-Covered Zinc-Blende GaN (001) Surfaces: Novel Surface Structures and Surfactant Behavior. **1998**, 80, 3097-3100		92
1857	Optical Phonons in Cubic AlxGa1-xM Approached by the Modified Random Element Isodisplacement Model. **1998**, 12, 443-449		3
1856	Secondary ion mass spectroscopy investigations of magnesium and carbon doped gallium nitride films grown by molecular beam epitaxy. **1998**, 13, 71-74		25

1855	Design Rules for High-Brightness Light-Emitting Diodes Grown on GaAs Substrate. **1998**, 37, 509-516	13
1854	Structural Properties of Al 1- xIn xN Ternary Alloys on GaN Grown by Metalorganic Vapor Phase Epitaxy. **1998**, 37, L697-L699	34
1853	Growth of GaN by Atomic Hydrogen-Assisted Molecular Beam Epitaxy. **1998**, 37, L1109-L1112	11
1852	Residual Strain Dependence of Stimulated Emission in GaN Layers Grown on (0001) Sapphire Substrates. **1998**, 37, L1023-L1025	15
1851	Analysis of InGaN High-Brightness Light-Emitting Diodes. **1998**, 37, 5990-5993	9
1850	Fabrication and Characterization of AlGaN/GaN Double-Heterolaser Structures on Sapphire Substrates Using Single Crystalline AlN Buffer Layers. **1998**, 37, L905-L906	10
1849	Micro-Raman Scattering Properties of Highly Oriented AlN Films. **1998**, 12, 1963-1974	20
1848	Analysis of the Visible and UV Electroluminescence in Homojunction GaN LEDs. **1998**, 3, 1	28
1847	Development of High-bright and Pure-white LED Lamps.. **1998**, 22, 2-5	225
1846	Defect related optical and electrical properties of mbe grown cubic GaN epilayers. **1998**, 146, 145-160	3
1845	Recent Progress in Crystal Growth and Conductivity Control of Wide Bandgap Group III Nitride Semiconductors. **1998**, 510, 145	1
1844	Phase Separation and Ordering in InGaN alloys. **1998**, 512, 431	1
1843	Defect Complexes and Non-Equilibrium Processes Underlying the P-Type Doping of GaN. **1998**, 537, 1	
1842	Role of Nanopipes in Degradation of AlGaN/InGaN/GaN Devices Operating at High Voltage. **1998**, 512, 205	2
1841	Transient Photoconductivity of GaN Thin Film on Sapphire Substrate. **1998**, 512, 303	1
1840	Dry Etching Damage Effect on Ohmic Characteristics of GaN. **1998**, 512, 495	
1839	Comparison of Novel Chlorine, Bromine and Iodine Plasma Chemistries for Anisotropic Trench Etching In GaN, InN and Ain. **1998**, 512, 501	
1838	Dry and Wet Etching for Group III - Nitrides. **1998**, 537, 1	4

1837	Hydrogen and Nitrogen Ambient Effects on Epitaxial Lateral Overgrowth (ELO) of GaN Via Metalorganic Vapor-Phase Epitaxy (MOVPE). **1998**, 537, 1	5
1836	Enhanced GaN Decomposition at MOVPE Pressures. **1998**, 537, 1	2
1835	Optical Properties of Si-DOPED AlxGal-xN/AlyGal-yN (x=0.24-0.53, y=0.11) Multi-Quantum-Well Structures. **1998**, 537, 1	3
1834	Homo- and Hetero-Epitaxial Gallium Nitride Grown by Molecular Beam Epitaxy. **1998**, 537, 1	
1833	Epitaxial Lateral Overgrowth of GaN on SiC and Sapphire Substrates. **1998**, 537, 1	
1832	Interface Effects on the Persistent Photoconductivity in Thin GaN and AlGaN Films. **1998**, 537, 1	1
1831	Gan Nanotubes. **1998**, 537, 1	
1830	Behavior of W and WSix Contact Metallization on n- and p-Type GaN. **1998**, 537, 1	
1829	Characterization of Hot-Electron Effects on Flicker Noise in III□V Nitride Based Heterojunctions. **1998**, 537, 1	
1828	Transport, Growth Mechanisms, and Material Quality in GaN Epitaxial Lateral Overgrowth. **1998**, 537, 1	4
1827	Fabrication of Self-Assembling AlGaN Quantum Dot on AlGaN Surfaces Using Anti-Surfactant. **1998**, 537, 1	
1826	Stimulated emission from as-grown GaN hexagons by selective area growth hydride vapour phase epitaxy. **1998**, 34, 1970	2
1825	Epitaxial Growth Of GaN By HWP(Helicon Wave Plasma) Assisted Metal-Organic CVD (Chemical Vapor Deposition) Process. **1998**,	
1824	Study of the Epitaxial Lateral Overgrowth (ELO) Process for GaN on Sapphire Using Scanning Electron Microscopy and Monochromatic Cathodoluminescence. **1998**, 3, 1	46
1823	Structural properties of MOVPE GaN layers grown by a new multi-buffer aproach. **1998**, 3, 1	3
1822	Epitaxial Lateral Overgrowth of GaN on SiC and Sapphire Substrates. **1999**, 4, 447-452	1
1821	Fabrication of Self-Assembling AlGaN Quantum Dot on AlGaN Surfaces Using Anti-Surfactant. **1999**, 4, 852-857	4
1820	Enhanced GaN Decomposition at MOVPE Pressures. **1999**, 4, 381-387	5

1819	Optical Properties of Si-DOPED AlxGa1□N/AlyGa1□N (x=0.24□.53, y=0.11) Multi-Quantum-Well Structures. **1999**, 4, 405-410	
1818	Group III-nitride based blue emitters. **1999**, 15-28	1
1817	Dry and Wet Etching for Group III□Nitrides. **1999**, 4, 38-48	9
1816	Defect Complexes and Non-Equilibrium Processes Underlying the P-Type Doping of GaN. **1999**, 4, 508-513	3
1815	Hydrogen and Nitrogen Ambient Effects on Epitaxial Lateral Overgrowth (ELO) of GaN VIA Metalorganic Vapor-Phase Epitaxy (Movpe). **1999**, 4, 118-123	3
1814	Optical properties of thin films and quantum wells of InxGa1-xN/GaN and their dependence on laser irradiation. **1999**, 14, 921-927	1
1813	Excitonic Emissions under High Excitation of Hexagonal GaN Single Crystal Grown by Sublimation Method. **1999**, 38, L102-L104	10
1812	Periodic Boundary Quantum Chemical Study on ZnO Ultra-Violet Laser Emitting Materials. **1999**, 38, 2603-2605	8
1811	Structural and Photoluminescence Characterization of GaN Film Grown on Si (111) Substrate. **1999**, 16, 293-294	3
1810	Visible-Blind UV Digital Camera Based On a 32 □32 Array of GaN/AlGaN p-i-n Photodiodes. **1999**, 4, 1	51
1809	Photoemission spectromicroscopy studies on epitaxial lateral overgrowth GaN surfaces. **1999**, 17, 1884	3
1808	Reactive Ion Etching of GaN and AlxGa1-xN Using Cl2/CH4/Ar Plasma. **1999**, 38, 2646-2651	12
1807	Chapter 1 Visible Light-Emitting Diodes. **1999**, 64, 1-47	1
1806	Effect of defect density on the electrical characteristics of n-type GaN Schottky contacts. **1999**, 17, 2030	25
1805	Development of a pen-shaped scanner and its applications. **1999**, 38, 2093	0
1804	Using Fourier transform infrared grazing incidence reflectivity to study local vibrational modes in GaN. **1999**, 85, 6430-6433	9
1803	Novel Defect Complexes and Their Role in the p-Type Doping of GaN. **1999**, 82, 1887-1890	72
1802	Structures of GaN(0001)- (2□), - (4□), and - (5□) Surface Reconstructions. **1999**, 82, 3074-3077	91

1801	Characterization of Dopants and Deep Level Defects in Gallium Nitride. **1999**, 185-207		9
1800	Room-temperature photopumped InGaN/GaN/AlGaN vertical-cavity surface-emitting laser. *Applied Physics Letters*, **1999**, 75, 1192-1194	3.4	69
1799	Facet formation of a GaN-based device using chemically assisted ion beam etching with a photoresist mask. **1999**, 17, 1230-1234		6
1798	Large Schottky barriers for Ni/p-GaN contacts. *Applied Physics Letters*, **1999**, 74, 1936-1938	3.4	55
1797	Microstructural investigation of oxidized Ni/Au ohmic contact to p-type GaN. **1999**, 86, 3826-3832		96
1796	Time-resolved photoluminescence studies of free and donor-bound exciton in GaN grown by hydride vapor phase epitaxy. *Applied Physics Letters*, **1999**, 75, 838-840	3.4	52
1795	Nanoindentation on AlGaN thin films. **1999**, 86, 6773-6778		59
1794	Residual strain dependence of optical characteristics in GaN layers grown on (0001) sapphire substrates. *Applied Physics Letters*, **1999**, 75, 1137-1139	3.4	28
1793	W and WSix Ohmic contacts on p- and n-type GaN. **1999**, 17, 1221-1225		4
1792	Low-resistance ohmic contacts to p-type GaN achieved by the oxidation of Ni/Au films. **1999**, 86, 4491-4497		247
1791	Domain structure in chemically ordered InxGa1⊠N alloys grown by molecular beam epitaxy. **1999**, 85, 883-886		42
1790	Structural reordering and electrical activation of ion-implanted GaAs and InP due to laser annealing in a controlled atmosphere. **1999**, 59, 2986-2994		10
1789	Effects of growth temperature on GaN nucleation layers. *Applied Physics Letters*, **1999**, 75, 2187-2189	3.4	41
1788	Optical properties of Si-doped GaN films. **1999**, 86, 6124-6127		19
1787	Surface Structure of GaN(0001) in the Chemical Vapor Deposition Environment. **1999**, 83, 741-744		40
1786	Low-resistance ohmic contacts to p-type GaN. *Applied Physics Letters*, **1999**, 74, 1275-1277	3.4	254
1785	Optical properties of low-pressure metalorganic vapor phase epitaxy AlxGa1⊠N thin-film waveguides by prism coupling technique. *Applied Physics Letters*, **1999**, 74, 3960-3962	3.4	9
1784	Pendeoepitaxy of gallium nitride thin films. *Applied Physics Letters*, **1999**, 75, 196-198	3.4	163

1783	A hierarchical Bayesian deconvolution with positivity constraints.	0
1782	Influence of Sapphire Nitridation on Properties of Indium Nitride Prepared by Metalorganic Vapor Phase Epitaxy. **1999**, 38, 645-648	21
1781	Computational Studies on GaN Surface Polarity and InN/GaN Heterostructures by Density Functional Theory and Molecular Dynamics. **1999**, 38, 2544-2548	8
1780	Improvement of the Crystalline Quality of InN Layers Grown on Sapphire (0001) by Surface Nitridation. **1999**, 38, 1884-1887	21
1779	Effects of Atomic Hydrogen on the Growth of GaN by RF-Molecular Beam Epitaxy. **1999**, 38, L230-L233	17
1778	Correlation between Dislocation Density and the Macroscopic Properties of GaN Grown by Metalorganic Vapor Phase Epitaxy. **1999**, 38, L1159-L1162	14
1777	Velocity overshoot in zincblende and wurtzite GaN. **1999**, 110, 469-472	18
1776	Polarization effects in nitride semiconductor device structures and performance of modulation doped field effect transistors. **1999**, 43, 1909-1927	92
1775	The role of threading dislocations in the physical properties of GaN and its alloys. **1999**, 273-274, 24-32	168
1774	Influence of strain and buffer layer type on In incorporation during GaInN MOVPE. **1999**, 59, 268-273	16
1773	Selective area growth and epitaxial lateral overgrowth of GaN by metalorganic vapor phase epitaxy and hydride vapor phase epitaxy. **1999**, 59, 104-111	17
1772	Secondary ion mass spectrometry analysis of Mg doped GaN films prepared by hot wall epitaxy. **1999**, 59, 230-234	
1771	Novel plasma chemistries for highly selective dry etching of InxGaN1☒: BI3 and BBr3. **1999**, 59, 340-344	1
1770	The influence of MOCVD process scheme on the optical properties of GaN layers. **1999**, 59, 16-19	2
1769	Blueish green photoluminescence from nitrided GaAs(100) surfaces. **1999**, 142, 237-242	12
1768	On the effect of ion implantation in the microstructure of GaN: an XAFS study. **1999**, 6, 552-4	1
1767	Nitrogen K-edge X-ray absorption measurements on N- and O-implanted GaN. **1999**, 101-103, 689-694	8
1766	p-Type co-doping study of GaN by photoluminescence. **1999**, 197, 368-371	1

1765	Doping behavior of In0.1Ga0.9N codoped with Si and Zn. **1999**, 197, 78-83	9
1764	The initiation of GaN growth by molecular beam epitaxy on GaN composite substrates. **1999**, 197, 12-18	8
1763	Optical and structural properties of epitaxial GaN films grown by pulsed laser deposition. **1999**, 200, 362-367	21
1762	Renaissance and progress in crystal growth of nitride semiconductors. **1999**, 198-199, 885-893	13
1761	InGaN-based blue light-emitting diodes and laser diodes. **1999**, 201-202, 290-295	68
1760	A new initial growth method for pure cubic GaN on GaAs(001). **1999**, 201-202, 336-340	12
1759	Growth of Ca8La2(PO4)6O2 single crystals as substrates for GaN epitaxial growth. **1999**, 204, 302-306	15
1758	Effect of Si doping on cubic GaN films grown on GaAs(100). **1999**, 206, 150-154	6
1757	GaN: Processing, defects, and devices. **1999**, 86, 1-78	1469
1756	Heteroepitaxial growth of III▯V compound semiconductors for optoelectronic devices. **1999**, 22, 363-367	3
1755	Growth and characterization of new oxide and fluoride crystals for optical applications. **1999**, 22, 431-437	3
1754	Polarization effects in nitride semiconductors and device structures. **1999**, 3, 97-106	16
1753	Electrical characteristics and thermal stability of W, WSiN, and Nb contacts to p- and n-type GaN. **1999**, 28, 228-233	9
1752	Magnetic resonance studies of InGaN-based quantum well diodes. **1999**, 28, 252-256	3
1751	Scanning electron microscopy and cathodoluminescence study of the epitaxial lateral overgrowth (ELO) process for gallium nitride. **1999**, 28, 295-300	6
1750	Electronic near-surface defect states of bare and metal covered n-GaN films observed by cathodoluminescence spectroscopy. **1999**, 28, 308-313	12
1749	Oxygen incorporation in AlInP, and its effect on P-type doping with magnesium. **1999**, 28, 916-925	15
1748	Compositional and morphological analysis of InxGa1⌧N/GaN epilayers. **1999**, 28, 181-185	

1747	Ohmic contacts to p-ZnSe and p-GaN wide-gap semiconductors. **1999**, 82, 43-47		1
1746	GaN-Based Quantum-Effect Electron Devices Using Quantum Interference of Hot Electron Waves. **1999**, 176, 189-193		1
1745	Solid Incorporation of AlGaN and Influence of Growth Interruption on GaN/AlGaN Quantum Well Structures Grown by MOCVD. **1999**, 176, 263-267		2
1744	Homoepitaxial Growth and Luminescence Characterization of GaN Epilayer by RF-MBE on MOCVD-Grown GaN Substrate. **1999**, 176, 459-463		2
1743	MOCVD Growth of GaN on LiAlO2(100) Substrates. **1999**, 176, 589-593		25
1742	Interface Treatment of GaN/InGaN-Multi Quantum Well Structures Grown in Production Type MOVPE Systems. **1999**, 176, 649-654		
1741	Excitonic absorption of GaN epilayers on sapphire: Dynamics, intensity, and temperature dependence. **1999**, 59, 2254-2260		11
1740	Influence of defect states on the nonlinear optical properties of GaN. **1999**, 60, 11624-11630		40
1739	Ordinary and extraordinary refractive indices for AlxGa1�N epitaxial layers. *Applied Physics Letters*, **1999**, 75, 67-69	3.4	70
1738	Brillouin scattering study of bulk GaN. **1999**, 85, 8502-8504		77
1737	Temperature dependence of Raman scattering in single crystal GaN films. *Applied Physics Letters*, **1999**, 74, 3125-3127	3.4	133
1736	Scanning tunneling microscope-induced luminescence of GaN at threading dislocations. **1999**, 17, 29		26
1735	Low-temperature scanning tunneling microscope-induced luminescence of an InGaN/GaN multiquantum well. *Applied Physics Letters*, **1999**, 74, 1457-1459	3.4	15
1734	Si dopant site within ion implanted GaN lattice. **1999**, 17, 2132-2135		3
1733	III-nitride dry etching: Comparison of inductively coupled plasma chemistries. **1999**, 17, 2202-2208		10
1732	Growth of GaN layers onto misoriented (0001) sapphire by metalorganic chemical vapor deposition. **1999**, 86, 6059-6067		28
1731	Properties of group III nitrides grown in production type MOVPE systems.		
1730	Structure asymmetry effects in the optical gain of piezostrained InGaN quantum wells. **1999**, 5, 756-764		12

1729	Strain relaxation of AlxGa1⊠N epitaxial layers on GaN and SiC substrates. **1999**, 286, 284-288	6
1728	Density-functional calculations for III-V nitrides using the local-density approximation and the generalized gradient approximation. **1999**, 59, 5521-5535	564
1727	Chapter 3 High-Brightness Nitride-Based Visible-Light-Emitting Diodes. **1999**, 129-207	1
1726	Introduction. **1999**, 1-7	3
1725	Stability and electronic structure of GaN nanotubes from density-functional calculations. **1999**, 60, 7788-7791	210
1724	Characteristics of InGaN-Based UV/Blue/Green/Amber/Red Light-Emitting Diodes. **1999**, 38, 3976-3981	636
1723	Synthesis of nanocrystal GaN powders by mechanochemical reaction.	
1722	InGaN-based violet laser diodes. **1999**, 14, R27-R40	191
1721	Transport, Growth Mechanisms, and Material Quality in GaN Epitaxial Lateral Overgrowth. **1999**, 4, 588-593	3
1720	Conducting (Si-Doped) Aluminum Nitride Epitaxial Films Grown by Molecular Beam Epitaxy. **1999**, 572, 333	
1719	Comparative Study of GaN Growth Process by MOVPE. **1999**, 572, 463	
1718	High-Sensitivity Visible-Blind AlGaN Photodiodes and Photodiode Arrays. **1999**, 595, 1	2
1717	Prism coupling as a non destructive tool for optical characterization of (Al, Ga) nitride compounds. **1999**, 595, 1	
1716	Growth of Crack-Free Thick AlGaN Layer and Its Application to GaN-Based Laser Diode. **1999**, 595, 1	3
1715	Growth and Characterization of Piezoelectrically Enhanced Acceptor-Type AlGaN/GaN Heterostructures. **1999**, 595, 1	1
1714	Modeling of the spectral response of AlxGa1⊠N p-n junction photodetectors. **2000**, 11, 29-34	4
1713	Growth and Characterization of Piezoelectrically Enhanced Acceptor-Type AlGaN/GaN Heterostructures. **2000**, 5, 605-611	
1712	Novel processing for improving optical property of InGaN/GaN MQW light-emitting diode. **2000**, 3938, 124	

1711	Combinatorial computational chemistry approach to the design of metal oxide electronics materials. **2000**, 3941, 2	4
1710	Comparison of Different Substrate Pre-Treatments on the Quality of GaN Film Growth on 6H-, 4H-, and 3C-SiC. **2000**, 622, 6161	2
1709	Nature of Low-Frequency Excess Noise in n-Type Gallium Nitride. **2000**, 622, 6231	2
1708	Microstructure of GaN Films Grown by RF-Plasma Assisted Molecular Beam Epitaxy. **2000**, 639, 3471	8
1707	Microstructure of GaN Grown on (1120) Sapphire. **2000**, 639, 391	
1706	Renaissance and Progress in Nitride Semiconductors�My Personal History of Nitride Research� **2000**, 639, 811	2
1705	X-ray Photoelectron Spectroscopy Evaluation on Surface Chemical States of GaN, InGaN and AlGaN Heteroepitaxial Thin Films Grown on Sapphire by MOCVD. **2000**, 618, 303	5
1704	Structural Evolution of Ni/Au Contact on GaN(0001). **2000**, 639, 1171	
1703	Raman characterization of GaN synthesized by N implantation in GaAs substrate. **2000**, 31, 615-618	5
1702	Growth and Characterization of a Cubic GaN p� Light Emitting Diode on GaAs (001) Substrates. **2000**, 180, 369-374	1
1701	GaN Bulk Substrates for GaN Based LEDs and LDs. **2000**, 180, 51-58	7
1700	The Effects of Atomic Hydrogen on Indium Incorporation and Ordering in InGaN Grown by RF-MBE. **2000**, 180, 59-64	2
1699	Suppression of Inversion Domains and Decrease of Threading Dislocations in Migration Enhanced Epitaxial GaN by RF-Molecular Beam Epitaxy. **2000**, 180, 65-71	2
1698	Lasing in Vertical Direction in Structures with InGaN Quantum Dots. **2000**, 180, 91-96	1
1697	In situ monitoring and control of multicomponent gas-phase streams for growth of GaN via MOCVD. **2000**, 212, 11-20	8
1696	The annealing effects of Mg-doped GaN epilayers capped with SiO2 layers. **2000**, 216, 62-68	4
1695	Epitaxial growth of InN films on MgAl2O4 (111) substrates. **2000**, 220, 185-190	4
1694	Initial stages of InN thin film growth onto MgAl2O4(111) and �Al2O3(00�1) substrates. **2000**, 220, 191-196	19

1693	Progress in crystal growth of nitride semiconductors. **2000**, 221, 231-239	23
1692	Time-resolved photoluminescence study of GaN grown by metalorganic chemical vapor deposition. **2000**, 221, 240-245	2
1691	Growth of AlN on sapphire substrates by using a thin AlN buffer layer grown two-dimensionally at a very low V/III ratio. **2000**, 221, 258-261	43
1690	Low-temperature growth of GaN by remote-plasma-enhanced organometallic vapor-phase epitaxy. **2000**, 221, 305-310	8
1689	Growth of GaN film on a-plane sapphire substrates by plasma-assisted MOCVD. **2000**, 221, 311-315	15
1688	Transmission electron microscopy study of hexagonal GaN film grown on GaAs (001) substrate by using AlAs nucleation layer. **2000**, 220, 379-383	5
1687	Anomalous behavior of excess energy curves of InxGa1�N grown on GaN and InN. **2000**, 220, 401-404	30
1686	Quasi-thermodynamic analysis of MOVPE of AlGaN. **2000**, 208, 73-78	12
1685	MBE growth and X-ray study of high-quality cubic-GaN on GaAs(001). **2000**, 208, 786-790	11
1684	Investigation of preparation and properties of epitaxial growth GaN film on Si(111) substrate. **2000**, 210, 511-515	8
1683	Controllable cubic and hexagonal GaN growth on GaAs(001) substrates by molecular beam epitaxy. **2000**, 210, 811-814	11
1682	Bulk GaN single-crystals growth. **2000**, 212, 39-48	37
1681	Illumination characteristics of lighting array using 10 candela-class white LEDs under AC 100V operation. **2000**, 87-89, 1180-1182	109
1680	Light-emitting diode (LED) polymerisation of dental composites: flexural properties and polymerisation potential. **2000**, 21, 1379-85	166
1679	Luminescence of an InGaN/GaN multiple quantum well light-emitting diode. **2000**, 44, 1055-1058	28
1678	Group III-nitride based hetero and quantum structures. **2000**, 24, 239-290	81
1677	Investigation on the origin of wurtzite domains in thick cubic GaN using reactive ion etching. **2000**, 372, 25-29	1
1676	Effects of gradient and non-linear core corrections on structural and electronic properties of GaN bulk and (001) surfaces. **2000**, 292, 97-108	7

1675	The evolution of group III nitride semiconductors. **2000**, 74, 101-106	9
1674	Optical properties in InGaN/GaN multiple quantum wells and blue LEDs. **2000**, 14, 205-209	10
1673	Fabrication and performance of GaN electronic devices. **2000**, 30, 55-212	373
1672	Fabrication and characterization of metal/GaN contacts. **2000**, 161, 263-267	35
1671	Influence of N/Ga-flux ratio on optical properties and surface morphology of GaN grown on sapphire(0001) by MBE. **2000**, 166, 423-427	2
1670	Pre-treatment of low temperature GaN buffer layer deposited on AlN/Si substrate by hydride vapor phase epitaxy. **2000**, 131, 465-469	1
1669	Morphological and optical characterization of GaN prepared by pulsed laser deposition. **2000**, 124, 272-277	7
1668	Specifics of MOCVD formation of InxGa1 N inclusions in a GaN matrix. **2000**, 34, 621-625	7
1667	Study of the effects of rapid thermal annealing in generationecombination noise in MBE grown GaN thin films. **2000**, 40, 1905-1909	7
1666	Studies of high DC current induced degradation in III-V nitride based heterojunctions. **2000**, 47, 1421-1425	5
1665	Depth of cure and compressive strength of dental composites cured with blue light emitting diodes (LEDs). **2000**, 16, 41-7	192
1664	Pendeo-epitaxial growth of gallium nitride on silicon substrates. **2000**, 29, 306-310	19
1663	Model development of GaN MOVPE growth chemistry for reactor design. **2000**, 29, 2-9	19
1662	Structural defects in nitride heteroepitaxy. **2000**, 339-381	2
1661	Ion implantation, isolation and thermal processing of GaN and related materials. **2000**, 193-249	1
1660	Nitride Semiconductor Surfaces. Atomic Structures of GaN(0001) Reconstructed Surfaces. Approach Using First-Principles Simulation and STM Measurement.. **2000**, 21, 134-141	
1659	High-Sensitivity Visible-Blind AlGaN Photodiodes and Photodiode Arrays. **2000**, 5, 35-41	2
1658	Prism coupling as a non destructive tool for optical characterization of (Al,Ga) nitride compounds. **2000**, 5, 747-753	0

1657	Growth of Crack-Free thick AlGaN Layer and its Application to GaN-Based Laser Diode. **2000**, 5, 452-458	
1656	Influence of AlN Buffer on Phase Structure of GaN on GaAs (001) Grown by Radio-Frequency Molecular Beam Epitaxy. **2000**, 39, 4704-4706	8
1655	Electrical Conductivity of Low-Temperature-Deposited Al0.1Ga0.9N Interlayer. **2000**, 39, 6493-6495	1
1654	Investigation of Initial Growth Process of GaN Film on Sapphire Using Computational Chemistry. **2000**, 39, 2380-2384	3
1653	Growth of Bulk GaN Single Crystals by the Pressure-Controlled Solution Growth Method. **2000**, 39, 2394-2398	15
1652	Effects of Atomic Hydrogen on the Indium Incorporation in InGaN Grown by RF-Molecular Beam Epitaxy. **2000**, 39, L343-L346	4
1651	High-Quality GaN on AlN Multiple Intermediate Layer with Migration Enhanced Epitaxy by RF-Molecular Beam Epitaxy. **2000**, 39, L197-L199	11
1650	Performance of GaN-Based Semiconductor Laser with Spectral Broadening due to Compositional Inhomogeneity in GaInN Active Layer. **2000**, 39, 390-392	4
1649	Investigation of Thermal Annealing Process of GaN Layer on Sapphire by Molecular Dynamics. **2000**, 39, 4400-4403	8
1648	Effect of Intentionally Formed 'V-Defects' on the Emission Efficiency of GaInN Single Quantum Well. **2000**, 39, L569-L571	22
1647	Investigation into the Role of Low-Temperature GaN in n-GaN/InGaN/p-GaN Double-Heterostructure Light-Emitting Diodes. **2000**, 39, 2512-2515	3
1646	Room Temperature 339 nm Emission from Al0.13Ga0.87N/Al0.10Ga0.90N Double Heterostructure Light-Emitting Diode on Sapphire Substrate. **2000**, 39, L445-L448	32
1645	X-ray diffraction, photoluminescence and secondary ion mass spectroscopy study of GaN films grown on Si(111) substrate by vacuum reactive evaporation. **2000**, 15, 649-652	5
1644	Atomic force microscopy and transmission electron microscopy observations of KOH-etched GaN surfaces. **2000**, 18, 37	64
1643	X-ray studies of group III-nitride quantum wells with high quality interfaces. **2000**, 18, 2300	3
1642	Al concentration control of epitaxial AlGaN alloys and interface control of GaN/AlGaN quantum well structures. **2000**, 87, 172-176	39
1641	GaN-BASED LASER DIODES. **2000**, 161-234	
1640	POLARIZATION EFFECTS IN NITRIDE SEMICONDUCTOR HETEROSTRUCTURES. **2000**, 10, 25-37	6

1639	Monte Carlo Simulation on Properties of a Novel Flat-Panel Fluorescent Display Excited by GaN Micro-Ultraviolet-Light-Emitting Diodes. **2000**, 39, 6281-6285		8
1638	Effects of Thermal Annealing on the Au/Ni and the Au/Ni/Si/Ni Contact Properties of p-type GaN Epilayers. **2000**, 39, 1062-1065		5
1637	Single crystal rare earth oxides epitaxially grown on GaN.		
1636	Nitrogen dioxide sensing using a novel gas correlation detector. **2000**, 11, 499-503		10
1635	Current transport mechanism of p-GaN Schottky contacts. *Applied Physics Letters*, **2000**, 77, 4353-4355	3.4	38
1634	Electroluminescence of a cubic GaN/GaAs (001) p� junction. *Applied Physics Letters*, **2000**, 76, 13-15	3.4	54
1633	Statistical Ga clusters and A1(TO) gap mode in AlxGa1�N alloys. **2000**, 62, 2522-2535		8
1632	Photoluminescence of donor�cceptor carbazole-based molecules in amorphous and powder forms. **2000**, 87, 7290-7293		23
1631	Influence of Si doping on optical characteristics of cubic GaN grown on (001) GaAs substrates. *Applied Physics Letters*, **2000**, 76, 3765-3767	3.4	16
1630	Epitaxial growth of wurtzite GaN on Si(111) by a vacuum reactive evaporation. **2000**, 87, 2830-2834		18
1629	Observation of long photoluminescence decay times for high-quality GaN grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2000**, 77, 2503-2505	3.4	25
1628	Growth and characterization of low-temperature grown GaN with high Fe doping. *Applied Physics Letters*, **2000**, 77, 4377-4379	3.4	67
1627	Effects of growth temperature on Mg-doped GaN epitaxial films grown by plasma-assisted molecular beam epitaxy. **2000**, 18, 450-456		2
1626	Amount of hole conversion across AlxGa1�N/GaN heterojunctions. **2000**, 88, 2696-2703		
1625	Comparison of excited nitrogen sources for molecular-beam-epitaxy GaN growth: Radio frequency and electron cyclotron resonance plasma sources. *Applied Physics Letters*, **2000**, 76, 3861-3863	3.4	19
1624	Vertically faceted lateral overgrowth of GaN on SiC with conducting buffer layers using pulsed metalorganic chemical vapor deposition. *Applied Physics Letters*, **2000**, 77, 2343-2345	3.4	43
1623	Infrared characterization of GaN and GaN/AlGaN molecular beam epitaxial layers. **2000**, 18, 643-647		4
1622	Observation of "Ghost" islands and surfactant effect of surface gallium atoms during GaN growth by molecular beam epitaxy. **2000**, 85, 2352-5		21

1621	Interfacial reaction and Fermi level movement induced by sequentially deposited metals on GaN: Au/Ni/GaN. **2000**, 61, 10966-10971		22
1620	Polycrystalline nitride semiconductor light-emitting diodes fabricated on quartz substrates. *Applied Physics Letters*, **2000**, 76, 2182-2184	3.4	58
1619	Identification of the ▯5 and ▯6 free excitons in GaN. *Applied Physics Letters*, **2000**, 77, 2879-2881	3.4	43
1618	Homoepitaxial growth mechanism of ZnO(0001): Molecular-dynamics simulations. **2000**, 61, 16187-16192		39
1617	Thermodynamic analysis of III▯V semiconductor alloys grown by metalorganic vapor phase epitaxy. **2000**, 88, 4407		6
1616	Nature of the 2.8-eV photoluminescence band in Si-doped GaN. **2000**, 62, 12593-12596		60
1615	p-GaN surface treatments for metal contacts. *Applied Physics Letters*, **2000**, 76, 415-417	3.4	138
1614	Visible Light-Emitting Diodes: Past, Present, and Very Bright Future. **2000**, 25, 27-31		15
1613	UV-Specific (320-365 nm) Digital Camera Based On a 128▯128 Focal Plane Array of GaN/AlGaN p-i-n Photodiodes. **2000**, 5, 1		24
1612	Issues in developing ohmic contacts to GaN.		1
1611	Thermodynamic Analysis of Ga-N-C-H system for MOVPE process. **2000**, 24, 169-180		16
1610	Gas-phase parasitic reactions and Al incorporation efficiency in light radiation heating, low-pressure metal▯organic chemical vapor deposition of AlGaN. **2000**, 45, 331-335		5
1609	Fabrication of nano-sized AlGaN alloy by dry milling and thermal annealing. **2000**, 309, L13-L15		6
1608	Novel dark-field imaging of GaN {0001} surfaces with low-energy electron microscopy. **2000**, 464, 217-222		10
1607	Synthesis of GaN▯carbon composite nanotubes and GaN nanorods by arc discharge in nitrogen atmosphere. *Applied Physics Letters*, **2000**, 76, 652-654	3.4	143
1606	Monte Carlo evaluations of degeneracy and interface roughness effects on electron transport in AlGaN▯GaN heterostructures. **2000**, 88, 829-837		36
1605	Adsorption and desorption kinetics of gallium atoms on 6H▯SiC(0001) surfaces. **2000**, 61, 4890-4893		31
1604	Modeling of a GaN-based light-emitting diode for uniform current spreading. *Applied Physics Letters* , **2000**, 77, 1903	3.4	89

1603	Dislocation density in GaN determined by photoelectrochemical and hot-wet etching. *Applied Physics Letters*, **2000**, 77, 3532-3534	3.4	149
1602	Study of low-frequency excess noise in RTA annealed n-type gallium nitride.		
1601	Ordinary optical dielectric functions of anisotropic hexagonal GaN film determined by variable angle spectroscopic ellipsometry. **2000**, 88, 3463-3469		25
1600	The effects of thermal annealing on ZnO thin films grown by pulsed laser deposition. **2000**, 88, 498-502		141
1599	Characterization of threading dislocations in GaN epitaxial layers. *Applied Physics Letters*, **2000**, 76, 3421-3423	3.4	357
1598	Dissociation of Al2O3(0001) substrates and the roles of silicon and oxygen in n-type GaN thin solid films grown by gas-source molecular beam epitaxy. **2000**, 87, 8766-8772		32
1597	Formation of GaAsN nanoinsertions in a GaN matrix by metal-organic chemical vapour deposition. **2000**, 15, 766-769		16
1596	Three-Dimensional Optical Data Storage Using Photochromic Materials. **2000**, 100, 1777-1788		1232
1595	Novel aspects of the growth of nitrides by MOVPE. **2001**, 13, 6935-6944		11
1594	Electronic structure of 1▯ GaN(0001) and GaN(0001▯) surfaces. **2001**, 64,		79
1593	Characterization of HVPE GaN layers by atomic force microscopy and Raman spectroscopy. **2001**, 16, 776-782		8
1592	Optical actinometry of Cl2, Cl, Cl+, and Ar+ densities in inductively coupled Cl2▯Ar plasmas. **2001**, 90, 3182-3191		61
1591	Processing of compound semiconductors. **2001**, 161-190		
1590	Growth of crack-free hexagonal GaN films on Si(100). *Applied Physics Letters*, **2001**, 79, 1459-1461	3.4	30
1589	Characterization of individual threading dislocations in GaN using ballistic electron emission microscopy. **2001**, 87, 106802		30
1588	Investigation of {111}A and {111}B planes of c-GaN epilayers grown on GaAs(001) by MOCVD. **2001**, 233, 52-56		1
1587	Aromatic polyethers containing distyrylbenzene and 1,3,4-oxadiazole chromophores: synthesis and electrochemical properties. **2001**, 125, 379-387		6
1586	Comparative optical studies of p-type and unintentionally doped GaN: The influence of annealing. *Applied Physics Letters*, **2001**, 78, 58-60	3.4	12

1585	Reliable InGaN multiple-quantum well green LEDs on Si grown by MOCVD.	
1584	Room Temperature Ohmic contact on n-type GaN using plasma treatment. **2001**, 6, 1	4
1583	Defect investigation of GaN thin films etched by photo-electrochemical and hot wet etching by atomic force and transmission electron microscopy. **2001**, 680, 1	
1582	Thermal Anneal Effects on Carbon-Hydrogen LVMs In AlGaN. **2001**, 692, 1	
1581	Local Vibrational Modes of Carbon-Hydrogen Complexes in Proton Irradiated AlGaN. **2001**, 692, 1	
1580	Electric Field Induced Heating and Energy Relaxation in GaN. **2001**, 693, 156	
1579	Prepare of ZnAl2O4/□Al2O3 complex substrates and growth of GaN films. **2001**, 693, 637	
1578	Introduction. **2001**, 73, 1-13	1
1577	Ultrafast harmonic mode-locking of monolithic compound-cavity laser diodes incorporating photonic-bandgap reflectors. **2001**,	
1576	GaN blue-light-emitting diode using room-temperature ohmic contacts. **2001**, 4598, 113	
1575	The improvement of electrical properties of Pd-based contact to p-GaN by surface treatment. **2001**, 30, 183-187	16
1574	Effect of Pt barrier on thermal stability of Ti/Al/Pt/Au in ohmic contact with Si-implanted n-type GaN layers. **2001**, 30, 861-865	5
1573	In-situ monitoring of surface stoichiometry and growth kinetics study of GaN (0001) in MOVPE by spectroscopic ellipsometry. **2001**, 30, 1402-1407	14
1572	Properties of GaN epitaxial layers grown at high growth rates by metalorganic chemical vapor deposition. **2001**, 30, 23-26	5
1571	Structure and optical properties of (0 0 1)GaAs surfaces nitrided in plasma-assisted NH3 gas. **2001**, 175-176, 436-441	5
1570	Structure and luminescence of GaN layers. **2001**, 179, 191-195	10
1569	Photoluminescence of rapid-thermal annealed Mg-doped GaN films. **2001**, 45, 1153-1157	12
1568	Optoelectronic device substrates. **2001**, 4, 20-24	1

1567	GaN-based optoelectronic devices on sapphire and Si substrates. **2001**, 4, 459-466	34
1566	Effect of H+ implantation on the structural properties of GaN. **2001**, 4, 585-589	4
1565	The status and future development of innovative optoelectronic devices based on III-nitrides on SiC and on III-antimonides. **2001**, 80, 224-231	9
1564	Optical properties of Pr implanted GaN epilayers and AlxGa1⊠N alloys. **2001**, 81, 167-170	5
1563	Microstructure of GaN nucleation layer during initial stage MOCVD growth. **2001**, 82, 108-110	8
1562	GaN-based high-power laser diodes. **2001**, 82, 248-252	6
1561	Evaluation of SiC as a substrate material for nitride materials heteroepitaxy. **2001**, 82, 53-55	2
1560	Comprehensive characterization of hydride VPE grown GaN layers and templates. **2001**, 33, 135-207	141
1559	Pressure-Controlled Solution Growth of Bulk GaN Crystals under High Pressure. **2001**, 223, 15-27	36
1558	Topological Analysis of Defects in Epitaxial Nitride Films and Interfaces. **2001**, 227, 45-92	26
1557	Characterization of Mg-Doped GaN Micro-Crystals Grown by Direct Reaction of Gallium and Ammonia. **2001**, 228, 371-373	3
1556	Raman Scattering and Photoluminescence of Mg-Implanted GaN Films. **2001**, 228, 449-452	
1555	Buried Tunnel Contact Junctions in GaN-Based Light-Emitting Diodes. **2001**, 188, 167-170	5
1554	Growth and Characterization of GaN Epilayers on Chemically Etched Surface of 3C-SiC Intermediate Layer Grown on Si(111) Substrate. **2001**, 188, 527-530	3
1553	Growth and Characterization of (La,Sr)(Al,Ta)O3 Single Crystals: a Promising Substrate for GaN Epitaxial Growth. **2001**, 36, 851-858	24
1552	The effect of p-GaN:Mg layers on the turn-on voltage of p⊠ junction LED. **2001**, 222, 459-464	13
1551	Defect luminescence of GaN grown by pulsed laser deposition. **2001**, 222, 497-502	16
1550	Effect of rapid thermal annealing on the structural characteristics of cubic GaN epilayer grown on GaAs (001) substrates by molecular beam epitaxy. **2001**, 222, 503-506	

1549	Nucleation of hexagonal AlN in nitridized AlAs buffer on (001) GaAs substrate. **2001**, 222, 507-510	3
1548	GaN decomposition in H2 and N2 at MOVPE temperatures and pressures. **2001**, 223, 466-483	180
1547	Current-induced migration of surface adatoms during GaN growth by molecular beam epitaxy. **2001** , 227-228, 376-380	3
1546	High-quality GaN grown by gas-source MBE. **2001**, 227-228, 386-389	4
1545	Epitaxial growth and characterization of GaN Films on (0 0 1) GaAs substrates by radio-frequency molecular beam epitaxy. **2001**, 227-228, 390-394	2
1544	Photoluminescence study of Si doping cubic GaN grown on (001) GaAs substrates by Molecular Beam Epitaxy. **2001**, 227-228, 420-424	3
1543	Growth of bulk GaN single crystals by the pressure-controlled solution growth method. **2001**, 229, 35-40	14
1542	Growth of bulk Ga1�MnxN single crystals. **2001**, 233, 631-638	32
1541	X-ray scattering from GaN epitaxial layers - an example of highly anisotropic coherence. **2001**, 34, A25-A29	19
1540	Heavily silicon-doped GaN by MOVPE. **2001**, 32, 137-142	24
1539	Effects of current spreading on the performance of GaN-based light-emitting diodes. **2001**, 48, 1065-1069	38
1538	Effects of rapid thermal annealing on the structural properties of GaN thin films. **2001**, 48, 1225-1230	11
1537	GaN-based blue laser diodes. **2001**, 13, 7099-7114	28
1536	Aluminum, Gallium, and Indium Nitrides. **2001**, 121-126	
1535	Photoluminescence in GaN and InGaN and their applications in photonics. **2001**, 109-160	3
1534	Hydrogen in wide bandgap semiconductors. **2001**, 191-220	3
1533	Current blocking layer in GaN light-emitting diode. **2001**,	1
1532	Effects of a two-step rapid thermal annealing process on Mg-doped p-type GaN films grown by metalorganic chemical vapor deposition. **2001**, 19, 215	9

1531	Electrical and Optical Properties of InGaN/AlGaN Double Heterostructure Blue Light-Emitting Diodes. **2001**, 18, 283-285	5
1530	Fracture of AlxGa1-xN/GaN Heterostructure -- Compositional and Impurity Dependence --. **2001**, 40, L195-L197	28
1529	The Effects of In Flow during Growth Interruption on the Optical Properties of InGaN Multiple Quantum Wells Grown by Low Pressure Metalorganic Chemical Vapor Deposition. **2001**, 40, L371-L373	11
1528	Effects of Ambient Gases on Current-Voltage Characteristics of Pt-GaN Schottky Diodes at High Temperatures. **2001**, 40, L663-L665	16
1527	Effect of Barrier Thickness on the Interface and Optical Properties of InGaN/GaN Multiple Quantum Wells. **2001**, 40, 3085-3088	39
1526	Computational Chemistry Study on Crystal Growth of InGaN/GaN. **2001**, 40, 2991-2995	9
1525	Suppression of GaInN/GaN Multi-Quantum-Well Decomposition during Growth of Light-Emitting-Diode Structure. **2001**, 40, L1170-L1172	10
1524	Detection of Nanopipes in GaN Films by Localized Avalanche Breakdown Using NaOH Electrolyte. **2001**, 40, L1241-L1243	2
1523	Quaternary AlInGaN Multiple Quantum Wells for Ultraviolet Light Emitting Diodes. **2001**, 40, L921-L924	36
1522	Crystallinity of GaN Thin Films Directly Grown on Metal Foils by the Reactive Evaporation Method. **2001**, 40, 4516-4517	5
1521	Effect of Cooling Process after GaN Epitaxial Growth by Radio-Frequency Molecular Beam Epitaxy. **2001**, 40, L1297-L1300	3
1520	Enhanced diffusion as a mechanism for ion-induced damage propagation in GaN. **2001**, 19, 603	13
1519	Light-Emitting Diodes: Progress in Solid-State Lighting. **2001**, 26, 764-769	29
1518	Growth of epitaxial GaN on LiGaO2 substrates via a reaction with ammonia. **2001**, 16, 2077-2081	7
1517	Effects of contact barriers on Si-substrated GaN photodetectors. **2001**, 19, 286	1
1516	Surface analysis of (NH4)2Sx-treated InGaN using x-ray photoelectron spectroscopy. **2001**, 19, 1734	18
1515	Formation of Hf ohmic contacts by surface treatment of n-GaN in KOH solutions. **2001**, 19, 1976	5
1514	Ab InitioPseudopotential Calculations of Electronic Structure of Off-Stoichiometric ZnO. **2001**, 40, 4103-4108	11

1513	Photoenhanced Electrochemical Etching of n-GaN Forced by Negative Bias. **2001**, 40, L1086-L1088		4
1512	Depth-Resolved Cathodoluminescence of III□V Nitride Films Grown by Plasma-Assisted Molecular Beam Epitaxy. **2001**, 40, 476-479		3
1511	Strain relaxation of GaN nucleation layers during rapid thermal annealing. *Applied Physics Letters*, **2001**, 78, 2443-2445	3.4	4
1510	Electronic structure of GaN and AlN surfaces.		
1509	Monte Carlo based analysis of intermodulation distortion behavior in GaN□AlxGa1□xN high electron mobility transistors for microwave applications. **2001**, 90, 3030-3037		
1508	Effect of an oxidized Ni/Au p contact on the performance of GaN/InGaN multiple quantum well light-emitting diodes. **2001**, 89, 1506-1508		30
1507	Optical metastability of subband gap (2.2 eV) yellow luminescence in GaN. *Applied Physics Letters*, **2001**, 79, 281-283	3.4	20
1506	Optical phonons of hexagonal AlxGa1□xN: Simulation and experiment. **2001**, 90, 1761-1767		8
1505	Fluorescence x-ray absorption fine structure study on local structures around Fe atoms heavily doped in GaN by low-temperature molecular-beam epitaxy. *Applied Physics Letters*, **2001**, 78, 2470-2472	3.4	13
1504	In-plane tensile-strained interfacial structure in a GaN nucleation layer on sapphire(0001). **2001**, 90, 2191-2194		5
1503	Optical characterization of wurtzite gallium nitride nanowires. *Applied Physics Letters*, **2001**, 79, 3693-3695	3.4	39
1502	Anisotropic diffusion and drift of photogenerated carriers near coreless dislocations in InGaN quantum well. *Applied Physics Letters*, **2001**, 79, 75-77	3.4	7
1501	Residual donors and compensation in metalorganic chemical vapor deposition as-grown n-GaN. **2001**, 90, 6130-6134		17
1500	Evidence of exciton recombination at very high temperature in InGaN. **2001**, 89, 6218-6222		1
1499	Low-resistance and high-transparency Ni/indium tin oxide ohmic contacts to p-type GaN. *Applied Physics Letters*, **2001**, 79, 2925-2927	3.4	159
1498	Electron-beam-induced optical memory effects in GaN. *Applied Physics Letters*, **2002**, 80, 2675-2677	3.4	13
1497	Characterization of Mg doped GaN by positron annihilation spectroscopy. **2002**, 92, 1898-1901		12
1496	InGaN multiple-quantum-well green light-emitting diodes on Si grown by metalorganic chemical vapor deposition. **2002**, 91, 528		52

1495	Impact of V/III flux ratio and Si-doping concentration on GaN grown by metalorganic chemical-vapor deposition on sapphire substrate.		
1494	High-density plasma-induced etch damage of InGaN/GaN multiple quantum well light-emitting diodes. **2002**, 92, 1189-1194		43
1493	69Ga and 71Ga NMR studies of quadrupole interaction in the free-standing GaN single crystals grown by hydride vapor-phase epitaxy. **2002**, 65,		11
1492	Structural properties of undoped and doped cubic GaN grown on SiC(001). **2002**, 91, 4983-4987		35
1491	Nonlinear behaviors of valence-band splitting and deformation potential in dilute GaNxAs1⊠ alloys. **2002**, 92, 1446-1449		23
1490	Quasiparticle band structures of wurtzite and rock-salt ZnO. **2002**, 91, 1339-1343		26
1489	High-density plasma-induced etch damage of wafer-bonded AlGaInP/mirror/Si light-emitting diodes. **2002**, 20, 766-771		6
1488	Role of defect centers in recombination processes in GaN monocrystals. *Applied Physics Letters*, **2002**, 80, 2824-2826	3.4	3
1487	Growth and characterization of GaInNxAs1⊠ thin films with band-gap energies in the red-blue portion of the visible spectrum. *Applied Physics Letters*, **2002**, 80, 1900-1902	3.4	3
1486	Study of photoluminescence at 3.310 and 3.368 eV in GaN/sapphire(0001) and GaN/GaAs(001) grown by liquid-target pulsed-laser deposition. *Applied Physics Letters*, **2002**, 80, 3301-3303	3.4	16
1485	Dependence of the Au/Ni/Si/Ni Contact Properties on the Si-layer Thickness and the Annealing Temperature in p-type GaN Epilayers. **2002**, 17, 1019-1023		3
1484	A comparison of polymerization by light-emitting diode and halogen-based light-curing units. **2002**, 133, 335-41		110
1483	GROWTH AND STRUCTURAL PROPERTIES OF GaN FILMS ON FLAT AND VICINAL SiC(0001) SUBSTRATES. **2002**, 16, 165-172		1
1482	Single-crystal GaN/Gd2O3/GaN heterostructure. **2002**, 20, 1274		35
1481	Interfacial Properties of AlN/Si (111) Grown by Metal-Organic Chemical Vapour Deposition. **2002**, 19, 543-545		5
1480	Scanning Near-Field Optical Spectroscopy of Quantum-Confined Semiconductor Nanostructures. **2002**, 199-209		1
1479	Chemical solution deposited GaN films from oxygen- and nitrogen-based precursors. **2002**, 17, 2540-2548		12
1478	Effect of growth temperature on the microstructure of the nucleation layers of GaN grown by MOCVD on (1120) sapphire. **2002**, 743, L3.19.1		

1477	Ion Beam Study of Early Stages of Growth of GaN films on Sapphire. **2002**, 743, L3.5.1		
1476	Electrical transport properties of individual gallium nitride nanowires synthesized by chemical-vapor-deposition. *Applied Physics Letters*, **2002**, 80, 3548-3550	3.4	133
1475	Schottky diodes based on a single GaN nanowire. **2002**, 13, 701-704		72
1474	Improvement in light-output efficiency of InGaN/GaN multiple-quantum well light-emitting diodes by current blocking layer. **2002**, 92, 2248-2250		66
1473	Production of Sapphire Blanks and Substrates for Blue LEDs and LDs. **2002**, 743, L3.39.1		1
1472	Influence of defects on electrical and optical characteristics of GaN/InGaN-based light-emitting diodes. **2002**,		21
1471	Theoretical investigation of native defects, impurities, and complexes in aluminum nitride. **2002**, 65,		196
1470	Upside-down tuning of light- and heavy-hole states in GaNAs/GaAs single quantum wells by thermal expansion and quantum confinement. *Applied Physics Letters*, **2002**, 81, 3386-3388	3.4	6
1469	Infrared characterization of GaN/Si grown at different temperatures by MOCVD.		
1468	Properties of AlxGa1⊠N layers grown by plasma-assisted molecular-beam epitaxy under Ga-rich conditions. *Applied Physics Letters*, **2002**, 81, 2178-2180	3.4	15
1467	Band gap engineering, band edge emission, and p-type conductivity in wide-gap LaCuOS1⊠Sex oxychalcogenides. **2002**, 91, 4768-4770		90
1466	Demonstration of an InGaN-based light-emitting diode on an AlN/sapphire template by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2002**, 81, 292-294	3.4	28
1465	Surface electronic structure of GaN()-(1⊠): comparison between theory and experiment. **2002**, 499, 193-202		13
1464	Impact of low-temperature buffer layers on nitride-based optoelectronics. **2002**, 90, 1015-1021		6
1463	Growth and characterization of the perovskite-type oxides (NdSr)(AlNb)O3 and (LaSr)(GaNb)O3 as substrates for GaN epitaxial growth. **2002**, 339, 335-338		2
1462	Thermal annealing behaviour of Ni/Au on n-GaN Schottky contacts*. **2002**, 35, 2648-2651		29
1461	Epitaxial growth and structure of III-V nitride thin films. **2002**, 57-115		2
1460	Growth of GaN Nanorods on (0001) Sapphire Substrates by Hydride Vapor Phase Epitaxy. **2002**, 727, 1		0

1459	Polymerization of orthodontic resin cement with light-emitting diode curing units. **2002**, 122, 236-41	49
1458	Development of high efficiency GaN-based multiquantum-well light-emitting diodes and their applications. **2002**, 8, 271-277	161
1457	InGaN/GaN light emitting diodes with a p-down structure. **2002**, 49, 1361-1366	20
1456	Design and fabrication of highly efficient GaN-based light-emitting diodes. **2002**, 49, 1715-1722	14
1455	Requirements for low intermodulation distortion in GaN-Al/sub x/Ga/sub 1-x/N high electron mobility transistors: a model assessment. **2002**, 49, 1511-1518	20
1454	Improved Molecular Beam Epitaxy for Fabricating AlGaN/GaN Heterojunction Devices. **2002**, 190, 23-31	24
1453	Spectroscopic Ellipsometry in-situ Monitoring/Control of GaN Epitaxial Growth in MBE and MOVPE. **2002**, 190, 33-41	14
1452	Rapid Delineation of Extended Defects in GaN and a Novel Method for Their Reduction. **2002**, 190, 5-14	8
1451	Single Chip White LEDs. **2002**, 192, 246-253	50
1450	Expanding Emission Wavelength on Nitride Light-Emitting Devices. **2002**, 192, 261-268	16
1449	UV Light-Emitting Diode Fabricated on Hetero-ELO-Grown Al0.22Ga0.78N with Low Dislocation Density. **2002**, 192, 296-300	46
1448	High Power LEDs Technology Status and Market Applications. **2002**, 194, 380-388	153
1447	High-Efficiency UV Light-Emitting Diode. **2002**, 194, 393-398	3
1446	Growth of GaN Nanorods by a Hydride Vapor Phase Epitaxy Method. **2002**, 14, 991-993	133
1445	Raman characterization of Ar+ ion-implanted GaN. **2002**, 33, 283-286	12
1444	Acid etching for accurate determination of dislocation density in GaN. **2002**, 31, 402-405	31
1443	Elastic, structural, bonding, and defect properties of zinc-blende BN, AlN, GaN, InN and their alloys. **2002**, 90, 269-277	44
1442	Effect of defects on the degradation of ZnSe-based white LEDs. **2002**, 91-92, 470-475	29

1441	Investigation of defects and surface polarity in GaN using hot wet etching together with microscopy and diffraction techniques. **2002**, 93, 229-233	40
1440	Investigation of dislocation density of GaN with single- and double-buffer layer grown on sapphire (0001) by RF-plasma assisted MBE. **2002**, 95, 308-313	
1439	Phase separation in Zn-doped InGaN grown by metalorganic chemical vapor deposition. **2002**, 5, 39-43	6
1438	AlN/GaN short-period superlattices with monolayer AlN for optical-device applications. **2002**, 13, 1098-1101	5
1437	ICTS measurements for p-GaN Schottky contacts. **2002**, 190, 318-321	8
1436	Preparation and structural properties for GaN films grown on Si (1 1 1) by annealing. **2002**, 193, 254-260	45
1435	Investigation of preparation and characterization of GaN films on sapphire (0001) substrates. **2002**, 202, 295-300	4
1434	Modification of new photoelectric material GaN by implantation of H+, He+ and N+ ion beam. **2002**, 158-159, 412-415	2
1433	Luminescence of monolayer thin films of the fully conjugated rigid-rod polymer poly(p-phenylenebenzobisthiazole). **2002**, 40, 1760-1767	11
1432	Effect of ZnO buffer layer on the quality of GaN films deposited by pulsed laser ablation. **2002**, 411, 69-75	28
1431	Theory of exciton□polariton in GaN thin films. **2002**, 124, 109-112	4
1430	An investigation of structural, optical and electrical properties of GaN thin films grown on Si() by reaction evaporation. **2002**, 46, 301-306	1
1429	GaN-based modulation doped FETs and UV detectors. **2002**, 46, 157-202	137
1428	High temperature characteristics of Ti/Al and Cr/Al ohmic contacts to n-type GaN. **2002**, 46, 1975-1981	20
1427	Investigation of radiative tunneling in GaN/InGaN single quantum well light-emitting diodes. **2002**, 46, 2291-2294	34
1426	GaN films deposited by planar magnetron sputtering. **2002**, 66, 233-237	22
1425	High power light emitting diode (LED) arrays versus halogen light polymerization of oral biomaterials: Barcol hardness, compressive strength and radiometric properties. **2002**, 23, 2955-63	78
1424	Characterizations of GaN films grown with indium surfactant by RF-plasma assisted molecular beam epitaxy. **2002**, 42, 1179-1184	11

1423	Blue light inhibits the growth of B16 melanoma cells. **2002**, 93, 551-8	37
1422	Quasi-thermodynamic analysis of MOVPE growth of GaxAlyIn1□x□yN. **2002**, 234, 145-152	3
1421	Modulated growth of thick GaN with hydride vapor phase epitaxy. **2002**, 234, 616-622	7
1420	MOCVD growth of device-quality GaN on sapphire using a three-step approach. **2002**, 234, 637-645	34
1419	Growth of perovskite-type oxides (RE, Sr)(Al, Ta)O3 as substrates for GaN epitaxial growth (RE=La, Nd). **2002**, 235, 277-282	16
1418	Characterization of local structures around In atoms in Ga1□xInx layers by fluorescence EXAFS measurements. **2002**, 237-239, 1139-1142	
1417	NH3 flow rates dependence of crystallinity in GaN thin films grown by reactive close-spaced method at low temperature. **2002**, 237-239, 1042-1046	1
1416	Pre-treatment of GaN template for homoepitaxial growth by radio-frequency molecular beam epitaxy. **2002**, 236, 66-70	1
1415	Effects of thermal convection of NH3 during growth of GaN epitaxial layers by horizontal MOCVD reactor. **2002**, 236, 113-118	2
1414	Characteristics of GaN/Si(111) epitaxy grown using Al0.1Ga0.9N/AlN composite nucleation layers having different thicknesses of AlN. **2002**, 241, 289-296	16
1413	Structural characteristic of cubic GaN nucleation layers on GaAs(001) substrates by MOCVD. **2002**, 242, 124-128	1
1412	Growth and characterization of low defect GaN by hydride vapor phase epitaxy. **2002**, 246, 223-229	60
1411	ECR Plasma in Growth of Cubic GaN by Low Pressure MOCVD. **2002**, 22, 161-176	4
1410	Luminescence of GaN Layers Grown on GaAs Substrates by the Method of Radical-Beam Epitaxy. **2002**, 69, 270-274	
1409	Mechanochemical Synthesis and Characterization of GaN Nanocrystals. **2002**, 4, 367-371	8
1408	Thickness measurement of GaN epilayer using high resolution X-ray diffraction technique. **2003**, 46, 437	2
1407	Analysis of physical properties of III-nitride thin films by nanoindentation. **2003**, 32, 496-500	43
1406	The properties of photo chemical-vapor deposition SiO2 and its application in GaN metal-insulator semiconductor ultraviolet photodetectors. **2003**, 32, 395-399	24

1405	Influence of substrate temperature and ion-beam energy on the syntheses of aluminium nitride thin films by nitrogen-ion-assisted pulsed-laser deposition. **2003**, 77, 433-439	5
1404	High brightness InGaN green LEDs with an ITO on n/sup ++/-SPS upper contact. **2003**, 50, 2208-2212	27
1403	Cathodoluminescence study of the excitons localization in AlGaN/GaN and InGaN/GaN quantum wells grown on sapphire. **2003**, 247, 284-290	1
1402	Transmission electron microscopy and atomic force microscopy studies of GaN films grown on AlAs/GaAs(001) substrates. **2003**, 252, 517-522	1
1401	Microstructure of GaN films grown on Si(111) substrates by metalorganic chemical vapor deposition. **2003**, 256, 416-423	14
1400	Advanced light emitting diodes structures for optoelectronic applications. **2003**, 433, 22-26	65
1399	GaN-based light-emitting diodes with Ni/AuBe transparent conductive layer. **2003**, 47, 1843-1846	39
1398	In0.23Ga0.77N/GaN MQW LEDs with a low temperature GaN cap layer. **2003**, 47, 2027-2030	52
1397	Sapphire etching with BCl3/HBr/Ar plasma. **2003**, 171, 280-284	17
1396	Thermodynamic study on compositional instability of InGaN/GaN and InGaN/InN during MBE. **2003**, 216, 453-457	5
1395	GaN-based quantum dots. **2003**, 16, 244-252	10
1394	Growth of GaN epitaxial layers on sapphire with preheated ammonia and their structural and optoelectronic properties. **2003**, 3, 351-354	7
1393	Electronic structures of substitutional C and O impurities in wurtzite GaN. **2003**, 23, 169-174	3
1392	Fabrication of GaN wafers for electronic and optoelectronic devices. **2003**, 23, 1-5	40
1391	Growth of c-axis oriented GaN films on quartz by pulsed laser deposition. **2003**, 23, 15-20	11
1390	Molecular beam epitaxy of cubic III-nitrides on GaAs substrates. **2003**, 1607-1626	27
1389	Growth of GaN quasi-substrates by hydride vapor phase epitaxy. **2003**, 1571-1582	16
1388	Strain effects on Auger electron spectroscopy in different regions of epitaxial-lateral-overgrowth GaN. **2003**, 2047-2050	1

1387	High brightness InGaN/GaN LEDs with indium-tin-oxide as p-electrode. **2003**, 2227-2231	5
1386	InGaN self-organized quantum dots grown by metalorganic chemical vapour deposition (MOCVD). **2003**, 2082-2086	3
1385	Thermal analysis and design of GaN-based LEDs for high power applications. **2003**, 2261-2264	11
1384	InGaN multiple-quantum-well light-emitting diodes on an AlN/sapphire template by metalorganic chemical vapor deposition. **2003**, 2244-2247	3
1383	Amorphous GaN:Zn films deposited by molecular beam deposition for blue electroluminescent devices. **2003**, 2678-2681	2
1382	Growth of GaN Thin Films on Silicon Using Single Source Precursors and Development of New Patterning Technology by Combination of MOCVD and Micro-Contact Printing Methods. **2003**, 124-128	
1381	Low-Resistance, High-Transparency, and Thermally Stable Ohmic Contacts on p-Type GaN Using Ru and Ir. **2003**, 227-230	2
1380	Progress of InGaN Light Emitting Diodes on SiC. **2003**, 276-279	8
1379	Tunneling conductivity features of the new reconstructed phases on the GaN(0001) surface. **2003**, 78, 578-582	2
1378	Degradation of InGaN blue light-emitting diodes under continuous and low-speed pulse operations. **2003**, 43, 977-980	30
1377	GaN nanocrystals from oxygen and nitrogen-based precursors. **2003**, 249, 106-120	27
1376	Growth of Mg-doped GaN micro-crystals using MgCl2 in direct reaction of Ga and NH3. **2003**, 249, 396-403	3
1375	Structure and luminescence of GaN films by sputtering post-annealing-reaction technique. **2003**, 12, 1402-1405	3
1374	Systematic analysis and control of low-temperature GaN buffer layers on sapphire substrates. **2003** , 93, 1311-1319	39
1373	Metal Compounds as Phosphors. **2003**, 689-717	2
1372	Two-step epitaxial lateral overgrowth of GaN. **2003**, 82, 55-60	9
1371	Effect of Cl[sub 2] Plasma Treatment on Metal Contacts to n-Type and p-Type GaN. **2003**, 150, G513	22
1370	Improvement of InGaN-GaN light-emitting diodes with surface-textured indium-tin-oxide transparent ohmic contacts. **2003**, 15, 649-651	47

1369	InGaN/GaN light-emitting diodes with ITO p-contact layers prepared by RF sputtering. **2003**, 18, L21-L23		35
1368	Enhanced output power of InGaN-GaN light-emitting diodes with high-transparency nickel-oxide-indium-tin-oxide Ohmic contacts. **2003**, 15, 646-648		32
1367	Transparent Ohmic contacts of oxidized Ru and Ir on p-type GaN. **2003**, 93, 5416-5421		32
1366	Time dependence of the photoluminescence of GaN/AlN quantum dots under high photoexcitation. **2003**, 68,		38
1365	Monte Carlo analysis of GaN-based Gunn oscillators for microwave power generation. **2003**, 93, 4836-4842		29
1364	Influence of double buffer layers on properties of Ga-polarity GaN films grown by rf-plasma assisted molecular-beam epitaxy. **2003**, 57, 2413-2416		3
1363	XPS studies of chemically etched surfaces of (La,Sr)(Al,Ta)O3 single crystals. **2003**, 361, 282-288		29
1362	Unimolecular electrical rectifiers. **2003**, 103, 3803-34		478
1361	Cathode ray tube phosphors. **2003**, 103, 3835-56		113
1360	Microstructural and Electrical Investigation of Low Resistance and Thermally Stable Pd/Ni Contact on p-Type GaN. **2003**, 150, G212		12
1359	The microstructure of GaN nucleation layers grown by MOCVD on (1120) sapphire versus pressure and temperature. **2003**, 798, 508		
1358	Group III- and Group IV-Nitride Nanorods and Nanowires. **2003**, 257-315		9
1357	GaN layers re-grown on etched GaN templates by plasma assisted molecular beam epitaxy. **2003**, 798, 205		2
1356	Analysis of dislocation scattering on electron mobility in GaN high electron mobility transistors. **2003**, 93, 10046-10052		22
1355	Light-induced narrowing of excitonic absorption lines in GaN. *Applied Physics Letters*, **2003**, 83, 3510-3512	3.4	8
1354	Optical and electrical properties of homoepitaxially grown multiquantum well InGaN/GaN light-emitting diodes. **2003**, 94, 6122-6128		30
1353	X-ray photoemission spectroscopic investigation of surface treatments, metal deposition, and electron accumulation on InN. *Applied Physics Letters*, **2003**, 82, 3254-3256	3.4	72
1352	Highly low resistance and transparent Ni/ZnO ohmic contacts to p-type GaN. *Applied Physics Letters*, **2003**, 83, 479-481	3.4	83

1351	Persistent photoconductivity and optical quenching of photocurrent in GaN layers under dual excitation. **2003**, 94, 3875-3882		40
1350	Low-threshold lasing of InGaN vertical-cavity surface-emitting lasers with dielectric distributed Bragg reflectors. *Applied Physics Letters*, **2003**, 83, 830-832	3.4	55
1349	Formation of low resistance and transparent ohmic contacts to p-type GaN using Ni�Mg solid solution. *Applied Physics Letters*, **2003**, 83, 3513-3515	3.4	53
1348	Electric-field-induced heating and energy relaxation in GaN. *Applied Physics Letters*, **2003**, 82, 3035-3037	3.4	19
1347	Role of oxygen at screw dislocations in GaN. **2003**, 91, 165501		82
1346	Layer structures under in-plane compressive strains in AlxGa1�N/AlN interfaces. **2003**, 68,		6
1345	III�V Nitrides: A New Age for Optoelectronics. **2003**, 28, 350-353		16
1344	GaN-Based Modulation Doped FETs and Heterojunction Bipolar Transistors. **2003**, 51-145		
1343	Effects of Transparent Pt Metal Layer on Performance of InGaN/GaN Multiple-Quantum Well Light-Emitting Diodes. **2003**, 6, G79		1
1342	Defects in GaN Films Grown on Si(111) Substrates by Metal-Organic Chemical Vapour Deposition. **2003**, 20, 1811-1814		2
1341	Tunnelling efficiency of n�InGaN/GaN short period superlattice tunnelling contact layer for nitride-based light emitting diodes. **2003**, 18, 545-548		12
1340	Pixel-to-point Transfer: a Process for Integrating Individual GaN-based Light-emitting Devices in o Heterogeneous Microsystems. **2003**, 768, 481		
1339	Budding and Bolting Responses of Horticultural Plants to Night-break Treatments with LEDs of Various Colors. **2003**, 59, 103-110		18
1338	Semiconductors, Nitride. **2003**,		
1337	Polymerization ability of several light curing sources on composite resin. **2003**, 28, 156		1
1336	The Evolution of Blue Light-Emitting Devices and Nitride Semiconductors. **2004**, 124, 107-113		1
1335	Ca(Eu1-xLax)4Si3O13 Red Phosphor and its Application to Three-Band-Type White LEDs. **2004**, 88, 297-303		
1334	Effect of each light curing units on the microhardness and microleakage of composite resin. **2004**, 29, 58		

1333	Dentin bond strength of bonding agents cured with light emitting diode. **2004**, 29, 504		
1332	Diodes, Light-emitting. **2004**,		
1331	Photoluminescence of ZnO layers grown on opals by chemical deposition from zinc nitrate solution. **2004**, 19, 851-854		15
1330	Novel Cladding Structure for ZnSe-based White Light Emitting Diodes with Longer Lifetimes of over 10,000 h. **2004**, 43, 1287-1292		40
1329	A Quaternary Magnetic Alloy Semiconductor (Ga,In,Mn)N. **2004**, 43, L851-L854		2
1328	Room-temperature synthesis of ultraviolet-emitting nanocrystalline GaN films using photochemical vapor deposition. *Applied Physics Letters*, **2004**, 85, 3059-3061	3.4	11
1327	Low resistance and transparent Ni□La solid solution/Au ohmic contacts to p-type GaN. *Applied Physics Letters*, **2004**, 84, 1504-1506	3.4	12
1326	Photoluminescence and resonant Raman scattering in highly conductive ZnO layers. *Applied Physics Letters*, **2004**, 84, 5168-5170	3.4	27
1325	Highly transparent Ag□SnO2 ohmic contact to p-type GaN for ultraviolet light-emitting diodes. *Applied Physics Letters*, **2004**, 85, 6374-6376	3.4	53
1324	Thermal stability of InGaN multiple-quantum-well light-emitting diodes on an AlN/sapphire template. **2004**, 95, 3170-3174		28
1323	Anomalous nonlinear photoresponse in a InGaN/GaN heterostructure. **2004**, 95, 6152-6158		1
1322	Low-resistance and high-reflectance Ni□Ag□Ru□Ni□Au ohmic contact on p-type GaN. *Applied Physics Letters*, **2004**, 85, 4421	3.4	25
1321	The effects of nitrogen plasma on reactive-ion etching induced damage in GaN. **2004**, 95, 727-730		33
1320	Nitride-Based Light-Emitting Diodes Grown on Particular Substrates: ZrB2, (3038) 4H-SiC and r-faced Sapphire.. **2004**, 831, 91		
1319	High-power InGaN light emitting diodes grown by molecular beam epitaxy. **2004**, 40, 1299		14
1318	Compositional Ordering in InxGa1-xN and its influence on optical properties. **2004**, 831, 126		
1317	Growth and Characterization of bulk GaN by Ga Vapor Transport. **2004**, 831, 176		1
1316	InGaN-based light-emitting diode with undercut-side wall.		

1315	Fabrication of GaN nanowires by ammoniating Ga2O3/Al2O3thin films deposited on Si(111) with radio frequency magnetron sputtering. **2004**, 15, 724-726	22
1314	Microstructure of M-plane GaN epilayers grown on □LiAlO2 by plasma-assisted molecular beam epitaxy. **2004**, 84, 435-441	35
1313	Full Issue PDF. **2004**, 29, 1-124	
1312	Curing performance of a new-generation light-emitting diode dental curing unit. **2004**, 135, 1471-9	44
1311	Preparation and Properties of GaN Films on GaAs Substrates. **2004**, 21, 955-958	4
1310	Surface-plasmon-enhanced light emitters based on InGaN quantum wells. **2004**, 3, 601-5	1210
1309	Repeated temperature modulation epitaxy for p-type doping and light-emitting diode based on ZnO. **2004**, 4, 42-46	1830
1308	Synthesis and structural properties of GaN powders. **2004**, 88, 180-184	21
1307	Multilayer (Al,Ga)N structures for solar-blind detection. **2004**, 10, 752-758	21
1306	Shear bond strength of orthodontic brackets bonded with light-emitting diode curing units at various polymerization times. **2004**, 125, 337-41	41
1305	Multiphonon resonant Raman scattering in ZnO crystals and nanostructured layers. **2004**, 70,	105
1304	Chemical Vapor Deposition of GaN from Gallium and Ammonium Chloride. **2004**, 40, 1049-1053	6
1303	White LEDs for solid state lighting. **2004**,	23
1302	Photoluminescence study of Si-doped (112 0)a-plane GaN grown on (11 02)r-plane sapphire by metalorganic chemical vapor deposition. **2004**, 263, 94-98	30
1301	Structural and optical properties of 3D growth multilayer InGaN/GaN quantum dots by metalorganic chemical vapor deposition. **2004**, 266, 423-428	2
1300	Influence of threading dislocations on the properties of InGaN-based multiple quantum wells. **2004**, 266, 455-460	5
1299	Electron mobility in indium nitride. **2004**, 269, 35-40	41
1298	Optical and electrical properties of polycrystalline GaN films prepared by post-nitridation technique. **2004**, 352, 1-4	5

1297	Exciton polariton spectra and carrier effective masses in ZnO single crystals. **2004**, 353, 111-115	27
1296	Luminescent and structural properties of the series Ba6□EuxTi2+xTa8□O30 and Ba4□KyEu2Ti4□Ta6+yO30. **2004**, 177, 875-882	5
1295	Pyrolysis effect of group V vapor sources on the composition ranges for metal-organic vapor phase epitaxy growth of III-V semiconductors. **2004**, 25, 53-58	1
1294	Novel cladding structure for ZnSe-based white LEDs with longer lifetime over 10,000 hours. **2004**, 241, 2659-2663	9
1293	Efficiency enhancement of InGaN/GaN light-emitting diodes utilizing island-like GaN substrate. **2004**, 241, 2713-2716	2
1292	ZnO growth using remote plasma metalorganic chemical vapor deposition. **2004**, 1, 880-883	
1291	Vertical transport in group III-nitride heterostructures and application in AlN/GaN resonant tunneling diodes. **2004**, 1, 2210-2227	45
1290	Thermal stability of Ni/Ag contacts on p-type GaN. **2004**, 1, 2528-2532	5
1289	Fabrication of p-side down GaN vertical light emitting diodes on copper substrates by laser lift-off. **2004**, 1, 2413-2416	4
1288	Determination of junction temperature and thermal resistance in the GaN-based LEDs using direct temperature measurement. **2004**, 1, 2429-2432	19
1287	High-power blue/UV light-emitting diodes as excitation sources for sensitive detection. **2004**, 25, 3796-804	36
1286	Nitride-based near-ultraviolet LEDs with an ITO transparent contact. **2004**, 106, 69-72	49
1285	Measurement of crystal orientation and residual stress in GaN film deposited by RF sputtering with powder target. **2004**, 74, 613-618	9
1284	Structural and electronic properties of single-wall GaN nanotubes: semi-empirical SCF-MO calculations. **2004**, 674, 1-5	10
1283	High reliability GaN-based light-emitting diodes with photo-enhanced wet etching. **2004**, 48, 1239-1242	29
1282	Bilayer-by-bilayer etching of 6H-GaN(0001) with Cl. **2004**, 561, L213-L217	7
1281	Investigations of morphology, purity and crystal defects of the InN pillar crystals prepared by means of halide chemical vapor deposition under atmospheric pressure. **2004**, 65, 1259-1263	11
1280	Lateral epitaxial patterned sapphire InGaN/GaN MQW LEDs. **2004**, 261, 466-470	63

1279	Indium-facilitated growth and characterization of N-polar GaN by RF plasma-assisted molecular beam epitaxy. **2004**, 263, 301-307		3
1278	Assessment of Li▯Ga▯N ternary system and GaN single crystal growth. **2004**, 264, 13-16		25
1277	Basic studies of molecular beam epitaxy▯past, present and some future directions. **2004**, 264, 605-619		23
1276	Solid-state lighting: failure analysis of white LEDs. **2004**, 268, 449-456		456
1275	Growth of In-rich InGaN/GaN quantum dots by metalorganic chemical vapor deposition. **2004**, 269, 95-99		24
1274	The effect of electrons and phonons scattering from interface roughness and well-width fluctuations on low-field mobility of 2DEG in GaN/AlGaN. **2004**, 23, 114-120		11
1273	Improved light output power of InGaN/GaN MQW LEDs by lower temperature p-GaN rough surface. **2004**, 112, 10-13		57
1272	Optical properties of zincblende GaN/BN cylindrical nanowires. **2004**, 234, 50-53		7
1271	Raman characterization of Mg+ion-implanted GaN. **2004**, 16, S49-S55		14
1270	Effect of substrate temperature on crystal orientation and residual stress in radio frequency sputtered gallium▯nitride films. **2004**, 22, 1587-1590		10
1269	Photoluminescence studies of GaN nanorods on Si (111) substrates grown by molecular-beam epitaxy. *Applied Physics Letters*, **2004**, 85, 5718-5720	3.4	75
1268	Mechanism for Heteroepitaxial Growth of Transparent P-Type Semiconductor: LaCuOS by Reactive Solid-Phase Epitaxy. **2004**, 4, 301-307		50
1267	Low-temperature synthesis and characterization of GaN nanocrystals from gallium trichloride precursor. **2004**, 19, 3484-3489		4
1266	Direct observation of different equilibrium Ga adlayer coverages and their desorption kinetics on GaN (0001) and (0001▯) surfaces. **2004**, 69,		79
1265	Single Wall Carbon Nanotubes for p-Type Ohmic Contacts to GaN Light-Emitting Diodes. **2004**, 4, 911-914		90
1264	Nitride-based LEDs with textured side walls. **2004**, 16, 750-752		57
1263	Nitride-based LEDs with an SPS tunneling contact Layer and an ITO transparent contact. **2004**, 16, 1002-1004		67
1262	Incorporation of Oxygen Donors in AlGaN. **2004**, 151, G536		30

1261	Application of strontium silicate yellow phosphor for white light-emitting diodes. *Applied Physics Letters*, **2004**, 84, 1647-1649	3.4	372
1260	InGaN multiple quantum well laser diodes grown by molecular beam epitaxy. **2004**, 40, 33		38
1259	Exciton-Polaritons. **2004**, 249-266		1
1258	The effect of interface-roughness and dislocation scattering on low temperature mobility of 2D electron gas in GaN/AlGaN. **2004**, 19, 427-432		131
1257	XPS characterisation of neodymium gallate wafers. **2004**, 377, 259-267		24
1256	Formation of Nonalloyed Low Resistance Ni/Au Ohmic Contacts to p-Type GaN Using Au Nanodots. **2004**, 7, G179		25
1255	Dissolution procedure for the determination of major and minor elements in La-Sr-Ga-Nb oxide by inductively coupled plasma-optical emission spectrometry. **2004**, 53, 49-52		
1254	About holographic lithography for grating coupler fabrication in gallium nitride grown by MOVPE on sapphire substrate. **2005**, 5956, 368		
1253	42.4: Enhanced Photoluminescence of (Y, A)V(O, S)4: Eu3+ (A = Sr, Ba) Compared with YVO4: Eu3+. **2005**, 36, 1425		1
1252	P-77: New Luminescent Materials: Ba3V2O8 and Ba2Y2/3V2O8: Eu3+. **2005**, 36, 583		
1251	Long-term accelerated current operation of white light-emitting diodes. **2005**, 114, 39-42		72
1250	Exciton□polaritons in nanostructured nitride superlattices. **2005**, 36, 1006-1010		2
1249	AlxGa1□N/GaN heterostructure field effect transistors with various Al mole fractions in AlGaN barrier. **2005**, 275, 398-403		5
1248	InGaN laser diodes and high brightness light emitting diodes grown by molecular beam epitaxy. **2005**, 278, 361-366		9
1247	MOCVD growth of GaN islands by multistep nucleation layer technique. **2005**, 277, 64-71		10
1246	Growth of vanadium-doped GaN by MOVPE. **2005**, 277, 57-63		20
1245	Growth of GaN crystals from molten solution with Ga free solvent using a temperature gradient. **2005**, 281, 5-10		14
1244	Synthesis of GaN nanospindles via a facile solid-state reaction route. **2005**, 280, 341-345		4

1243	Blue luminescence from the InGaN multiple quantum wells. **2005**, 25, 390-394	1
1242	GaN nanocolumns formed by inductively coupled plasmas etching. **2005**, 28, 115-120	13
1241	Investigation of optical properties of nanoporous GaN films. **2005**, 28, 141-149	68
1240	Interface optical phonon localization in graded GaN thin films. **2005**, 336, 259-263	1
1239	ICP etching of sapphire substrates. **2005**, 27, 1171-1174	49
1238	Atomic resolution electron energy-loss spectroscopy. **2005**, 143, 105-115	11
1237	Effects of different modified underlayer surfaces on growth and optical properties of InGaN quantum dots. **2005**, 77, 307-314	3
1236	Hooge noise parameter of epitaxial n-GaN on sapphire. **2005**, 49, 865-870	4
1235	Forward-current electroluminescence from GaN/ZnO double heterostructure diode. **2005**, 49, 1693-1696	21
1234	Growth of bulk GaN single crystals by flux method. **2005**, 6, 766-771	23
1233	Growth and characterization of GaN films on Si(111) substrate using high-temperature AlN buffer layer. **2005**, 198, 350-353	11
1232	Elastic waves at the (001) and (110) surfaces of AlN, GaN and InN. **2005**, 590, 224-242	12
1231	Spin-polarized electron current from Mn-doped closed zigzag GaN nanotubes. **2005**, 401, 47-51	6
1230	Effect of shorter polymerization times when using the latest generation of light-emitting diodes. **2005**, 128, 744-8	21
1229	Effect of LED and halogen light curing on polymerization of resin-based composites. **2005**, 32, 134-40	47
1228	GaO2H, Ga2O3 and Ga2O3 powders synthesized from ball-milled GaN powders. **2005**, 94, 261-265	8
1227	Wavelength shift of gallium nitride light emitting diode with p-down structure. **2005**, 52, 1217-1219	21
1226	Reverse active mode current characteristics of SiGe HBTs. **2005**, 52, 1219-1222	12

1225	Growth behaviour of bulk GaN single crystals grown with various flux ratios using solvent-thermal method. **2005**, 40, 827-831	5
1224	Self-formation of GaN hollow nanocolumns by inductively coupled plasma etching. **2005**, 80, 1607-1610	26
1223	Initial interface study of Au deposition on GaN(0001). **2005**, 370, 287-293	4
1222	InN, latest development and a review of the band-gap controversy. **2005**, 38, 1-37	159
1221	High growth rate deposition of oriented InN pillar crystals. **2005**, 134, 617-620	1
1220	Electron beam-induced current investigation of GaN Schottky diode. **2005**, 34, 1059-1064	2
1219	Scintillation Detectors for Experiments on Plasma Accelerators. **2005**, 48, 764-771	1
1218	Improvement of the crystallinity of GaN epitaxial films grown on sapphire substrates due to the use of AlN quantum dot buffer layers. **2005**, 40, 5533-5535	1
1217	Properties of cubic GaN films obtained by nitridation of porous GaAs(001). **2005**, 202, 1668-1672	4
1216	Extracting phosphor-scattered photons to improve white LED efficiency. **2005**, 202, R60-R62	242
1215	Improved performance of InGaN/GaN blue light-emitting diodes with a SiO2/TiO2 Bragg reflector. **2005**, 202, 2836-2839	14
1214	Progresses in III-nitride distributed Bragg reflectors and microcavities using AlInN/GaN materials. **2005**, 242, 2326-2344	124
1213	A printable form of single-crystalline gallium nitride for flexible optoelectronic systems. **2005**, 1, 1164-8	98
1212	Surface plasmon enhanced InGaN light emitter. **2005**,	4
1211	Effects of Oxidized Cu and Co Layers on the Formation of Au Ohmic Contacts to p-GaN. **2005**, 152, G367	1
1210	Ga Adlayer Governed Surface Defect Evolution of (0001)GaN Films Grown by Plasma-Assisted Molecular Beam Epitaxy. **2005**, 44, L906-L908	40
1209	Design and Preparation of AlN/GaN Quantum Wells for Quantum Cascade Laser Applications. **2005**, 44, 5918-5922	11
1208	Improvement in Extraction Efficiency of GaN-Based Light-Emitting Diodes with Textured Surface Layer by Natural Lithography. **2005**, 44, 2525-2527	13

1207	High-Power GaN-Based Light-Emitting Diodes with Transparent Indium Zinc Oxide Films. **2005**, 44, 2516-2519		19
1206	Nitride based Power Chip with Indium-Tin-Oxide p-Contact and Al Back-Side Reflector. **2005**, 44, 2462-2464		13
1205	Effect of SiO2(1.2 μm)/Ti-Foil Substrate Nitridation on GaN Thin Films Grown by Reactive Evaporation Method. **2005**, 44, 8448-8450		0
1204	Presence of nanosize Au dots on the formation of ohmic contact for the Ni/Au base film to p-GaN. **2005**, 23, 2127		3
1203	Enhancement of electroluminescence in GaN-based light-emitting diodes using an efficient current blocking layer. **2005**, 23, 2284		4
1202	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaN/GaN multiple quantum wells on bulk GaN substrates. **2005**, 97, 103507		20
1201	Electronic properties of InN nanowires. *Applied Physics Letters*, **2005**, 87, 253103	3.4	44
1200	Excitation power dynamics of photoluminescence in InGaN/GaN quantum wells with enhanced carrier localization. **2005**, 97, 013525		31
1199	Effect of AlN nucleation layer on the structural properties of bulk GaN grown on sapphire by molecular-beam epitaxy. **2005**, 98, 016109		6
1198	Investigation of strontium silicate yellow phosphors for white light emitting diodes from a combinatorial chemistry. *Applied Physics Letters*, **2005**, 87, 031108	3.4	53
1197	Surface and interface studies of GaN epitaxy on Si(111) via buffer layers. **2005**, 95, 266105		48
1196	In situ hole doping of wide-gap semiconductors by dual-target simultaneous laser ablation: GaN and SiC epitaxial films. *Applied Physics Letters*, **2005**, 87, 162106	3.4	6
1195	Atomic and electronic structure of mixed and partial dislocations in GaN. **2005**, 94, 025504		53
1194	Continuous evolution of Ga adlayer coverages during plasma-assisted molecular-beam epitaxy of (0001) GaN. *Applied Physics Letters*, **2005**, 86, 041908	3.4	41
1193	Near-field scanning optical microscopic transient lens for carrier dynamics study in InGaN/GaN. *Applied Physics Letters*, **2005**, 87, 161104	3.4	33
1192	Nitride-based LEDs with n/sup -/-GaN current spreading layers. **2005**, 26, 891-893		22
1191	Excitonic blue luminescence from p-LaCuOSe/n-InGaZn5O8 light-emitting diode at room temperature. *Applied Physics Letters*, **2005**, 87, 211107	3.4	50
1190	High-quality thin single-crystal γ-Al2O3 films grown on Si (111). *Applied Physics Letters*, **2005**, 87, 091908	3.4	34

1189	Relationship between Excess Ga and Residual Oxides in Amorphous GaN Films Deposited by Compound Source Molecular Beam Epitaxy. **2005**, 44, 8432-8434	12
1188	Full Issue PDF. **2005**, 30, 1-112	
1187	Full Issue PDF. **2005**, 30, 1-140	
1186	Compositional modulation in In(x)Ga(1-x)N: TEM and X-ray studies. **2005**, 54, 243-50	17
1185	Scanning Tunneling Microscopy. **2005**, 55-112	2
1184	Beveled sidewall formation and its effect on the light output of a GaInN multiquantum well light-emitting diode with sapphire substrate. **2005**, 44, 111304	3
1183	Impact of dimming white LEDs: chromaticity shifts due to different dimming methods. **2005**, 5941, 291	48
1182	Light-emitting diodes as an illumination source for plants: a review of research at Kennedy Space Center. **2005**, 10, 71-8	35
1181	Study of InGaN self-assembled quantum dots with interruption growth by metal organic chemical vapor deposition. **2005**,	
1180	GaN film growth on Si substrate for sub-wavelength optical MEMS.	1
1179	Degree of conversion of two lingual retainer adhesives cured with different light sources. **2005**, 27, 173-9	40
1178	Control of Spectral Properties of Strontium-Alkaline Earth-Silicate-Europium Phosphors for LED Applications. **2005**, 152, G382	33
1177	Near-Ultraviolet InGaN/GaN Light-Emitting Diodes Grown on Patterned Sapphire Substrates. **2005**, 44, 2512-2515	28
1176	Synthesis and structural properties of GaN particles from GaO2H powders. **2005**, 14, 1730-1734	34
1175	Self-formation of GaN hollow nanocolumns by inductively coupled plasma etching.	
1174	Growth and optical properties on formation of self-assembled GaN nanorod grown on Si(111) substrates.	
1173	On the origin of a-type threading dislocations in GaN layers. **2005**, 23, 1588-1591	18
1172	Structure of nanocrystalline GaN from X-ray diffraction, Rietveld and atomic pair distribution function analyses. **2005**, 15, 4654	42

1171	Resonant Raman scattering study of Ar+ion-implanted AlGaN. **2005**, 17, 1995-2002	1
1170	Catalyst-free GaN nanorods grown by metalorganic molecular beam epitaxy.	
1169	A Practical Guide for X-Ray Diffraction Characterization of Ga(Al, In)N Alloys. **2005**, 22, 1984-1986	3
1168	Holographic lithography for grating coupler fabrication in gallium nitride grown on sapphire substrate.	1
1167	Roughness-induced piezoelectric charges in wurtzite group-III-nitride heterostructures. **2005**, 72,	7
1166	Optical characterization of ultrabright LEDs. **2005**, 44, 4000-3	14
1165	Life of LED-based white light sources. **2005**, 1, 167-171	473
1164	Low resistance WSix-based ohmic contacts on n-type GaN. **2005**, 98, 013712	3
1163	Formation of High-Quality Ag-Based Ohmic Contact to p-Type GaN for UV LEDs Using a Tin-Zinc Oxide Interlayer. **2005**, 8, G280	7
1162	Suppression of nonradiative recombination by V-shaped pits in GaInN/GaN quantum wells produces a large increase in the light emission efficiency. **2005**, 95, 127402	323
1161	Light-output enhancement in a nitride-based light-emitting diode with 22□undercut sidewalls. **2005** , 17, 19-21	70
1160	Confocal microphotoluminescence of InGaN-based light-emitting diodes. **2005**, 98, 064503	58
1159	Enhanced light output of an InGaN/GaN light emitting diode with a nano-roughened p-GaN surface. **2005**, 16, 1844-1848	74
1158	Nitride-based flip-chip ITO LEDs. **2005**, 28, 273-277	75
1157	Enhanced output power of near-ultraviolet InGaN-GaN LEDs grown on patterned sapphire substrates. **2005**, 17, 288-290	147
1156	Effect of Substrate Temperature on Crystal Orientation and Residual Stress in RF Sputtered Gallium Nitride Films. **2005**, 490-491, 613-618	1
1155	Luminescence Properties of Eu2+-Activated Alkaline-Earth Silicon-Oxynitride MSi2O2-□N2+2/3□M = Ca, Sr, Ba):□A Promising Class of Novel LED Conversion Phosphors. **2005**, 17, 3242-3248	536
1154	GaN:ZnO solid solution as a photocatalyst for visible-light-driven overall water splitting. **2005**, 127, 8286-7	1195

1153	Surface plasmon enhanced spontaneous emission rate of InGaN□GaN quantum wells probed by time-resolved photoluminescence spectroscopy. *Applied Physics Letters*, **2005**, 87, 071102	3.4	300
1152	Technology of MOVPE Production Tools. **2005**, 39-68		
1151	Photocurrent in epitaxial GaN. **2005**, 97, 033709		35
1150	GaN-based light-emitting diodes with indium tin oxide texturing window layers using natural lithography. *Applied Physics Letters*, **2005**, 86, 221101	3.4	132
1149	Roughness-induced mechanisms for electron scattering in wurtzite group-III-nitride heterostructures. **2005**, 72,		18
1148	Fabrication and performance of blue GaN-based vertical-cavity surface emitting laser employing AlN□GaN and Ta2O5□SiO2 distributed Bragg reflector. *Applied Physics Letters*, **2005**, 87, 081105	3.4	53
1147	Temperature dependence of the specific resistance in Ti□Al□Ni□Au contacts on n-type GaN. **2006**, 100, 123706		67
1146	Enhancement of the light output of GaN-based ultraviolet light-emitting diodes by a one-dimensional nanopatterning process. *Applied Physics Letters*, **2006**, 88, 103505	3.4	51
1145	Breakthroughs in Improving Crystal Quality of GaN and Invention of the p□ Junction Blue-Light-Emitting Diode. **2006**, 45, 9001-9010		168
1144	The atomic and electronic structure of dislocations in Ga-based nitride semiconductors. **2006**, 86, 2241-2269		17
1143	Optical properties of GaN nanorods grown by molecular-beam epitaxy; dependence on growth time. **2006**, 17, 952-5		40
1142	. **2006**, 5, 273-277		2
1141	Cu/M/Cu Sub-mount Applied in High Brightness LED Array Package. **2006**,		2
1140	Growth of GaN Quantum Well Film on Si Substrate and Its Application to a GaN-Si Hybrid Lightning Device. **2006**,		0
1139	Electric-field effects on persistent photoconductivity in undoped n-type epitaxial GaN. *Applied Physics Letters*, **2006**, 88, 072106	3.4	10
1138	Thermal stability improvement by using Pd□NiO□Al□Ti□Au reflective ohmic contacts to p-GaN for flip-chip ultraviolet light-emitting diodes. *Applied Physics Letters*, **2006**, 88, 062113	3.4	4
1137	Epitaxial Crystal Growth: Methods and Materials. **2006**, 271-301		4
1136	The lasing characteristics of GaN-based vertical-cavity surface-emitting laser with AlN-GaN and Ta2O5--SiO2 distributed Bragg reflectors. **2006**, 18, 877-879		15

1135	Enhancement of InGaNGaN IndiumTinOxide Flip-Chip Light-Emitting Diodes With TiO$_2$SiO$_2$Multilayer Stack Omnidirectional Reflector. **2006**, 18, 2050-2052		35
1134	Fabrication and efficiency improvement of micropillar InGaNCu light-emitting diodes with vertical electrodes. *Applied Physics Letters*, **2006**, 88, 181113	3.4	21
1133	ZnO-Based Light Emitters. **2006**, 525-554		3
1132	Hydrostatic-pressure-induced porous gallium nitride from nanotube bundles: an ab initio study. **2006**, 125, 174711		2
1131	Ab initio calculation of excitons in ZnO. **2006**, 73,		62
1130	Luminescent Properties of (Sr, Zn)Al2O4:Eu2+,B3+ Particles as a Potential Green Phosphor for UV LEDs. **2006**, 18, 2249-2255		109
1129	Optical Performance of InGaN/AlGaN Double Heterostucture Light Emitting Diodes. **2006**,		
1128	Terahertz response of GaN thin films. **2006**, 14, 4898-907		34
1127	Zinc Oxide Doped Indium Oxide Ohmic Contacts to p-Type GaN. **2006**, 153, G931		4
1126	Luminescence properties of red-emitting M2Si5N8:Eu2+ (M=Ca, Sr, Ba) LED conversion phosphors. **2006**, 417, 273-279		579
1125	Principal phosphor materials and their optical properties. **2006**,		
1124	Principal phosphor materials and their optical properties. **2006**,		1
1123	Phosphors for lamps. **2006**,		1
1122	Efficiency Improvement of GaN-Based LEDs with ITO Texturing Window Layers Using Natural Lithography. **2006**, 12, 1196-1201		33
1121	Stoichiometry control of sputtered CuCl thin films: Influence on ultraviolet emission properties. **2006**, 100, 096108		4
1120	Growth of GaN nano-structures using Ga(mDTC)3 precursor. **2006**, 159, 737-740		
1119	Type-II 450-550 nm InGaN-GaNAs for quantum well active region lasers and light emitters on GaN. **2006**,		
1118	Fabrication and characterization of InGaN resonant-cavity light-emitting diodes on silicon substrates. **2006**, 3, 2137-2140		2

1117	Synthesis and luminescence properties of Mg-Ti-O:Eu red-emitting phosphors. **2006**, 3, 2758-2761	16
1116	Study of Au nanoparticles/ITO ohmic contacts to p-type GaN. **2006**, 203, 2451-2456	11
1115	New PLAD apparatus and fabrication of epitaxial films and junctions of functional materials: SiC, GaN, ZnO, diamond and GMR layers. **2006**, 252, 4886-4896	1
1114	The thermodynamic analysis of the driving force for the Ni/GaN interfacial reaction. **2006**, 422, 316-320	5
1113	Dislocations formed under longitudinal stress field in epitaxial-lateral-overgrowth GaN. **2006**, 9, 15-18	1
1112	Carrier transport and capture in GaN single crystals and radiation detectors and effect of the neutron irradiation. **2006**, 568, 421-426	3
1111	Morphological and luminescent characteristics of GaN dots deposited on AlN by alternate supply of TMG and NH3. **2006**, 252, 3454-3459	4
1110	Preparation and characterization of transparent ZnO/epoxy nanocomposites with high-UV shielding efficiency. **2006**, 47, 2127-2132	231
1109	Improved quality of InGaN/GaN multiple quantum wells by a strain relief layer. **2006**, 286, 209-212	65
1108	N-type doping of GaN/Si(111) using Al0.2Ga0.8N/ALN composite buffer layer and Al0.2Ga0.8N/GaN superlattice. **2006**, 286, 235-239	5
1107	Crystal growth and characterization of thick GaN layers grown by oxide vapor transport technique. **2006**, 289, 140-144	15
1106	A study of the chemical reactions involved in Li□Ga□N system. **2006**, 290, 621-625	3
1105	A comparative study on Be and Mg doping in GaN films grown using a single GaN precursor via molecular beam epitaxy. **2006**, 291, 60-65	7
1104	Morphology optimization of MOCVD-grown GaN nucleation layers by the multistep technique. **2006**, 292, 26-32	20
1103	Bulk GaN single crystal growth and characterization using various alkali metal flux. **2006**, 292, 216-220	10
1102	GaN UV detectors for protein studies. **2006**, 563, 27-30	4
1101	Compositional modulation in. **2006**, 376-377, 468-472	15
1100	Atomically flat GaMnN by diffusion of Mn into GaN(0001). **2006**, 40, 607-611	7

1099	Growth of bulk GaN in a vertical hydride vapour phase epitaxy reactor. **2006**, 40, 205-213	25
1098	Back doping design in delta-doped AlGaN/GaN heterostructure field-effect transistors. **2006**, 140, 308-312	22
1097	Iridium-based semi-transparent current spreading layer on short-period-superlattice (SPS) tunneling contact of InGaN/GaN LEDs. **2006**, 50, 1212-1215	5
1096	Observation of a (√3 × √3)-R30° reconstruction on GaN(0 0 0 1) by RHEED and LEED. **2006**, 600, 169-174	10
1095	The use of transparent indium–zinc oxide/(oxidized-Ni/Au) ohmic contact to GaN-based light-emitting diodes for light output improvement. **2006**, 515, 2501-2506	7
1094	Equation for Internal Quantum Efficiency and Its Temperature Dependence of Luminescence, and Application to InxGa1-xN/GaN Multiple Quantum Wells. **2006**, 45, 8719-8723	21
1093	Effective single-charge end point of cordless light-emitting diode light-curing units. **2006**, 130, 378-84	2
1092	Bulk GaN single crystals: a reinvestigation of growth mechanism using Li3N flux. **2006**, 85, 169-172	8
1091	Production of vacancy defects in high-energy Sn-ion irradiated GaN: Positron beam Doppler broadening study. **2006**, 376-377, 507-511	5
1090	Exciton-polariton confinement in Fibonacci quasiperiodic superlattice. **2006**, 600, 4337-4341	3
1089	Synthesis of GaN nanowires on gold-coated substrates by pulsed laser ablation. **2006**, 6, 403-406	13
1088	Simulation of visible and ultra-violet group-III nitride light emitting diodes. **2006**, 213, 214-238	52
1087	Rapid thermal annealed InGaN/GaN flip-chip LEDs. **2006**, 53, 32-37	16
1086	Raman spectra of single micrometer-sized tubular ZnO. **2006**, 99, 160-163	42
1085	Improvement of InGaN/GaN light emitting diode performance with a nano-roughened p-GaN surface by excimer laser-irradiation. **2006**, 99, 414-417	13
1084	‘Pop-in’ phenomenon during nanoindentation in epitaxial GaN thin films on c-plane sapphire substrates. **2006**, 99, 410-413	36
1083	Elektrische Lichtquellen: Chemie in Lampen. **2006**, 40, 294-305	18
1082	Curing effectiveness of a light emitting diode on dentin bonding agents. **2006**, 77, 164-70	10

1081	Effect of light-curing method on marginal adaptation, microleakage, and microhardness of composite restorations. **2006**, 78, 302-11	8
1080	The In compositional gradation effect on photoluminescence in InGaN/GaN multi-quantum-well structures. **2006**, 18, 3127-3140	3
1079	Growth and nonlinear characterization of AlN/GaN structures. **2006**, 8, S524-S527	2
1078	Microleakage beneath ceramic and metal brackets photopolymerized with LED or conventional light curing units. **2006**, 76, 1035-40	43
1077	LED deep UV source for charge management of gravitational reference sensors. **2006**, 23, S141-S150	40
1076	InGaN self-assembled quantum dots grown by metal-organic chemical vapour deposition with growth interruption. **2006**, 17, 1713-6	24
1075	Growth of gallium nitride nanorods by metalorganic molecular beam epitaxy. **2006**, 24, 695	7
1074	Using EELS to observe composition and electronic structure variations at dislocation cores in GaN. **2006**, 86, 4727-4746	12
1073	Dependence of Yellow Phosphor on Optical and Electrical Properties of the White Light Emitting Diode Chip. **2006**, 510-511, 106-109	1
1072	Nonlithographic Random Masking and Regrowth of GaN Microhillocks to Improve Light-Emitting Diode Efficiency. **2006**, 45, L4-L7	14
1071	Self-assembled Al(x)Ga(1-x)N nanorods grown on Si(001) substrates by using plasma-assisted molecular beam epitaxy. **2006**, 17, 4640-3	21
1070	Advanced Processing of Gallium Nitride for Electronic Devices. **2006**, 1-95	
1069	Investigation on Ag/Ti Ohmic Contacts to Si-Doped n-Type Al0.27Ga0.73N and the Effect of Post Annealing Treatments. **2006**, 517, 281-286	
1068	Polymerization efficiency of different photocuring units through ceramic discs. **2006**, 31, 68-77	55
1067	Fabrication and characterization of pre-aligned gallium nitride nanowire field-effect transistors. **2006**, 17, 1264-1271	54
1066	Nitridation of porous GaAs by an ECR ammonia plasma. **2006**, 15, 33-36	4
1065	Vertically Increasing Well Thickness and In Content in GaInN MQW▯ due to V-shaped Pits. **2006**, 955, 1	1
1064	Controlled Self-formation of GaN Nanotubes by Inductively Coupled Plasmas Etching. **2006**,	

1063	Electronic structures of group-III�nitride nanorods studied by x-ray absorption, x-ray emission, and Raman spectroscopy. *Applied Physics Letters*, **2006**, 88, 223113	3.4	18
1062	Influence of Rapid Thermal Annealing on the Luminescence Properties of Nanoporous GaN Films. **2006**, 9, G150		11
1061	InGaN�GaN blue light emitting diodes with modulation-doped AlGaN�GaN heterostructure layers. **2006**, 24, 1001-1004		2
1060	First-principles calculations of the structural and electronic properties of clean GaN(0001) surfaces. **2006**, 73,		100
1059	High spatial resolution picosecond cathodoluminescence of InGaN quantum wells. *Applied Physics Letters*, **2006**, 89, 232109	3.4	70
1058	Elastic layered waves in (001) III-V nitride systems. **2006**, 74,		4
1057	GaN microcavity structure with dielectric distributed Bragg reflectors fabricated by using a wet-chemical etching of a (111) Si substrate. *Applied Physics Letters*, **2006**, 89, 041129	3.4	13
1056	Impact of disorder on high quality factor III-V nitride microcavities. *Applied Physics Letters*, **2006**, 89, 261101	3.4	64
1055	Visible-blind ultraviolet imagers consisting of 8�8 AlGaN p-i-n photodiode arrays. **2006**, 24, 641-644		5
1054	Optical activation of Eu ions in nanoporous GaN films. **2006**, 99, 104305		6
1053	Improvement of electrical and optical properties of p-GaN Ohmic metals under ultraviolet light irradiation annealing processes. **2006**, 24, 634-636		2
1052	Nitride-based flip-chip LEDs with transparent Ohmic contacts and reflective mirrors. **2006**, 29, 403-408		22
1051	Accuracy of the calculated unoccupied states in GaN phases as tested by high-resolution electron energy-loss spectroscopy. **2006**, 73,		12
1050	Electron trap level in a GaN nanorod p-n junction grown by molecular-beam epitaxy. *Applied Physics Letters*, **2006**, 88, 192104	3.4	17
1049	Radiative recombination and ultralong exciton photoluminescence lifetime in GaN freestanding film via two-photon excitation. *Applied Physics Letters*, **2006**, 89, 022108	3.4	40
1048	Preparation of (Sr[sub 1�]Ca[sub x])[sub 2]Si[sub 5]N[sub 8]�Eu[sup 2+] Solid Solutions and Their Luminescence Properties. **2006**, 153, H232		66
1047	MEASUREMENT OF FLICKER NOISE AS A DIAGNOSTIC TOOL FOR HOT-ELECTRON DEGRADATION IN GaN-BASED LEDS. **2007**, 07, L419-L428		
1046	Gallium Nitride: Synthesis and Characterization. **2007**, 66, 1-16		3

1045	Electronic Structures of Wurtzite GaN with Ga and N Vacancies. **2007**, 24, 2048-2051		7
1044	Influence of low-V/III intermediate layer on GaN grown on patterned sapphire substrate by MOVPE. **2007**,		
1043	High-quality GaN films grown on surface treated sapphire substrate. **2007**, 40, 1108-1112		3
1042	Silicate Phosphors for White LEDs Identified through Combinatorial Chemistry. **2007**, 10, J15		17
1041	Intentional and unintentional localization in InGaN. **2007**, 87, 1967-1969		11
1040	Reduction of Ohmic Contact Resistance onn-GaN by Surface Treatment Using Cl2Inductively Coupled Plasma Following Laser Lift-Off. **2007**, 46, 965-967		6
1039	Gallium nitride quantum dots in a nitrogen-bonded silica gel matrix. **2007**, 19, 346209		11
1038	InGaN blue light-emitting diodes with ZnO nucleation layers prepared by the sol□gel method. **2007**, 22, 1178-1182		8
1037	An electrical model of InGaN based high power light emitting diodes with self-heating effect. **2007**, 6669, 297		2
1036	Effects of ZnO buffer layers on the fabrication of GaN films using pulsed laser deposition. **2007**, 101, 093519		13
1035	Effects of strained InGaN interlayer on contact resistance between p-GaN and indium tin oxide. *Applied Physics Letters*, **2007**, 90, 181125	3.4	13
1034	Basal-plane slip in InGaN□GaN heterostructures in the presence of threading dislocations. *Applied Physics Letters*, **2007**, 90, 171922	3.4	11
1033	Time-resolved Photoluminescence Characterization of InGaN/GaN Quantum Wells. **2007**,		
1032	Atomistic view of the autosurfactant effect during GaN epitaxy. **2007**, 98, 206106		13
1031	Yellow-emitting Sr3SiO5:Ce3+,Li+ phosphor for white-light-emitting diodes and yellow-light-emitting diodes. *Applied Physics Letters*, **2007**, 90, 041906	3.4	190
1030	Impact of the initial stage of deposition conditions on the properties of subsequent GaN Layer. **2007**,		
1029	Structure of adsorbed organometallic rhodium: model single atom catalysts. **2007**, 98, 056102		7
1028	Time-resolved cathodoluminescence study of carrier relaxation, transfer, collection, and filling in coupled InxGa1□N□GaN multiple and single quantum wells. **2007**, 75,		18

1027	Effects of thermal annealing in ion-implanted Gallium Nitride. **2007**,		2
1026	Atomic ordering effect of quantum dots embedded in InGaN�GaN multiquantum well structures. *Applied Physics Letters*, **2007**, 90, 012116	3.4	2
1025	Using Planarized p-GaN Layer to Reduce Electrostatic Discharged Damage in Nitride-Based Light-Emitting Diode. **2007**, 46, L457-L460		6
1024	Dislocation Reduction Mechanism in Low-Nucleation-Density GaN Growth Using AlN Templates. **2007**, 46, 2895-2900		11
1023	Chapter 12 Nano-particulate photocatalysts for overall water splitting under visible light. **2007**, 18, 301-315		4
1022	Luminescence Properties of (Sr[sub 1�]Ba[sub u])Si[sub 2]O[sub 2]N[sub 2]:Eu[sup 2+], Yellow or Orange Phosphors for White LEDs, Synthesized with (Sr[sub 1�]Ba[sub u])[sub 2]SiO[sub 4]:Eu[sup 2+] as a Precursor. **2007**, 154, J320		64
1021	Electrical Activation and Carrier Compensation in Si and Mg Implanted GaN by Scanning Capacitance Microscopy. **2007**, 131-133, 491-496		8
1020	High power and high reliability GaN/InGaN flip-chip light-emitting diodes. **2007**, 16, 1135-1139		14
1019	GaN-based Indium[hyphen (true graphic)]tin-oxide light emitting diodes with nanostructured silicon upper contacts. **2007**, 1, 110		
1018	Diodes, Light-emitting. **2007**,		
1017	Effect of indium tin oxide (ITO) current spreading layer on the current uniformity of vertical structure GaN-based light-emitting diodes. **2007**,		2
1016	Photocatalytic Overall Water Splitting on Gallium Nitride Powder. **2007**, 80, 1004-1010		92
1015	Fabrication and Characterization of InGaN-Based Green Resonant-Cavity LEDs Using Hydrogen Ion-Implantation Techniques. **2007**, 154, H962		5
1014	AlGaN-based deep ultraviolet light emitting diodes with reflection layer. **2007**,		4
1013	Measurement of pure Kerr nonlinearity in GaN thin films at 800 nm by means of eclipsing Z-scan experiments. **2007**, 9, L3-L4		18
1012	Thermodynamic description of the Ca�Ga system. **2007**, 31, 120-124		2
1011	Near ultraviolet InGaN/GaN MQWs grown on maskless periodically grooved sapphire substrates fabricated by wet chemical etching. **2007**, 428, 312-315		8
1010	Consideration of the Actual Current-Spreading Length of GaN-Based Light-Emitting Diodes for High-Efficiency Design. **2007**, 43, 625-632		29

1009	The growth of high-Al-content InAlGaN quaternary alloys by RF-MBE. **2007**, 40, 765-768		19
1008	Barrier inhomogeneity and electrical properties of Pt□aN Schottky contacts. **2007**, 102, 113701		143
1007	Homogenous indium distribution in InGaN/GaN laser active structure grown by LP-MOCVD on bulk GaN crystal revealed by transmission electron microscopy and x-ray diffraction. **2007**, 18, 465707		19
1006	Optical quenching of NiO□i coated ZnO nanowires. *Applied Physics Letters*, **2007**, 91, 012102	3.4	24
1005	Improved local thermal management of AlGaN-based deep-UV light emitting diodes. **2007**, 22, 1081-1085		4
1004	Preparation and Luminescence Characteristics of Ca 3 Y 2 (BO 3) 4 :Eu 3+ Phosphor. **2007**, 24, 2977-2979		9
1003	Weak ferromagnetism in Cu-doped GaN. *Applied Physics Letters*, **2007**, 91, 232109	3.4	38
1002	White electroluminescence from a hybrid polymer-GaN:Mg nanocrystals device. *Applied Physics Letters*, **2007**, 91, 093132	3.4	5
1001	Effect of barrier growth temperature on morphological evolution of green InGaN/GaN multi-quantum well heterostructures. **2007**, 40, 5050-5054		31
1000	Anti-localization suppresses non-radiative recombination in GaInN/GaN quantum wells. **2007**, 87, 2041-2065		20
999	Application the Yellow Phosphor and Luminescence Characteristics of SrSiO3:xEu2+ Synthesized by Hydrothermal Synthesis Process. **2007**,		
998	X-ray reciprocal space maps and x-ray scattering topographic observation of GaN layer on GaAs (001) in plasma-assisted molecular beam epitaxy. **2007**, 101, 063516		2
997	Conducting Organic Materials and Devices. **2007**, i-188		19
996	Hydrothermal Synthesis of V0.13Mo0.87O2.935 Nanowires with Strong Blue Photoluminescence. **2007**, 111, 5882-5885		15
995	Precursors to Semiconducting Materials. **2007**, 1-34		7
994	Preparation of CaAlSiN3:Eu2+ Phosphors by the Self-Propagating High-Temperature Synthesis and Their Luminescent Properties. **2007**, 19, 4592-4599		472
993	Enhanced white light emission from GdAl3(BO3)4:Dy3+,Ce3+nanorods. **2007**, 18, 145602		33
992	Fabrication and characteristics of thin-film InGaN□aN light-emitting diodes with TiO2/SiO2omnidirectional reflectors. **2007**, 22, 831-835		14

991	Lifetime Estimation of High Power White LEDs. **2007**, 31, 11-18	53
990	Topological analysis of citation networks to discover the future core articles. **2007**, 58, 872-882	44
989	Bright Blue Photo- and Electroluminescence from Eu2+-Doped GaN/SiO2 Nanocomposites. **2007**, 17, 3462-3469	19
988	First-principles calculations of structural properties of GaN : V. **2007**, 144, 109-113	9
987	Enhanced luminescence of InGaN/GaN multiple quantum wells by strain reduction. **2007**, 51, 860-864	54
986	Metal-doped ZnO thin films: Synthesis and characterizations. **2007**, 201, 5318-5322	52
985	Effect of growth temperature on polytype transition of GaN from zincblende to wurtzite. **2007**, 515, 4393-4396	23
984	Luminescence and ultrafast phenomena in InGaN multiple quantum wells. **2007**, 515, 4401-4404	3
983	Electrical and thermal stability of Ag ohmic contacts for GaN-based flip-chip light-emitting diodes by using an AgAl alloy capping layer. **2007**, 10, 14-18	10
982	GaN as a radiation hard particle detector. **2007**, 576, 60-65	57
981	Quantitative determination of depth carrier profiles in ion-implanted Gallium Nitride. **2007**, 257, 336-339	15
980	Investigation of InGaN/GaN light emitting diodes with nano-roughened surface by excimer laser etching method. **2007**, 136, 182-186	13
979	Structural, spectroscopic and photoluminescence studies of LiEu(WO4)2�(MoO4)x as a near-UV convertible phosphor. **2007**, 180, 619-627	128
978	Electrical performance of gallium nitride nanocolumns. **2007**, 37, 200-203	19
977	Photoluminescence properties of Ba3V2O8, Ba3(1�)Eu2xV2O8 and Ba2Y2/3V2O8:Eu3+. **2007**, 122-123, 95-98	62
976	The influence of the coating metals with various work function on the photoluminescence of a GaN-based blue LED wafer. **2007**, 126, 636-640	3
975	AlGaN ultraviolet metal-semiconductor-metal photodetectors grown on Si substrates. **2007**, 135, 502-506	16
974	Low current operation of GaN-based blue-violet laser diodes fabricated on sapphire substrate using high-temperature-grown single-crystal AlN buffer layer. **2007**, 298, 682-686	2

973	Optical and micro-structural properties of high photoluminescence efficiency InGaN/AlInGaN quantum well structures. **2007**, 298, 504-507	8
972	Thermodynamic study of AlGaN composition grown by metalorganic chemical vapor deposition. **2007**, 298, 367-371	4
971	Key inventions in the history of nitride-based blue LED and LD. **2007**, 300, 2-10	74
970	Nitrogen supply rate dependence of InGaN growth properties, by RF-MBE. **2007**, 305, 12-18	28
969	Growth of dislocation-free GaN islands on Si(1 1 1) using a scandium nitride buffer layer. **2007**, 308, 302-308	37
968	On the use of the thermal step method as a tool for study of space charge in semiconductor gallium nitride: GaN. **2007**, 4, 212-215	2
967	Fabrication of GaN/ZnO bilayers on sapphire by pulsed laser ablation-deposition. **2007**, 4, 1427-1431	
966	GaN films deposited on (111)Si by CS-MBD with re-evaporation enhancement technique for UV light-emitting devices. **2007**, 4, 1719-1722	1
965	Single crystalline GaN grown on porous Si(111) by MOVPE. **2007**, 4, 1908-1912	5
964	The phonon dispersion of wurtzite-ZnO revisited. **2007**, 244, 1478-1482	16
963	Intersubband absorption at 1.5□3.5 □m in GaN/AlN multiple quantum wells grown by molecular beam epitaxy on sapphire. **2007**, 244, 2892-2905	18
962	Improved electroluminescence on nonpolar m -plane InGaN/GaN quantum wells LEDs. **2007**, 1, 125-127	123
961	Surface and bulk exciton recombination dynamics in GaN freestanding films via one- and two-photon excitations. **2007**, 18, 453-457	4
960	Development of Cocatalysts for Photocatalytic Overall Water Splitting on (Ga1□ Zn x)(N1□ O x) Solid Solution. **2007**, 11, 145-157	48
959	Effects of growth interruption on the properties of InGaN/GaN MQWs grown by MOCVD. **2007**, 3, 1-3	6
958	Hybrid II-VI and III-V Compound Double Heterostructures and Their Properties. **2007**, 36, 409-413	4
957	Low-resistance and transparent Ni□Co solid solution/Au ohmic contacts to p-type GaN for green GaN-based light-emitting diodes. **2008**, 44, 735-741	3
956	Synthesis and luminescent properties of Sr4Al14O25:Eu2+ blue□green emitting phosphor for white light-emitting diodes (LEDs). **2008**, 19, 339-342	22

955	Study of the thermal step signal of GaN grown on porous silicon substrate by MOVPE. **2008**, 19, 1156-1159	3
954	Tunable bluish green to yellowish green Ca2(1-x)Sr2xAl2SiO7:Eu2+ phosphors for potential LED application. **2008**, 92, 195-198	46
953	A new approach to white light emitting diodes of p-GaN/i-ZnO/n-ZnO heterojunctions. **2008**, 92, 185-188	23
952	Growth of GaN Films on Si (100) Buffered with ZnO by Ion-Beam-Assisted Filtered Cathodic Vacuum Arc Technique. **2008**, 37, 573-577	1
951	Luminescence properties of nitride red phosphor for LED. **2008**, 26, 652-655	28
950	Improvement of GaN-based LED with SiO2 photonic crystal on an ITO film by holographic lithography. **2008**, 5, 2152-2154	7
949	Fabrication of GaN-based UV TF-ELDs by CS-MBE technique and their application to RGB light-emitting pixels. **2008**, 5, 2176-2178	
948	Space charged region in GaN and InN nanocolumns investigated by atomic force microscopy. **2008**, 5, 1609-1611	1
947	Effects of patterned ion implanted sapphire substrate for LED. **2008**, 5, 2213-2215	2
946	Synthesis of rare-earth activated AlN and GaN powders via a three-step conversion process. **2008**, 5, 1889-1891	6
945	Effects of the high-energy proton irradiation on the properties of GaN ionizing radiation detectors. **2008**, 5, 3029-3031	1
944	Fabrication and characterization of self-assembled InGaN quantum dots by periodic interruption growth. **2008**, 205, 300-304	
943	Doping asymmetry in wide-bandgap semiconductors: Origins and solutions. **2008**, 245, 641-652	153
942	Enhanced Emission of (In, Ga) Nitride Nanowires Embedded with Self-Assembled Quantum Dots. **2008**, 18, 938-942	16
941	White Light-Emitting Diodes with Excellent Color Rendering Based on Organically Capped CdSe Quantum Dots and Sr3 SiO5 :Ce(3+) ,Li(+) Phosphors. **2008**, 20, 2696-702	366
940	Modeling, optimization, and growth of GaN in a vertical halide vapor-phase epitaxy bulk reactor. **2008**, 310, 906-910	10
939	Chemical planarization of GaN using hydroxyl radicals generated on a catalyst plate in H2O2 solution. **2008**, 310, 1637-1641	40
938	Emission and microstructural behaviors in the InGaN/GaN MQWs with the p-GaN layers grown at different growth temperatures. **2008**, 310, 4916-4919	9

937	White light-emitting Mg0.1Sr1.9SiO4:Eu2+ phosphors. **2008**, 128, 489-493	74
936	Optical properties of GaN/AlN quantum dots. **2008**, 9, 816-829	12
935	Purple-to-yellow tunable luminescence of Ce3+ doped yttrium□silicon□oxide□nitride phosphors. **2008**, 451, 218-221	34
934	Exciton states in wurtzite InGaN/GaN quantum wells: Strong built-in electric field and interface optical-phonon effects. **2008**, 145, 235-240	12
933	Surface phonon polariton of wurtzite GaN thin film grown on -plane sapphire substrate. **2008**, 145, 535-538	21
932	Influence of NH3 gas for GaN epilayer on □Ga2O3 substrate by nitridation. **2008**, 202, 5497-5500	8
931	Optimization of GaN nucleation layer deposition conditions on sapphire substrates in HVPE system. **2008**, 82, 988-993	4
930	Basal plane-oriented gallium nitride films on fused silica via acetate dip coating. **2008**, 516, 2858-2863	
929	Physical properties and etching characteristics of metal (Al, Ag, Li) doped ZnO films grown by RF magnetron sputtering. **2008**, 516, 6598-6603	24
928	Synthesis and photoluminescent properties of Eu3+-doped (1 □x)CaO□Li2O□WO3 phosphors. **2008**, 150, 95-98	17
927	Characterization of threading dislocations in GaN using low-temperature aqueous KOH etching and atomic force microscopy. **2008**, 59, 1171-1173	16
926	Preparation and luminescence properties of LED conversion novel phosphors SrZnO2:Sm. **2008**, 62, 907-910	34
925	Excitons in wurtzite AlGaN□GaN quantum-well heterostructures. **2008**, 77,	14
924	Effects of Polarization in Optoelectronic Quantum Structures. **2008**, 467-511	5
923	Lattice Constant Effect of Photonic Crystals on the Light Output of Blue Light-Emitting Diodes. **2008**, 20, 1455-1457	13
922	Luminescence properties of triple phosphate Ca8MgGd(PO4)7 : Eu2+for white light-emitting diodes. **2008**, 41, 095110	53
921	Improvement of light extraction from high-power flip-chip light-emitting diodes by femtosecond laser direct structuring of the sapphire backside surface. **2008**, 104, 074507	14
920	Coupled modeling of current spreading, thermal effects and light extraction in III-nitride light-emitting diodes. **2008**, 23, 125023	33

919	Electronic excitations in single-walled GaN nanotubes from first principles: Dark excitons and unconventional diameter dependences. **2008**, 77,		38
918	Change of shade by light polymerization in a resin cement polymerized beneath a ceramic restoration. **2008**, 36, 219-23		24
917	Elasticplastic transition during nanoindentation in bulk GaN crystal. **2008**, 450, 405-411		43
916	Reaction mechanism and kinetic analysis of the formation of Sr2SiO4 via solid-state reaction. **2008**, 466, 457-462		29
915	Detecting emerging research fronts based on topological measures in citation networks of scientific publications. **2008**, 28, 758-775		175
914	. **2008**, 26, 1445-1454		13
913	Cyan-white-red luminescence from europium doped Al2O3-La2O3-SiO2 glasses. **2008**, 16, 6731-5		29
912	Splitting of valance subbands in the wurtzite c-plane InGaN/GaN quantum well structure. *Applied Physics Letters*, **2008**, 93, 161910	3.4	1
911	GaN-Based Schottky Barrier Photodetectors With a 12-Pair Mg$_{rm x}$ N$_{rm y}$ GaN Buffer Layer. **2008**, 44, 916-921		35
910	Introduction. **2008**, 16, 287		74
909	Introduction. **2008**, 16, 535		
908	Luminescence of Sr[sub 2]SiO[sub 4]N[sub 2x]:Eu[sup 2+] Phosphors Prepared by Spark Plasma Sintering. **2008**, 155, J58		21
907	Structures, physical properties, and chemistry of layered oxychalcogenides and oxypnictides. **2008**, 47, 8473-86		149
906	InGaNGaN Multiple-Quantum-Well LEDs with Si-Doped Barriers. **2008**, 155, H455		4
905	AlGaN/GaN two-dimensional electron gas metal-insulator-semiconductor photodetectors with sputtered SiO2 layers. **2008**, 2, 55-57		12
904	Saving Energy and Renewable Energy Through Crystal Technology. **2008**, 435-453		
903	Electroluminescence efficiency enhancement using metal nanoparticles. *Applied Physics Letters*, **2008**, 93, 021120	3.4	43
902	Influence of Si-doping in the barriers on optical and electrical properties of InGaN/GaN MQW LEDs. **2008**,		

901	Failure Analysis of a Phosphor-Converted White Light-Emitting Diode due to the CaS:Eu Phosphor. **2008**, 47, 3524-3526	15
900	Origin of the Visible Light Absorption of GaN-Rich Ga1⊠ ZnxN1⊠Ox (x = 0.125) Solid Solution. **2008**, 112, 15915-15919	51
899	Blue-green optically pumped GaN-based vertical cavity surface emitting laser. **2008**, 44, 972	8
898	Uniaxial Strain Effects on Optical Properties of c -plane Wurtzite GaN. **2008**, 25, 4139-4142	3
897	Luminescence characteristics of Eu 3+ activated borate phosphor for white light emitting diode. **2008**, 17, 1907-1910	9
896	Synthesis of Nitridosilicate CaSr[sub 1⊠]Eu[sub x]Si[sub 5]N[sub 8] (x=0⊠) Phosphor by Calcium Cyanamide Reduction for White Light-Emitting Diode Applications. **2008**, 155, J17	32
895	Room-Temperature Growth of UV-Emitting GaN with a Hexagonal Crystal-Structure Using Photochemical Vapor Deposition. **2008**, 1, 061102	7
894	Metal Organic Chemical Vapor Deposition Growth of GaN-Based Light Emitting Diodes With Naturally Formed Nano Pyramids. **2008**, 47, 2954-2956	4
893	Structural, Optical and Electrical Properties of InGaN Sputtered Thin Films. **2008**, 1151, 30501	2
892	Growth of GaNSb alloy on the N-rich side by metal-organic vapor phase epitaxy. **2008**,	
891	Polychromatic light-emitting diodes with a fluorescent nanosphere opal coating. **2008**, 19, 355203	27
890	Blue-to-Orange Tunable Luminescence from Europium Doped Yttrium⊠Silicon⊠Oxide⊠Nitride Phosphors. **2008**, 25, 3444-3447	3
889	Optimization of GaN Barriers During the Growth of InGaN/GaN Quantum Wells at Low Temperature. **2008**, 1108, 1	
888	Highly Efficient InGaN-Based 383-nm Ultraviolet Light-Emitting Diodes Fabricated on Sapphire Substrate Using High-Temperature-Grown AlN Buffer. **2008**, 1, 101101	9
887	Abnormal photoluminescence properties of GaN nanorods grown on Si(111) by molecular-beam epitaxy. **2008**, 19, 475402	16
886	Enhance light extraction of InGaN-based green LEDs by nano-imprinted 2D photonic crystal pattern. **2008**, 23, 055002	19
885	Electrical transport properties of a nanorod GaN p-n homojunction grown by molecular-beam epitaxy. **2008**, 103, 066107	11
884	LED vs halogen light-curing of adhesive-precoated brackets. **2008**, 78, 935-40	12

883	Na doping concentration tuned conductivity of ZnO films via pulsed laser deposition and electroluminescence from ZnO homojunction on silicon substrate. **2008**, 41, 155114		45
882	The effects of crystallographic orientation and strain on the properties of excitonic emission from wurtzite InGaN/GaN quantum wells. **2008**, 20, 215223		14
881	Morphology transformation of patterned, uniform and faceted GaN microcrystals. **2008**, 41, 015406		6
880	Effects of high-intensity curing lights on microleakage under bonded lingual retainers. **2008**, 78, 1084-8		5
879	Improved heat-dissipating silicone by Nano-materials for LED packaging. **2008**,		4
878	High doping level in Mg-doped GaN layers grown at low temperature. **2008**, 103, 013110		41
877	Properties of GaN layers deposited on (0001) sapphire templates. **2008**,		1
876	A yellow-emitting Ce3+ phosphor, La1�CexSr2AlO5, for white light-emitting diodes. *Applied Physics Letters*, **2008**, 93, 091905	3.4	148
875	A Study of Oxygen Content in GaN, AlN, and GaAlN Powders. **2008**, 155, J137		1
874	Dislocation scattering in AlxGa1�N�GaN heterostructures. *Applied Physics Letters*, **2008**, 93, 182111	3.4	25
873	Selective lateral anodic etching of n-doped GaN without photo-assistance for lift-off application. **2008**,		
872	Line defects of M-plane GaN grown on �LiAlO2 by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2008**, 92, 202106	3.4	15
871	Degradation of GaN-based quantum well light-emitting diodes. **2008**, 103, 024501		35
870	LED Unit of Compact, High Power and Long Lifetime. **2008**, 32, 196-201		
869	High Efficiency Nitride Based Phosphors for White LEDs. **2008**, 32, 129-134		9
868	Thermal and Optical Improvement of Light-Emitting Diodes with Mesh Pattern on Sapphire Back Delineated by Laser Etching. **2008**,		
867	Direct imaging of GaN p-n junction by cross-sectional scanning photoelectron microscopy and spectroscopy. *Applied Physics Letters*, **2009**, 94, 122110	3.4	9
866	Substrates for III-Nitride-Based Electroluminescent Diodes. 29-73		

865	Study on the Luminous and Thermal Characteristics of High-Power Near-Ultraviolet LED Packages with Various Chip Arrangements. **2009**, 33, 142-146		1
864	Carrier localization degree of In0.2Ga0.8N/GaN multiple quantum wells grown on vicinal sapphire substrates. **2009**, 105, 013103		6
863	Time-resolved spectroscopy on GaN nanocolumns grown by plasma assisted molecular beam epitaxy on Si substrates. **2009**, 105, 013113		55
862	The high mobility a-plane GaN film grown with flow-rate modulation epitaxy. **2009**,		
861	Low-temperature time-resolved cathodoluminescence study of exciton dynamics involving basal stacking faults in a-plane GaN. *Applied Physics Letters*, **2009**, 94, 201115	3.4	39
860	Exciton localization on basal stacking faults in a-plane epitaxial lateral overgrown GaN grown by hydride vapor phase epitaxy. **2009**, 105, 043102		65
859	Surface transformation and inversion domain boundaries in gallium nitride nanorods. *Applied Physics Letters*, **2009**, 95, 211907	3.4	15
858	Tunable luminescence from Sm3+, Ce3+ codoped Al2O3-La2O3-SiO2 glasses for white light emission. **2009**, 24, 1730-1734		10
857	Atomistic modeling of III-V nitrides: modified embedded-atom method interatomic potentials for GaN, InN and Ga(1-x)In(x)N. **2009**, 21, 325801		15
856	Polarization effects on quantum levels in InN/GaN quantum wells. **2009**, 20, 485204		3
855	Effect of Local Structures on the Luminescence of Li[sub 2](Sr,Ca,Ba)SiO[sub 4]:Eu[sup 2+]. **2009**, 156, J52		45
854	On the driving techniques for high-brightness LEDs. **2009**,		8
853	Enhancement in Photoluminescence of CaMoO4 : Eu3 + Through Introducing MVO4 (M = Y or Bi). **2009**, 156, J367		2
852	Lineshape theory of photoluminescence from semiconductor alloys. **2009**, 106, 123521		33
851	GaN-Based LED with Embedded Microlens-like Structure. **2009**, 156, H976		6
850	Raman studies of GaN/sapphire thin film heterostructures. **2009**, 106, 054317		55
849	Growth of two-dimensional GaN in Na-4 mica nanochannels. **2009**, 42, 235504		14
848	InGaN nanopillars grown on silicon substrate using plasma assisted molecular beam epitaxy. **2009**, 20, 325605		23

847	Effects of the sapphire substrate thickness on the performances of GaN-based LEDs. **2009**, 24, 065002	1
846	Theoretical study of composition fluctuation in InGaN films on various substrates. **2009**, 152, 012025	5
845	Carrier relaxation dynamics in SnxNy nanowires grown by chemical vapor deposition. **2009**, 106, 114303	7
844	GaN MSM Photodetectors with a Semi-Insulating AlInN Cap Layer and Sputtered ITO Transparent Electrodes. **2009**, 12, H369	1
843	X-ray Diffraction Study of InGaN/GaN Superlattice Implanted With Eu3+ Ions. **2009**, 1202, 112	
842	Rigid ion model of high field transport in GaN. **2009**, 21, 174206	16
841	Activation of Hydrogen-Passivated Mg in GaN-Based Light Emitting Diode Annealing with Minority-Carrier Injection. **2009**, 26, 017103	
840	Degradation Mechanism of GaN-based LEDs With Different Growth Parameters. **2009**, 1195, 210	
839	Preparation, Electronic Structure, and Photoluminescence Properties of Eu[sup 2+]-Activated Carbonate Sr[sub 1]Ba[sub x]CO[sub 3] for White Light-Emitting Diodes. **2009**, 156, J267	11
838	Luminescent characteristics of LiSrBO3:M (M=Eu3+, Sm3+, Tb3+, Ce3+, Dy3+) phosphor for white light-emitting diode. **2009**, 44, 2068-2071	44
837	Luminescence properties of Eu2+-activated Ca12Al10.6Si3.4O32Cl5.4: A promising phosphor for solid state lighting. **2009**, 63, 1275-1277	18
836	Development of GaN-Based Vertical-Cavity Surface-Emitting Lasers. **2009**, 15, 850-860	21
835	LEDs for Solid-State Lighting: Performance Challenges and Recent Advances. **2009**, 15, 1028-1040	575
834	Surface Texturing of High-Power Flip-Chip LEDs by Femtosecond Laser Direct Structuring. **2009**, 15, 1250-1256	11
833	Aktuelle Entwicklungen auf dem Gebiet der anorganischen Leuchtstoffe. **2009**, 121, 3626-3636	56
832	Convergence of Microscopy Techniques. **2009**, 11, 50-52	
831	Recent developments in the field of inorganic phosphors. **2009**, 48, 3572-82	885
830	First-principles study of narrow single-walled GaN nanotubes. **2009**, 373, 367-370	18

829	A DFT study of the nuclear magnetic response of the zigzag AlNBN and BNAlN nanotube junctions. **2009**, 913, 126-130	15
828	Study on sapphire removal for thin-film LEDs fabrication using CMP and dry etching. **2009**, 255, 9469-9473	46
827	Thermal transportation simulation of a susceptor structure with ring groove for the vertical MOCVD reactor. **2009**, 311, 4679-4684	15
826	Influence of ion beam bombardment on characteristic of InGaN/GaN single quantum well grown by metalorganic chemical vapor deposition. **2009**, 23, 180-184	
825	Structures and luminescence properties of Eu2+- doped sialon phosphors for UV-LED. **2009**, 23, 312-316	5
824	Photoluminescence spectra tuning of Eu2+ activated orthosilicate phosphors used for white light emitting diodes. **2009**, 20, 433-438	31
823	Ab initio study of [001] GaN nanowires. **2009**, 11, 841-859	25
822	Local surface plasmon induced fluorescence emission enhancement and its application in white light emitting diodes. **2017**, 140, 18-24	
821	Increased Synthetic Control-Gaining Access to Predicted Mg Si N and Ca Si N. **2017**, 56, 4810-4813	17
820	Photoluminescence tuning of Ca8SrxMgGd(PO4)7:Eu2+,yMn2+ phosphors for applications in white LEDs with excellent color rendering index. **2017**, 7, 19223-19230	9
819	Reaction mechanism and luminescence properties of orange-red SrAlSi4N7:Eu2+ phosphor for white-LEDs. **2017**, 35, 223-229	6
818	Layered Nitridomagnesogallates CaMg2GaN3 and CaMg2Ga2N4. **2017**, 2017, 1067-1074	6
817	Significant performance enhancement of InGaN/GaN nanorod LEDs with multi-layer graphene transparent electrodes by alumina surface passivation. **2017**, 28, 055201	22
816	Interface dislocations in InxGa1N/GaN heterostructures. **2017**, 214, 1600442	5
815	Luminescence properties of Na2SiF6:Mn4+ red phosphors for high colour-rendering white LED applications synthesized via a simple exothermic reduction reaction. **2017**, 1, 928-932	24
814	A novel approach to obtain highly intense self-activated photoluminescence emissions in hydroxyapatite nanoparticles. **2017**, 249, 64-69	16
813	Two-dimensional lateral GaN/SiC heterostructures: First-principles studies of electronic and magnetic properties. **2017**, 95,	13
812	Increasing the indium incorporation efficiency during InGaN layer growth by suppressing the dissociation of NH3. **2017**, 102, 35-39	8

811	CdS-Free p-Type Cu2ZnSnSe4/Sputtered n-Type In x Ga1⊠ N Thin Film Solar Cells. **2017**, 46, 1481-1487		
810	Efficient resonance energy transfer study from Ce 3+ to Tb 3+ in BaMgF 4. **2017**, 187, 233-244		22
809	Epitaxial Crystal Growth: Methods and Materials. **2017**, 1-1		11
808	LEDs for lighting: Basic physics and prospects for energy savings. **2017**, 18, 453-461		47
807	Effect of preparation conditions in sol-gel method on yellow phosphor with wide spectrum. **2017**, 7, 015208		3
806	Study on the band alignment of GaN/CH3NH3PbBr3 heterojunction by x-ray photoelectron spectroscopy. *Applied Physics Letters*, **2017**, 111, 122103	3.4	2
805	A broad-band orange-yellow-emitting Lu2Mg2Al2Si2O12: Ce3+ phosphor for application in warm white light-emitting diodes. **2017**, 7, 46713-46720		26
804	GAN-BASED PHOTODETECTORS. **2017**, 115-148		
803	Perspectives on Electronic and Photonic Materials. **2017**, 1-1		0
802	Enhanced DC-Operated Electroluminescence of Forwardly Aligned p/MQW/n InGaN Nanorod LEDs via DC Offset-AC Dielectrophoresis. **2017**, 9, 37912-37920		4
801	Highly Luminous and Thermally Stable Mg-Substituted CaMgSiO:Ce (0⊠x⊠1) Phosphor for NUV-LEDs. **2017**, 56, 12116-12128		19
800	In situ stress measurements during MOCVD growth of thick N-polar InGaN. **2017**, 122, 085303		4
799	Semiconductor Solid-Solution Nanostructures: Synthesis, Property Tailoring, and Applications. **2017** , 13, 1701998		49
798	The microstructure, local indium composition and photoluminescence in green-emitting InGaN/GaN quantum wells. **2017**, 268, 305-312		3
797	Growth study of self-assembled GaN nanocolumns on silica glass by plasma assisted molecular beam epitaxy. **2017**, 480, 67-73		16
796	Emission rate and internal quantum efficiency enhancement in different geometrical shapes of GaN LED. **2017**,		1
795	YScSiNC:Ce-A Broad Cyan-Emitting Phosphor To Weaken the Cyan Cavity in Full-Spectrum White Light-Emitting Diodes. **2017**, 56, 11087-11095		51
794	Recent Advances in Metal Halide-Based Perovskite Light-Emitting Diodes. **2017**, 5, 1734-1749		63

793	Enhanced photoluminescence property of single-component CaAlSiN3: Ce3+, Eu2+ multicolor phosphor through Ce3+-Eu2+ energy transfer. **2017**, 727, 633-641		12
792	Impact of carrier localization on recombination in InGaN quantum wells and the efficiency of nitride light-emitting diodes: Insights from theory and numerical simulations. *Applied Physics Letters*, **2017**, 111, 113501	3.4	44
791	Natural and Artificial Sources of Light. **2017**, 59-73		
790	Fabrication of Flexible White Light-Emitting Diodes from Photoluminescent Polymer Materials with Excellent Color Quality. **2017**, 9, 35279-35286		22
789	Understanding the links between composition, polyhedral distortion, and luminescence properties in green-emitting □Si6□AlzOzN8□:Eu2+ phosphors. **2017**, 5, 10039-10046		16
788	High temperature degradation mechanism of a red phosphor, CaAlSiN3:Eu for solid-state lighting. **2017**, 122, 113104		11
787	Bulk GaN substrate with overall dislocation density on the order of 105/cm2 fabricated by hydride vapor phase epitaxy. **2017**, 478, 123-128		20
786	Structural evolutions and significantly reduced thermal degradation of red-emitting Sr2Si5N8:Eu2+via carbon doping. **2017**, 5, 8927-8935		29
785	A comparative ab intio study on structural evolution, stability and electronic properties of undoped and Al-doped GaxNy (x + y = 4-25 clusters. **2017**, 132, 1		2
784	A potential white light emitting cubic ZrO2:Dy3+, Li+ nano phosphors for solid state lighting applications. **2017**, 192, 496-503		17
783	Surface optical phonon modes in hexagonal shaped Al0.97Ga0.03N nanostructures. **2017**, 123, 1		3
782	Adsorption of alkali-metal atoms on GaN nanowires photocathode. **2017**, 423, 829-835		49
781	Pretreatment by selective ion-implantation for epitaxial lateral overgrowth of GaN on patterned sapphire substrate. **2017**, 641, 2-7		2
780	Photo-reception properties of common LEDs. **2017**, 25, 222-228		11
779	Migration of Mg and other interstitial metal dopants in GaN. **2017**, 11, 1700081		9
778	A conceptual chemical process for the recycling of Ce, Eu, and Y from LED flat panel displays. **2017**, 126, 42-49		23
777	Tomographic Particle Image Velocimetry using Smartphones and Colored Shadows. **2017**, 7, 3714		21
776	Ga-Polar (In,Ga)N/GaN Quantum Wells Versus N-Polar (In,Ga)N Quantum Disks in GaN Nanowires: A Comparative Analysis of Carrier Recombination, Diffusion, and Radiative Efficiency. **2017**, 8,		8

775	Temperature dependent photoluminescence of Dy3+ doped LiCaBO3 phosphor. **2017**, 28, 17168-17176	16
774	III-Nitride Digital Alloy: Electronics and Optoelectronics Properties of the InN/GaN Ultra-Short Period Superlattice Nanostructures. **2017**, 7, 6671	22
773	Consistency on Two Kinds of Localized Centers Examined from Temperature-Dependent and Time-Resolved Photoluminescence in InGaN/GaN Multiple Quantum Wells. **2017**, 4, 2078-2084	15
772	III-Nitride Light-Emitting Diodes. **2017**, 1-21	
771	Room-Temperature Synthesis of GaN Driven by Kinetic Energy beyond the Limit of Thermodynamics. **2017**, 9, 41629-41633	11
770	Nanocomposite Phosphor Consisting of CaI:Eu Single Nanocrystals Embedded in Crystalline SiO. **2017**, 9, 41405-41412	2
769	Single layers and multilayers of GaN and AlN in square-octagon structure: Stability, electronic properties, and functionalization. **2017**, 96,	13
768	Differential optical gain in a GaInN/AlGaN quantum dot. **2017**, 38, 062001	
767	Accuracy of GW for calculating defect energy levels in solids. **2017**, 96,	17
766	Fabrication of AlGaN nanorods with different Al compositions for emission enhancement in UV range. **2017**, 28, 385205	13
765	Spectroscopic investigation of native defect induced electron□phonon coupling in GaN nanowires. **2017**, 50, 275103	9
764	Optoelectronic device physics and technology of nitride semiconductors from the UV to the terahertz. **2017**, 80, 106501	121
763	Characteristics and Properties of A(I,II)M(IV)F6 Fluoride Phosphors. **2017**, 371-398	
762	Comparative study of threading dislocations in GaN epitaxial layers by nondestructive methods. **2017**, 57, 32-38	10
761	Fringe field control of one-dimensional room temperature sub-band resolved quantum transport in site controlled AlGaN/GaN lateral nanowires. **2017**, 214, 1600620	5
760	Nitride Semiconductor Nanorod Heterostructures for Full-Color and White-Light Applications. **2017** , 96, 341-384	3
759	Luminescence properties of violet-blue emitting Ca2MgSi2O7:Ce3+ phosphor prepared by solid state reaction method. **2017**, 28, 381-393	3
758	Measurement of atomic electric fields and charge densities from average momentum transfers using scanning transmission electron microscopy. **2017**, 178, 62-80	77

757	Properties of Sr2.13Ba0.8SiO5:0.07Eu2+ phosphor synthesized by microwave assisted with SiC method. **2017**, 694, 340-344	
756	Emission enhancements in phosphor chips with surface gratings. **2017**, 181, 184-188	3
755	Design of Single-Phased Multicolor-Emission Phosphor for LED. **2017**, 459-508	2
754	Imaging the motion of electrons across semiconductor heterojunctions. **2017**, 12, 36-40	86
753	Effect of d-orbitals on the energy gap of group-III nitrides nanostructures. **2017**, 85, 324-333	4
752	Spectroscopic investigations of phosphate-borate-fluoride glass doped with Tb3+/Eu3+. **2017**, 457, 31-35	12
751	Electrical transport and thermoelectric properties of PbTe1□Ix synthesized by high pressure and high temperature. **2017**, 696, 161-165	15
750	Ultrafine Gd 2 O 2 S:Pr powders prepared via urea precipitation method using SO 2 /SO 4 2□as sulfuration agent□A comparative study. **2017**, 305, 382-388	10
749	Label-Free Biosensors Based on III-Nitride Semiconductors. **2017**, 59-102	3
748	Hydride-vapor-phase epitaxial growth of highly pure GaN layers with smooth as-grown surfaces on freestanding GaN substrates. **2017**, 56, 085503	57
747	Review□The Current and Emerging Applications of the III-Nitrides. **2017**, 6, Q149-Q156	45
746	Nanostructured GaN transistors. **2017**,	2
745	Achievements and perspectives of GaN based light emitting diodes: A critical review. **2017**,	2
744	Effect of InGaN thickness on assisted trap recombination and behaviour of InGaN/AlGaN double heterostructure LED. **2017**, 162, 01038	1
743	Temperature dependence of drain current transient response by gate pulse voltage in AlGaN / GaN high electron mobility transistors. **2017**,	2
742	The Effect of Spectral Quality on Daily Patterns of Gas Exchange, Biomass Gain, and Water-Use-Efficiency in Tomatoes and Lisianthus: An Assessment of Whole Plant Measurements. **2017**, 8, 1076	19
741	Aluminum-free nitride laser diodes: waveguiding, electrical and degradation properties. **2017**, 25, 33113	5
740	Optimization of nano-honeycomb structures for flexible w-LEDs. **2017**, 25, 20466-20476	1

739	Development of a high-power blue laser (445 nm) for material processing. **2017**, 42, 2251-2254	34
738	Electronic Properties of Rare-Earth Doped GaN. **2017**, 877, 012027	2
737	Investigation of a Simplified Mechanism Model for Prediction of Gallium Nitride Thin Film Growth through Numerical Analysis. **2017**, 7, 43	6
736	The Effect of Trimethylaluminum Flow Rate on the Structure and Optical Properties of AlInGaN Quaternary Epilayers. **2017**, 7, 69	2
735	Quantum DotIncorporated Hybrid Light-Emitting Diode. **2017**,	
734	Recent Developments in Applications of Quantum-Dot Based Light-Emitting Diodes. **2017**,	5
733	Solid-State Lighting. **2017**, 115-140	
732	AlN/GaN Digital Alloy for Mid- and Deep-Ultraviolet Optoelectronics. **2017**, 7, 11826	17
731	Characterization of Interface State Density of Ni/p-GaN Structures by Capacitance/Conductance-Voltage-Frequency Measurements. **2017**, 34, 097301	6
730	Organometallic Vapor Phase Epitaxial Growth of Group III Nitrides ?. **2017**,	
729	A Top-Down Approach for Fabrication of Nanorods on GaN-Based LEDs Using Self-Assembled Ni. **2018**, 171-176	1
728	Ab Initio-Aided Sensitizer Design for Mn4+-Activated Mg2TiO4 as an Ultrabright Fluoride-Free Red-Emitting Phosphor. **2018**, 30, 1769-1775	20
727	High quality self-separated GaN crystal grown on a novel nanoporous template by HVPE. **2018**, 8, 3166	7
726	Three-dimensional imaging of threading dislocations in GaN crystals using two-photon excitation photoluminescence. **2018**, 11, 031004	53
725	Phosphors Based on Phosphates of NaZr2(PO4)3 and Langbeinite Structural Families. **2018**, 8, 1-33	7
724	Nanostructuring Multilayer Hyperbolic Metamaterials for Ultrafast and Bright Green InGaN Quantum Wells. **2018**, 30, e1706411	33
723	Fundamentals, progress, and future directions of nitride-based semiconductors and their composites in two-dimensional limit: A first-principles perspective to recent synthesis. **2018**, 5, 011105	50
722	Organometal Halide Perovskites for Next Generation Fully Printed and Flexible LEDs and Displays. **2018**, 199-214	

721	Broad luminescence of Ce3+in multiple sites in (La,Ce,Y)6Si4S17. **2018**, 51, 135103		2
720	Impact of substrate temperature on magnetic properties of plasma-assisted molecular beam epitaxy grown (Ga,Mn)N. **2018**, 747, 946-959		13
719	Tunable Band Gaps of InxGa1□N Alloys: From Bulk to Two-Dimensional Limit. **2018**, 122, 6930-6942		23
718	Power-dependent photoluminescence in strained InxGa1□N/GaN multiple-quantum wells: Simulations of alloying and interface-specific effects. **2018**,		
717	Perspective: Toward efficient GaN-based red light emitting diodes using europium doping. **2018**, 123, 160901		66
716	Double-Polarity Selective-Area Growth of GaN by Metal-Organic Vapor-Phase Epitaxy Using Narrow-Pitch Patterns. **2018**, 255, 1700475		5
715	Unique Color Converter Architecture Enabling Phosphor-in-Glass (PiG) Films Suitable for High-Power and High-Luminance Laser-Driven White Lighting. **2018**, 10, 14930-14940		104
714	Codoping effects of the Zn acceptor on the structural characteristics and electrical properties of the Ge donor-doped GaN thin films and its hetero-junction diodes all made by reactive sputtering. **2018**, 82, 126-134		5
713	Synthesis, luminescence and application of BaKYSi2O7:Eu2+: A new blue-emitting phosphor for near-UV white-light LED. **2018**, 44, 8334-8343		25
712	Insertion of NiO electron blocking layer in fabrication of GaN□rganic heterostructures. **2018**, 57, 030303		
711	Formation of graphitic carbon nitride and boron carbon nitride film on sapphire substrate. **2018**, 57, 02CB09		10
710	Controlling surface property of K2SiF6:Mn4+ for improvement of lighting-emitting diode reliability. **2018**, 116, 118-125		14
709	Observation of Anisotropic Growth and Compositional Discontinuity in AlGaN Electron-Blocking Layers on GaN Microrods. **2018**, 18, 1593-1597		3
708	Tuning the Composition of Multicomponent Semiconductor Nanocrystals: The Case of I□I□VI Materials. **2018**, 30, 1446-1461		100
707	Adsorption of 3d transition metal atoms on graphene-like gallium nitride monolayer: A first-principles study. **2018**, 115, 108-115		22
706	Optical absorption edge broadening in thick InGaN layers: Random alloy atomic disorder and growth mode induced fluctuations. *Applied Physics Letters*, **2018**, 112, 032106	3.4	21
705	UV excitation band induced novel Na3Gd(VO4)2:RE3+ (RE3+□=□Eu3+ or Dy3+ or Sm3+) double vanadate phosphors for solid-state lightning applications. **2018**, 739, 218-226		44
704	Thermal conductivity of rare-earth scandates in comparison to other oxidic substrate crystals. **2018**, 738, 415-421		8

703	Structural and photoluminescence characteristics of Sm3+ activated RE2Ti2O7 (RE = Gd, La) as orange-red emitting phosphors. **2018**, 196, 326-336	19
702	Study of Gd-induced shift of luminescence spectra of YGAG:Ce micropowders as a function of grain size. **2018**, 196, 94-99	1
701	Invention, development, and status of the blue light-emitting diode, the enabler of solid-state lighting. **2018**, 19, 113-133	61
700	Application of a novel red-emitting cationic iridium(III) coordination polymer in warm white light-emitting diodes. **2018**, 76, 141-146	8
699	General Introduction. **2018**, 1-14	
698	A single-phased warm-white-emitting K3Y(PO4)2:Dy3+,Sm3+ phosphor with tuneable photoluminescence for near-UV-excited white LEDs. **2018**, 157, 72-79	31
697	Light quality in plant tissue culture: does it matter?. **2018**, 54, 195-215	65
696	Properties of GaN-based nanopillar-shaped crystals grown on a multicrystalline Si substrate. **2018**, 8, 015004	4
695	Photoluminescence properties of a ScBO:Cr phosphor and its applications for broadband near-infrared LEDs.. **2018**, 8, 12035-12042	127
694	The Study on the Droop Effect in the InGaN/AlGaInN MQWs With Lattice-Matched AlGaN/InGaN Superlattices Barrier by Highly Excited Photoluminescence Measurement. **2018**, 10, 1-9	3
693	Detection of deep-level defects and reduced carrier concentration in Mg-ion-implanted GaN before high-temperature annealing. **2018**, 8, 025310	9
692	Carrier confinement effects of In Ga1-N/GaN multi quantum disks with GaN surface barriers grown in GaN nanorods. **2018**, 78, 365-369	3
691	Characterization of quaternary Zn/Sn-codoped GaN films obtained with Zn x Sn0.04GaN targets at different Zn contents by the RF reactive magnetron sputtering technology. **2018**, 53, 9099-9106	2
690	Electrical characteristics of n-GaN Schottky contacts on cleaved surfaces of free-standing substrates: Metal work function dependence of Schottky barrier height. **2018**, 57, 04FG13	14
689	Induction-heating MOCVD reactor with significantly improved heating efficiency and reduced harmful magnetic coupling. **2018**, 488, 16-22	4
688	Recent advances in rare earth doped alkali-alkaline earth borates for solid state lighting applications. **2018**, 535, 106-113	20
687	Synthesis and luminescence properties of Ca5-(PO4)3Br: xEu2+A novel blue-emitting bromapatite phosphor for near-ultraviolet-pumped white light-emitting diodes. **2018**, 154, 383-392	1
686	(Ln 3+ = Eu 3+ /Dy 3+ /Dy 3+ , Eu 3+) doped NaGd(MoO 4) 2 phosphors with uniform morphologies: Hydrothermal synthesis, luminescent properties, energy transfer and color tunable emission. **2018**, 195, 170-175	17

685	Facile synthesis of thermally stable CsPbBr3 perovskite quantum dot-inorganic SiO2 composites and their application to white light-emitting diodes with wide color gamut. **2018**, 149, 246-252	66
684	Controlling Surface Morphology and Circumventing Secondary Phase Formation in Non-polar m-GaN by Tuning Nitrogen Activity. **2018**, 47, 359-367	1
683	Review☐Phosphor Plates for High-Power LED Applications: Challenges and Opportunities toward Perfect Lighting. **2018**, 7, R3134-R3147	92
682	Structural properties and self-activated photoluminescence emissions in hydroxyapatite with distinct particle shapes. **2018**, 44, 236-245	21
681	Combined angle-resolved X-ray photoelectron spectroscopy, density functional theory and kinetic study of nitridation of gallium arsenide. **2018**, 427, 662-669	10
680	Synthesis of high quality Ce:YAG nanopowders by graphene oxide nanosheet-assisted co-precipitation method. **2018**, 36, 130-134	7
679	Effect of fluxes on synthesis and luminescence properties of BaSi2O2N2:Eu2+ oxynitride phosphors. **2018**, 36, 225-230	14
678	Anisotropic Fracture Toughness of Bulk GaN. **2018**, 255, 1700515	5
677	Luminescence properties of phosphate phosphors Ba 3 Gd 1☒ (PO 4) 3 : x Sm 3+. **2018**, 36, 456-460	14
676	Warm white light-emitting diodes using organic☐inorganic halide perovskite materials coated YAG:Ce3+ phosphors. **2018**, 44, 3868-3872	17
675	White phosphor using Yb3+-sensitized Er3+-and Tm3+-doped sol-gel derived lead-fluorosilicate transparent glass ceramic excited at 980 nm. **2018**, 75, 733-738	8
674	Effect of indium droplets on growth of InGaN film by molecular beam epitaxy. **2018**, 113, 650-656	7
673	The Limits of Transmittance of an Interface and Their Effects on Light Extraction. **2018**, 7, R3016-R3022	1
672	GaN nanophosphors for white-light applications. **2018**, 75, 61-67	6
671	Influences of growth parameters on the reaction pathway during GaN synthesis. **2018**, 482, 44-55	3
670	Effect of Insertion of Ultrathin Al2O3 Interlayer at Metal/GaN Interfaces. **2018**, 255, 1700382	5
669	Color-tunable photoluminescence and energy transfer of (Tb Mn)Al(Al Si)O:Ce solid solutions for white light emitting diodes.. **2018**, 8, 36056-36062	11
668	Differences in Morphologies of GaN-Based Nanocrystals Grown on Metal-Foils and Multi-Crystalline Si Substrates. **2018**, 941, 2109-2114	

667	Breakdown-induced conductive channel for III-nitride light-emitting devices. **2018**, 8, 16547	3
666	What is red? On the chromaticity of orange-red InGaN/GaN based LEDs. **2018**, 124, 183102	18
665	Mechanism of leakage current increase in p-GaN gate AlGaN/GaN power devices induced by ON-state gate bias. **2018**, 57, 124101	8
664	Bright and Blue Nanocrystal Emitters. **2018**, 2, 2199-2201	4
663	Square Column Structure of High Efficiency, Reliable, Uniformly Flexible LED Devices. **2018**, 8, 472	3
662	First-principles calculations of optoelectronic properties of CaO: Eu+2 (SrO: Eu+2) for energy applications. **2018**, 32, 1850333	5
661	Directional light emission enhancement from LED-phosphor converters using dielectric Vogel spiral arrays. **2018**, 3, 126103	14
660	Novel Method for Estimating Phosphor Conversion Efficiency of Light-Emitting Diodes. **2018**, 8, 442	5
659	Fabrication of GaN single crystals at 700°C using Na-Li-Ca mixed flux system. **2018**, 8, 055326	4
658	Processing and Property Characterization of Zn Acceptor/Sn Donor Codoped Gallium Nitride Films Prepared by Reactive Sputtering with a Cermet Target. **2018**, 47, 7420-7428	1
657	Unambiguous Identification of Carbon Location on the N Site in Semi-insulating GaN. **2018**, 121, 145505	27
656	Nurturing transformative U.S. energy research: Two guiding principles. **2018**, 5, 1	1
655	Effect of elevated CO2 and spectral quality on whole plant gas exchange patterns in tomatoes. **2018**, 13, e0205861	16
654	Control of Narrow-Band Emission in Phosphor Materials for Application in Light-Emitting Diodes. **2018**, 3, 2573-2586	76
653	Crystal growth and spectral properties of Tb:Lu 2 O 3. **2018**, 27, 097801	2
652	Anomalous electroluminescent blue-shift behavior induced by well widths variance and localization effect in InGaN/GaN multi-quantum wells. **2018**, 26, 21736-21744	9
651	High luminous fluorescence generation using Ce:YAG transparent ceramic excited by blue laser diode. **2018**, 8, 2760	35
650	Surface Plasmon Resonance Optical Sensor: A Review on Light Source Technology. **2018**, 8,	158

649	Integrating AlInN interlayers into InGaN/GaN multiple quantum wells for enhanced green emission. *Applied Physics Letters*, **2018**, 112, 201106	3.4	23
648	Transparent, crystalline ZnO thin films: Effect of spin coating parameters on the structural and optical properties. **2018**,		1
647	Kinetically controlled indium surface coverage effects on PAMBE-growth of InN/GaN(0001) quantum well structures. **2018**, 123, 195302		2
646	59-2: Invited Paper: Ultra-Fine Pitch Thin-Film Micro LED Display for Indoor Applications. **2018**, 49, 782-785		14
645	Temperature dependent Cr3+ photoluminescence in garnets of the type X3Sc2Ga3O12 (X = Lu, Y, Gd, La). **2018**, 202, 523-531		101
644	Shape Evolution of Highly Lattice-Mismatched InN/InGaN Nanowire Heterostructures. **2018**, 47, 966-972		1
643	Charge Transfer in Molecular Materials. **2018**, 1-31		3
642	Two-step synthesis of a novel red-emitting Ba2ZrF8:Mn4+ phosphor for warm white light-emitting diodes. **2018**, 107, 242-247		14
641	Mechanism for the formation of nitrogen-filled voids after annealing of GaN on a sapphire substrate. **2018**, 124, 045304		2
640	Sr4Y6(AlO4)x(SiO4)6-xO�Eu2+: A novel apatite structure blue-green emitting phosphor. **2018**, 44, 19900-19906		9
639	Tuning the correlated color temperature of white light-emitting diodes resembling Planckian locus. **2018**, 26, A136-A143		15
638	Fabrication and optical characterization of GaN waveguides on (�01)-oriented �Ga_2O_3. **2018**, 8, 88		10
637	Light extraction efficiency enhancement of flip-chip blue light-emitting diodes by anodic aluminum oxide. **2018**, 9, 1602-1612		8
636	III-nitride nanowires on unconventional substrates: From materials to optoelectronic device applications. **2018**, 61, 1-31		45
635	Fabrication and performance assessment of coprecipitation-based YAG:Ce nanopowders for white LEDs. **2018**, 199, 24-30		5
634	Optical and Thermal Performances of (Ga,In)N/GaN Light Emitting Diodes Transferred on a Flexible Tape. **2018**, 30, 1567-1570		4
633	Efficiency droop in GaInN/GaN LEDs. **2018**, 299-325		6
632	Engineered Nanomaterial in Electronics and Electrical Industries. **2018**, 324-364		10

631	Nonpolar and semipolar LEDs. **2018**, 273-295		3
630	Silicate conductive filament assisted broadband light emission of HfO2 high-k solid state incandescent devices. **2018**, 6, 7913-7919		2
629	Energy band engineering of InGaN/GaN multi-quantum-well solar cells via AlGaN electron- and hole-blocking layers. *Applied Physics Letters*, **2018**, 113, 043501	3.4	12
628	Preparation and Photo luminescent Properties of Sr2Si5N8: Eu2+Red Phosphors for White Light-Emitting Diodes. **2018**, 170, 042114		1
627	Controlled Morphology, Improved Photoluminescent Properties, and Application of an Efficient Non-rare Earth Deep Red-Emitting Phosphor. **2018**, 57, 9892-9901		40
626	Probing the Internal Atomic Charge Density Distributions in Real Space. **2018**, 12, 8875-8881		24
625	Polarization-Selecting III-Nitride Elliptical Nanorod Light-Emitting Diodes Fabricated with Nanospherical-Lens Lithography. **2018**, 12, 8748-8757		8
624	Hot electron transport in wurtzite-GaN: effects of temperature and doping concentration. **2018**, 39, 072002		1
623	Evaluation of lattice curvature and crystalline homogeneity for 2-inch GaN homo-epitaxial layer. **2018**, 8, 075318		2
622	Lattice-plane orientation mapping of homo-epitaxial GaN(0001) thin films via grazing-incidence X-ray diffraction topography in 2-in. wafer. **2018**, 11, 081002		8
621	Synthesis and Luminescence Properties of CaGd2(MoO4)4:Dy3+, Eu3+, Tm3+ Phosphors for Warm White UV LEDs. **2018**, 47, 6210-6220		4
620	Novel high color purity and thermally stable Eu3+ ions activated Ba2Gd5B5O17 red emitting phosphor for near-UV based WLEDs. **2018**, 84, 312-317		15
619	Growth Temperature Dependence of Morphology of GaN Single Crystals in the Na-Li-Ca Flux Method. **2018**, 47, 1569-1574		4
618	Synthesis of K2SiF6:Mn4+ phosphor for LED lamp. **2018**,		1
617	Growth of GaN Layers on Si(111) Substrates by Plasma-Assisted Molecular Beam Epitaxy. **2018**, 52, 660-663		3
616	Activation of buried p-GaN in MOCVD-regrown vertical structures. *Applied Physics Letters*, **2018**, 113, 062105	3.4	25
615	Phosphors for white LEDs. **2018**, 123-208		4
614	Effect of the built-in electric field on electron Raman scattering of parabolic InxGa1�N/GaN quantum dot. **2018**, 56, 1894-1902		1

613	Nano-imaging of intersubband transitions in van der Waals quantum wells. **2018**, 13, 1035-1041	45
612	Crack-free GaN-based ultraviolet multiple quantum wells structures grown on AlN/2□misoriented sapphire template. **2018**, 663, 44-48	2
611	Low-temperature and global epitaxy of GaN on amorphous glass substrates by molecular beam epitaxy via a compound buffer layer. **2018**, 662, 174-179	9
610	Luminescent properties of Eu-doped calcium aluminosilicate glass-ceramics: A potential tunable luminophore. **2018**, 85, 41-47	10
609	Enhancing the electroluminescence of OLEDs by using ZnO nanoparticle electron transport layers that exhibit the Auger electron effect. **2018**, 663, 61-70	9
608	Monolayer Transition Metal Dichalcogenides as Light Sources. **2018**, 30, e1707627	46
607	An Historical Survey on Light Technologies. **2018**, 6, 25881-25897	8
606	Introduction. **2018**, 1-5	
605	Assembled Lanthanide Complexes with Advanced Photophysical Properties. **2018**,	2
604	Efficient blue light-emitting diodes based on quantum-confined bromide perovskite nanostructures. **2019**, 13, 760-764	313
603	Fabrication and Characterization of GaN-Based Micro-LEDs on Silicon Substrate*. **2019**, 36, 088501	0
602	Stabilizing Fluoride Phosphors: Surface Modification by Atomic Layer Deposition. **2019**, 31, 7192-7202	24
601	YAGG:Ce transparent ceramics with high luminous efficiency for solid-state lighting application. **2019**, 8, 389-398	27
600	Selective area growth of GaN nanowires on Si(1 1 1) substrate with Ti masks by molecular beam epitaxy. **2019**, 524, 125181	1
599	Reuse of ScAlMgO4 substrates utilized for halide vapor phase epitaxy of GaN. **2019**, 58, SC1023	9
598	Impact of low-temperature annealing on defect levels generated by Mg-ion-implanted GaN. **2019**, 58, SCCB10	5
597	Effects of three-dimensional strain distribution on the performance of GaN-based light-emitting diodes on patterned sapphire substrates. **2019**, 58, SC1036	2
596	High-quality GaN crystals grown from double-polarity hydride vapor phase epitaxy and single-polarization regrowth. **2019**, 58, SC1019	

595	Growth of GaN and improvement of lattice curvature using symmetric hexagonal SiO2 patterns in HVPE growth. **2019**, 58, SC1049	3
594	Intensive luminescence from a thick, indium-rich In0.7Ga0.3N film. **2019**, 58, 065503	0
593	Enhancing the luminescent efficiency of Y3Al5O12:Ce3+ by coating graphitic carbon nitride: Toward white light-emitting diodes. **2019**, 801, 10-18	26
592	Enhanced UV light induced photocatalytic degradation of Methyl Orange by Fe doped spray pyrolysis deposited ZnO thin films. **2019**, 494, 116-123	14
591	Kinetic Monte Carlo Simulation of the Growth of AlN Films by Metal Organic Chemical Vapor Deposition. **2019**, 256, 1900114	1
590	The self-compensation effect of heavily Mg doped p-GaN films studied by SIMS and photoluminescence. **2019**, 133, 106177	3
589	Electrodeless photo-assisted electrochemical etching of GaN using a H3PO4-based solution containing S2O8 2□ions. **2019**, 12, 066504	10
588	The Future Is Blue (LEDs): Why Chemistry Is the Key to Perovskite Displays§. **2019**, 31, 6003-6032	55
587	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. **2019**, 6, 1963-1971	16
586	A red-emitting Mn4+ activated phosphor with controlled morphology and two-dimensional luminescence nanofiber film: Synthesis and application for high-performance warm white light-emitting diodes (WLEDs). **2019**, 808, 151551	11
585	Nanophosphors-Based White Light Sources. **2019**, 9,	7
584	Cathodoluminescence and scanning transmission electron microscopy study of InGaN/GaN quantum wells in core-shell GaN nanowires. **2019**, 12, 085003	7
583	Determining colour coordinates of colourful light generated by three laser sources. **2019**, 1191, 012004	
582	Color tunable emission from single-phased Ba2CaZn2Si6O17: Bi3+, Eu3+ phosphors with good energy transfer efficiency for white light emitting diodes. **2019**, 215, 116649	7
581	Tunable emission and energy-transfer mechanism of single-phase Na3Y(PO4)2:Ce3+, Mn2+phosphors for white LEDs. **2019**, 215, 116651	4
580	A computational survey of semiconductors for power electronics. **2019**, 12, 3338-3347	13
579	Lattice restraint induced ultra-large bandgap widening of ZnO nanoparticles. **2019**, 7, 8969-8974	7
578	Experimental Evidence of Large Bandgap Energy in Atomically Thin AlN. **2019**, 29, 1902608	15

577	Study of luminescence properties of dysprosium-doped CaAl O phosphor for white light-emitting diodes. **2019**, 34, 804-811	3
576	Performance enhancement of UV quantum well light emitting diode through structure optimization. **2019**, 51, 1	10
575	Studies on CdSe/PVK nanocomposites films for electroluminescent display applications. **2019**, 97, 109319	5
574	. **2019**, 66, 4817-4822	10
573	Blue emission from Sr0.98Ga2B2O7: 0.01Bi3+, 0.01Dy3+ phosphor with high quantum yield. **2019**, 810, 151849	9
572	TEM study of GaN-based nanopillar-shaped-crystals grown on a multicrystalline Si substrate. **2019**, 58, 068009	2
571	Design and Fabrication of Micro LEDs for High Data Rate LiFi Communications. **2019**,	0
570	Al2O3-Ce:Tb3Al5O12 composite ceramic phosphors for high efficiency warm white light illumination. **2019**, 97, 109384	3
569	A review of blue light emitting diodes for future solid state lighting and visible light communication applications. **2019**, 136, 106294	9
568	Nitride Semiconductors. **2019**, 109-147	1
567	Structural, vibrational and dielectric properties of Sr2SiO4:Eu2+, Dy3+. **2019**,	
566	Luminescence and Tm3+-to-Dy3+ energy transfer in TeO2:ZnO glass under NIR/UV excitation. **2019**, 215, 116706	12
565	Computational Study of Electronic Structure Rare-Earth Doped Semiconductor III-V: GGA Approximation. **2019**, 1175, 012090	
564	Preparation of gallium nitride from gallium□magnesium alloy powders. **2019**, 35, 1950-1955	
563	Lattice-Mismatched PbTe/ZnTe Heterostructure with High-Speed Midinfrared Photoresponses. **2019**, 11, 39342-39350	8
562	High-performance flat-type InGaN-based light-emitting diodes with local breakdown conductive channel. **2019**, 9, 13654	6
561	Emerging Perovskite Nanocrystals-Enhanced Solid-State Lighting and Liquid-Crystal Displays. **2019**, 9, 59	47
560	InAlN underlayer for near ultraviolet InGaN based light emitting diodes. **2019**, 12, 034002	23

559	Theoretical optimization of inhomogeneous broadening in InGaN/GaN MQWs to polariton splitting at low temperature. **2019**, 128, 151-156	3
558	Growth of high-quality GaN crystals on a BCN nanosheet-coated substrate by hydride vapor phase epitaxy. **2019**, 21, 1302-1308	4
557	Facile in situ synthesis of zeolite-encapsulating Cs2SiF6:Mn4+ for application in WLEDs. **2019**, 7, 1345-1352	13
556	Silica encapsulated LuAG:Pr3+ nanocrystals by surfactant assisted co-precipitation and microwave calcination: Structural, growth mechanism, photoluminescence and thermoluminescence properties. **2019**, 233, 296-309	5
555	Solid State Multicolor Emission in Substitutional Solid Solutions of Metal-Organic Frameworks. **2019**, 141, 11298-11303	44
554	Effect of annealing on the photocatalytic activity of chemically prepared TiO2 thin films under visible light. **2019**, 193, 163006	5
553	Tuning the optoelectronic properties of graphene-like GaN via adsorption for enhanced optoelectronic applications. **2019**, 296, 26-31	8
552	Correlation of Optical, Structural, and Compositional Properties with V-Pit Distribution in InGaN/GaN Multiquantum Wells. **2019**, 11, 22834-22839	5
551	Temperature-dependent cathodoluminescence mapping of InGaN epitaxial layers with different In compositions. **2019**, 58, SCCB13	
550	Observation of sharp emission lines from Zn-doped GaN. **2019**, 58, SCCB15	
549	First-principles study of two-dimensional bilayer GaN: structure, electronic properties and temperature effect. **2019**, 58, SCCB35	2
548	Growth process of molybdenum disulfide thin films grown by thermal vapour sulfurization. **2019**, 30, 10419-10426	2
547	Optical properties of InN/GaN quantum dot superlattice by changing dot size and interdot spacing. **2019**, 13, 102246	6
546	Performance Improvement of GaN Based Laser Diode Using Pd/Ni/Au Metallization Ohmic Contact. **2019**, 9, 291	6
545	Enhanced Performance of InGaN-Based Blue LEDs Using an AlGaN/InGaN Super-Lattice Last Quantum Barrier. **2019**, 216, 1800913	1
544	Improving the moisture resistance and luminescent properties of K2TiF6:Mn4+ by coating with CaF2. **2019**, 115, 98-104	19
543	Blue Emission of □GaN Colloidal Quantum Dots via Zn Doping. **2019**, 31, 5370-5375	6
542	Long time aging effect on Be-implanted GaN epitaxial layer. **2019**, 9, 055209	1

541	GaN crystals growth in the Na-Li-Ca flux by liquid phase epitaxy (LPE) technique. **2019**, 521, 30-33	6
540	Light-output enhancement of InGaN light emitting diodes regrown on nanoporous distributed Bragg reflector substrates. **2019**, 58, SCCC14	5
539	A high-sensitivity compact gas concentration sensor using ultraviolet light absorption with a heating function for a high-precision trimethyl aluminum gas supply system. **2019**, 58, SBBL04	2
538	Characterization of non-uniform InGaN alloys: spatial localization of carriers and optical properties. **2019**, 58, SCCC03	2
537	Electronic Structure and Impurity Level Location of Rare-Earth (Ce, Pr, Nd, Dy) Doped GaN : GGA Approximation. **2019**, 1127, 012029	1
536	Prevailing Strategies to Tune Emission Color of Lanthanide-Activated Phosphors for WLED Applications. **2019**, 7, 1900319	81
535	Bulk- and Nanocrystalline-Halide Perovskite Light-Emitting Diodes. **2019**, 305-341	2
534	Coexistence of doping and strain to tune electronic and optical properties of GaN monolayer. **2019**, 130, 93-102	9
533	Effect of off-angle of stripe patterns on facet stability and embedding in selective-area hydride vapor phase epitaxy growth. **2019**, 58, SC1001	
532	Length-controlled and selective growth of individual indium nitride nanowires by localized laser heating. **2019**, 12, 056501	3
531	Incubation effect during laser micromachining of GaN films with femtosecond pulses. **2019**, 30, 16821-16826	2
530	High-Performance WS Monolayer Light-Emitting Tunneling Devices Using 2D Materials Grown by Chemical Vapor Deposition. **2019**, 13, 4530-4537	34
529	The emergence and prospects of deep-ultraviolet light-emitting diode technologies. **2019**, 13, 233-244	458
528	Large scale N-doped GNTs@a-SiOx(x=1▯)NPs: template-free one-step synthesis, and field emission and photoluminescence properties. **2019**, 7, 3756-3764	2
527	Carbon in GaN: Calculations with an optimized hybrid functional. **2019**, 99,	24
526	Versatile Crystal Structures and (Opto)electronic Applications of the 2D Metal Mono-, Di-, and Tri-Chalcogenide Nanosheets. **2019**, 29, 1900040	37
525	Electrical Polarization in AlN/GaN Nanodisks Measured by Momentum-Resolved 4D Scanning Transmission Electron Microscopy. **2019**, 122, 106102	17
524	Intrinsic White-Light-Emitting Metal▯rganic Frameworks with Structurally Deformable Secondary Building Units. **2019**, 131, 7900-7904	6

523	Intrinsic White-Light-Emitting Metal-Organic Frameworks with Structurally Deformable Secondary Building Units. **2019**, 58, 7818-7822	54
522	Blue laser diode-pumped Ce:YAG phosphor-coated cylindrical rod-based extended white light source with uniform illumination. **2019**, 29, 056203	9
521	Influence of polymerization among Al- and Ga-containing molecules on growth rate and Al content in AlGaN. **2019**, 516, 17-20	6
520	Structure dependence of GaN-based nanopillar-shaped crystals grown on a quartz glass substrate on their growth conditions. **2019**, 125, 1	1
519	A Novel Polymethyl Methacrylate Derivative Grafted with Cationic Iridium(III) Complex Units: Synthesis and Application in White Light-Emitting Diodes. **2019**, 11,	3
518	Sb-doped p-ZnO quantum dots: Templates for ZnO nanorods homojunction white light-emitting diodes by low-temperature solution process. **2019**, 480, 122-130	19
517	Spin Polarization and Magnetic Properties of VGaON and VGaONInGa in GaN: GGA+U Approach. **2019**, 32, 2661-2672	
516	Blue-green light-emitting diode with patterned electrode: Spectral analysis. **2019**, 212, 37-41	1
515	Preparation and photoluminescence of novel LaCa(SiPON)O oxynitride phosphors containing Eu/Ce/Tb ions. **2019**, 48, 3028-3037	22
514	Influence of Orientation of a Silicon Substrate with a Buffer Silicon Carbide Layer on Dielectric and Polar Properties of Aluminum Nitride Films. **2019**, 61, 2386-2391	7
513	First-Principle Electronic Properties of Monoclinic (AlxInyGa1-x-y)2O3 Alloys. **2019**,	
512	Brief review on the physics of solid-state lighting device. **2019**, 1378, 022038	1
511	Nanorod Array Structure Through a Nanomolding Process for Semiconductor Lighting and Display Applications. **2019**, 14, 1950153	1
510	Increased Radiative Recombination in Nitride Laser Diodes with Inverse Tapered Electron Blocking Layer. **2019**,	0
509	Fabrication of Pyramid Structure Substrate Utilized for Epitaxial Growth Free-Standing GaN. **2019**, 9, 547	2
508	Influence of annealing conditions on the structure and luminescence properties of KGd1□Eux(MoO4)2 (0⁄□x⁄□1). **2019**, 21, 6460-6471	4
507	Deep-ultraviolet integrated photonic and optoelectronic devices: A prospect of the hybridization of group III□itrides, III□xides, and two-dimensional materials. **2019**, 40, 121801	17
506	Fabrication of Less Bowed Light-Emitting Diodes on Sapphire Substrates with a SiO2 Thin Film on Their Back Sides. **2019**, 75, 480-484	1

505	Engineering Monoclinic (AlxInyGa1-x-y)2O3 for Ultraviolet Photodetector. **2019**,		
504	Crowd-sourcing materials-science challenges with the NOMAD 2018 Kaggle competition. **2019**, 5,		22
503	Thermal boundary resistance predictions with non-equilibrium Green's function and molecular dynamics simulations. *Applied Physics Letters*, **2019**, 115, 231601	3.4	7
502	Room-temperature synthesis, optimized photoluminescence and warm-white LED application of a highly efficient non-rare-earth red phosphor. **2019**, 775, 1365-1375		21
501	Development of LED-based standard source for total luminous flux calibration. **2019**, 51, 870-882		3
500	. **2019**, 55, 1-4		6
499	Deep-Ultraviolet Biomolecular Imaging and Analysis. **2019**, 7, 1801099		17
498	Dehydrogenation-driven to synthesize high-performance Lu2Si4N6C:Ce3+- a broad green-emitting phosphor for full-spectrum lighting. **2019**, 783, 855-862		11
497	Enhancing the performance of GaN based LDs by using low In content InGaN instead of GaN as lower waveguide layer. **2019**, 111, 810-813		5
496	Synthesis and Luminescence Properties of CsPbX@Uio-67 Composites toward Stable Photoluminescence Convertors. **2019**, 58, 1690-1696		45
495	Room Temperature Bonding on Interface Between Metal and Ceramic. **2019**, 48, 72-78		2
494	Intensity-Stabilized LEDs With Monolithically Integrated Photodetectors. **2019**, 66, 7426-7432		25
493	Coordination of Fe to Eugenol to Engineer Self-Assembled Emulsions by Rice Proteins for Iron Fortification. **2019**, 84, 276-283		7
492	Light-Emitting Diodes. **2019**,		3
491	Effective n-type doping of Mg3Sb2 with group-3 elements. **2019**, 125, 025105		29
490	Nitride Nanowires for Light Emitting Diodes. **2019**, 425-484		5
489	Technology and Droop Study for High Internal Quantum Efficiency. **2019**, 281-310		2
488	Synthesis and photoluminescence properties of high-efficiency BaGd2Si3O10:Eu3+ red phosphors for WLEDs and display device applications. **2019**, 30, 4196-4202		6

487	The mechanism of N-vacancy defects self-activated light emitting based on CaMg2N2. **2019**, 208, 388-393	5
486	Mechanical and electronic properties under high pressure on ternary AlGaN and InGaN compounds□ first-principles perspective. **2019**, 6, 015052	12
485	Intense broad-band absorption and blue-emitting Ca9La(PO4)5(SiO4)Cl2:Eu2+ phosphor under near-ultraviolet excitation. **2019**, 206, 154-157	16
484	Structural determination of europium-incorporated Mo2C microrods and photoluminescence studies. **2019**, 157, 416-419	3
483	Luminescent properties of new red emitting fluoborate based phosphors, Na3Ba2-xB6O12F:xEu3+. **2019**, 179, 427-433	2
482	Luminescence properties of Li2SrSiO4:Eu2+ silicate yellow phosphors with high thermal stability for high-power efficiency white LED application. **2019**, 207, 22-28	29
481	Luminescence properties of color tunable new garnet structure (Lu1-xMnx)3Al2(Al1-xSix)3O12: Ce3+ solid solution phosphors. **2019**, 207, 98-104	21
480	Snoring and breathing pauses during sleep: interview survey of a United Kingdom population sample reveals a significant increase in the rates of sleep apnoea and obesity over the last 20 years - data from the UK sleep survey. **2019**, 54, 250-256	10
479	Valance band properties of MgZnO thin films with increasing Mg content; phase separation effects. **2019**, 6, 036402	2
478	Study of SiC buffer layer thickness influence on photovoltaic properties of n-GaN NWs/SiC/p-Si heterostructure. **2019**, 90, 20-25	5
477	Homo-epitaxial growth of high crystal quality GaN thin films by plasma assisted□olecular beam epitaxy. **2019**, 506, 30-35	4
476	Gallium nitride. **2019**, 351-399	2
475	From the absolute surface energy to the stabilization mechanism of high index polar surface in wurtzite structure: The case of ZnO. **2019**, 772, 482-488	5
474	Early history of MOVPE reactor development. **2019**, 506, 190-200	4
473	Multiple Color Inorganic Thin-Film Phosphor, RE-Doped Amorphous Gallium Oxide (RE = Rare Earth: Pr, Sm, Tb, and Dy), Deposited at Room Temperature. **2019**, 216, 1700833	11
472	The influence of second coordination-sphere interactions on the luminescent properties of □Ca3(PO4)2-related compounds. **2020**, 815, 152352	14
471	First-principles study on the electronic structures and optical properties of RbVO3. **2020**, 218, 116832	3
470	Filter-Bank Modulation Based Signal Design and Transmission Techniques for Intensity Modulated MIMO Visible Light Communication Systems. **2020**, 111, 1129-1150	3

469	Electronic surface, optical and electrical properties of p GaN activated via in-situ MOCVD and ex-situ thermal annealing in InGaN/GaN LED. **2020**, 106, 104757		
468	High-Frequency GaN Electronic Devices. **2020**,		12
467	III-Nitride Tunneling Hot Electron Transfer Amplifier (THETA). **2020**, 109-157		0
466	Modulation of electronic structure properties of C/B/Al-doped armchair GaN nanoribbons. **2020**, 118, e1656833		3
465	Effects of Dosage Increase on Electrical Properties of Metal-Oxide-Semiconductor Diodes with Mg-Ion-Implanted GaN Before Activation Annealing. **2020**, 257, 1900367		5
464	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. **2020**, 217, 1900729		3
463	Suppression the formation of V-pits in InGaN/ GaN multi-quantum well growth and its effect on the performance of GaN based laser diodes. **2020**, 822, 153571		7
462	Combining experiment and computation to elucidate the optical properties of Ce in BaSiO. **2020**, 22, 2327-2336		8
461	Broadened Bandwidth Amplified Spontaneous Emission from Blue GaN-Based Short-Cavity Superluminescent Light-Emitting Diodes. **2020**, 9, 015019		5
460	Strain effect on the orientation-dependent harmonic spectrum of monolayer aluminum nitride. **2020**, 63, 1		30
459	Structural and Optical Properties of GaN Film on Copper and Graphene/Copper Metal Foils Grown by Laser Molecular Beam Epitaxy. **2020**, 20, 3929-3934		6
458	First-principle investigation of monoclinic (Al x In y Ga1xy)2O3 quaternary alloys. **2020**, 35, 025023		6
457	Achieving homogeneity of InGaN/GaN quantum well by well/barrier interface treatment. **2020**, 505, 144283		9
456	Light-emitting devices. **2020**, 175-197		
455	Novel Siloxane-Modified Epoxy Resins as Promising Encapsulant for LEDs. **2019**, 12,		2
454	Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. **2020**, 127, 013102		4
453	Van der Waals Epitaxy of III-Nitrides and Its Applications. **2020**, 13,		2
452	Room-temperature operation of c-plane GaN vertical cavity surface emitting laser on conductive nanoporous distributed Bragg reflector. *Applied Physics Letters*, **2020**, 117, 011101	3.4	11

451	Cu2O as hole injection layer on In-rich InGaN nanowires. **2020**, 128, 025304		4
450	Novel Radiation Device for Application in the UV-A and UV-B Range. **2020**, 9, 065012		0
449	Quantifying Exciton Heterogeneities in Mixed-Phase Organometal Halide Multiple Quantum Wells via Stark Spectroscopy Studies. **2020**, 12, 52538-52548		7
448	Epitaxy from a Periodic Y-O Monolayer: Growth of Single-Crystal Hexagonal YAlO Perovskite. **2020**, 10,		
447	Bottom tunnel junction blue light-emitting field-effect transistors. *Applied Physics Letters*, **2020**, 117, 031107	3.4	2
446	Progress in Modeling of III-Nitride MOVPE. **2020**, 66, 100486		5
445	Simulating random alloy effects in III-nitride light emitting diodes. **2020**, 128, 041102		9
444	Luminescence color tuning of Ce3+ and Tb3+ co-doped Ca2YZr2Al3O12 phosphors with high color rendering index via energy transfer. **2020**, 228, 117557		6
443	Optimization of Ce3+ concentration and Y4MgSi3O13 phase in Mg2+-Si4+ Co-doped Ce: YAG ceramic phosphors. **2020**, 103, 6453-6460		2
442	Mapping Inversion Domain Boundaries along Single GaN Wires with Bragg Coherent X-ray Imaging. **2020**, 14, 10305-10312		4
441	Comprehensive Analysis of Metal Modulated Epitaxial GaN. **2020**, 12, 37693-37712		10
440	Structural and luminescence properties of GaN nanowires grown on Si substrate by Au catalyst. **2020**, 3, 591-594		1
439	Light emitting diodes (LEDs) in fluorescence-based analytical applications: a review. **2020**, 1-38		6
438	Structural Engineering of Eu2+-Doped Silicates Phosphors for LED Applications. **2020**, 1, 137-145		59
437	Photoluminescent transparent ceramics with an adjustable spectrum for high-color rendering laser lighting. **2020**, 8, 16483-16488		6
436	Highly spatially resolved mapping of the piezoelectric potentials in InGaN quantum well structures by off-axis electron holography. **2020**, 128, 155704		3
435	GaN-Based Materials. **2020**, 41-98		
434	Identifying domains of applicability of machine learning models for materials science. **2020**, 11, 4428		29

433	Elimination of the internal electrostatic field in two-dimensional GaN-based semiconductors. **2020**, 4,		11
432	. **2020**,		9
431	Luminescence Characteristics of Hybridized Polyfluorene. **2020**, 1535, 012055		
430	Cathodoluminescence spatially resolves optical transitions in thick group-III and N-polar InGaN films. **2020**, 128, 175305		
429	A Novel Highly Efficient Host-Sensitized Red Emitting (Ba2YV3O11 : Eu3+) Phosphor for Hybrid White LEDs. **2020**, 5, 5128-5136		7
428	Koopmans□tuning of HSE hybrid density functional for calculations of defects in semiconductors: A case study of carbon acceptor in GaN. **2020**, 127, 155701		5
427	Colloidal quantum dot hybrids: an emerging class of materials for ambient lighting. **2020**, 8, 10676-10695		18
426	Synthesis of New Nitride Alloys with Mg by Plasma-Assisted Molecular Beam Epitaxy. **2020**, 257, 2000122		1
425	In-situ X-ray diffraction analysis of GaN growth on graphene-covered amorphous substrates. **2020**, 59, 070902		3
424	Recent Progress on Light-Emitting Electrochemical Cells with Nonpolymeric Materials. **2020**, 30, 1908641		14
423	Barrier heights and Fermi level pinning in metal contacts on p-type GaN. *Applied Physics Letters*, **2020**, 116, 213506	3.4	9
422	DHI contemporary methodologies: A review and frontiers. **2020**, 135, 106184		6
421	Graphene□nsulator□emiconductor Ultraviolet Light-Responsive Nitride LEDs for Multi-Applications. **2020**, 2, 2104-2112		1
420	Photo- and Electroluminescence from Zn-Doped InN Semiconductor Nanocrystals. **2020**, 8, 2000604		2
419	A brief review of formation energies calculation of surfaces and edges in semiconductors. **2020**, 41, 061101		4
418	Photovoltaic Solar Cells for Outdoor LiFi Communications. **2020**, 1-1		5
417	Vertical alignment of InN- and GaN-based nanopillar crystals grown on a multicrystalline Si substrate. **2020**, 537, 125603		4
416	Optical insights of indium-doped □Ga2O3 nanoparticles and its luminescence mechanism. **2020**, 31, 6185-6191		2

415	Evidence for trap-assisted Auger recombination in MBE grown InGaN quantum wells by electron emission spectroscopy. *Applied Physics Letters*, **2020**, 116, 091102	3.4	8
414	Hydrostatic pressure dependence of indirect and direct excitons in InGaN/GaN quantum wells. **2020**, 101,		2
413	First-principles exploration of defect-pairs in GaN. **2020**, 41, 032104		8
412	Photo and cathodoluminescence of commercial YAG:Ce based phosphors in UV region. **2020**, 478, 120-124		3
411	Tunable Dual-Emission in Monodispersed Sb /Mn Codoped Cs NaInCl Perovskite Nanocrystals through an Energy Transfer Process. **2020**, 16, e2002547		39
410	Comparison of optoelectronic properties of epitaxial and non-epitaxial GaN nanostructures. **2020**, 31, 13756-13764		3
409	Non-polar nitride single-photon sources. **2020**, 22, 073001		1
408	Hybrid heterostructures and devices based on two-dimensional layers and wide bandgap materials. **2020**, 12, 100092		14
407	Moisture resistance, luminescence enhancement, energy transfer and tunable color of novel core-shell structure BaGeF6:Mn4+ phosphor. **2020**, 390, 124579		28
406	Emission spectrum control in monolithic blue-cyan dichromatic light-emitting diodes. **2020**, 35, 045017		2
405	Effect of indium accumulation on the growth and properties of ultrathin In(Ga)N/GaN quantum wells. **2020**, 190, 108565		2
404	Optical characteristics, morphology evolution and thermal stability of novel red-emitting Mn4+-activated K2LiAl1-yGayF6 solid solution phosphors for high-performance warm WLED. **2020**, 824, 153818		19
403	Role of the surface density of states in understanding size-dependent surface band bending in GaN nanowires. **2020**, 510, 145502		4
402	Investigating Blue-Light Exposure from: Lighting and Displays. **2020**, 36, 17-20		2
401	Violet Light-Emitting Diodes Based on p-CuI Thin Film/n-MgZnO Quantum Dot Heterojunction. **2020**, 12, 6037-6047		17
400	Suspended-ultrathin Si membrane on SOI: a novel structure to reduce thermal stress of GaN epilayer. **2020**, 768, 022053		1
399	From physics to fixtures to food: current and potential LED efficacy. **2020**, 7, 56		56
398	. **2020**, 56, 1-9		7

397	Interaction potentials for modelling GaN precipitation and solid state polymorphism. **2020**, 32, 205401	2
396	Study of the Surface of Polycrystalline Tin Bombarded with Nitrogen Ions. **2020**, 14, 97-100	
395	Growth of a-axial GaN core nanowires, semi-polar (11?01) GaN/InGaN multiple quantum well co-axial nanowires on Si substrate, and their carrier dynamics. **2020**, 105, 109854	1
394	High performance GaN-based hybrid white micro-LEDs integrated with quantum-dots. **2020**, 41, 032301	2
393	Exploring a particle-size-reduction strategy of YAG:Ce phosphor via a chemical breakdown method. **2021**, 39, 938-945	4
392	Semiconductor LEDs. **2021**, 61-86	
391	Enhanced luminescence of quasi-double heterostructured violet light-emitting diodes based on n-Mg0.027Zn0.973O QD and p-Cu1-Zn I thin films fabricated via simple thermal diffusion and iodination processes. **2021**, 413, 127401	2
390	Ce3+ doped BaLu2Al2Ga2SiO12 □A novel blue-light excitable cyan-emitting phosphor with ultra-high quantum efficiency and excellent stability for full-spectrum white LEDs. **2021**, 39, 1031-1039	5
389	Synthesis of CsPbX3 (X = Cl/Br, Br, and Br/I)@SiO2/PMMA composite films as color-conversion materials for achieving tunable multi-color and white light emission. **2021**, 14, 1187-1194	12
388	Performance Limits of an Alternating Current Electroluminescent Device. **2021**, 33, e2005635	1
387	Preparation, optical properties and first principle calculation of CsVO3. **2021**, 229, 117658	1
386	Role of oxygen vacancy in rare-earth-free LiCa3Mg(VO4)3 phosphor: Enhancing photoluminescence by heat-treatment in oxygen flow. **2021**, 79, 123-132	6
385	Toward 200 Lumens per Watt of Quantum-Dot White-Light-Emitting Diodes by Reducing Reabsorption Loss. **2021**, 15, 550-562	33
384	AlGaN-based ultraviolet light-emitting diodes: challenges and opportunities. **2021**, 36, 294-305	13
383	Nanosecond pulsed-bias-actuated and exciton-dynamics-induced chirp in InGaN/GaN LEDs towards realizing electrically-tunable broadband light emitters. **2021**, 229, 117703	2
382	Analysis of mechanically induced subsurface damage and its removal by chemical mechanical polishing for gallium nitride substrate. **2021**, 67, 350-358	5
381	Group-III-nitride and halide-perovskite semiconductor gain media for amplified spontaneous emission and lasing applications. **2021**, 54, 143001	7
380	Role of rare-earth ions for energy-saving LED lighting devices. **2021**, 407-444	0

379	Cooperative roles of chemical reactions and mechanical friction in chemical mechanical polishing of gallium nitride assisted by OH radicals: tight-binding quantum chemical molecular dynamics simulations. **2021**, 23, 4075-4084		2
378	The most optimal barrier height of InGaN light-emitting diodes. **2021**, 127, 1		1
377	The exceptionally high thermal conductivity after 'alloying' two-dimensional gallium nitride (GaN) and aluminum nitride (AlN). **2021**, 32, 135401		5
376	Self-assembled Growth of GaN Nanostructures on Flexible Metal Foils by Laser Molecular Beam Epitaxy. **2021**, 135-161		
375	Phosphor-Based InGaN/GaN White Light-Emitting Diodes With Monolithically Integrated Photodetectors. **2021**, 68, 132-137		2
374	Electronic and magnetic properties of Fe-doped GaN: first-principle calculations. **2021**, 76, 245-251		0
373	Smooth GaN membranes by polarization-assisted electrochemical etching. *Applied Physics Letters*, **2021**, 118, 062107	3.4	3
372	Dynamic Device Characteristics and Linewidth Measurement of InGaN/GaN Laser Diodes. **2021**, 13, 1-10		2
371	Effect of Oxygen and Aluminum Incorporation on the Local Structure of GaN Nanowires: Insight from Extended X-ray Absorption Fine Structure Analysis. **2021**, 125, 3225-3234		
370	Synthesis and dielectric enhancement of rare-earth ions substituted lanthanum tantalate solid solutions. **2021**, 46, 33-45		
369	Electrically injected GaN-based microdisk towards an efficient whispering gallery mode laser. **2021**, 29, 5598-5606		5
368	Triple-Site Dopant–Defect Complexes in Mg–H-Codoped GaN: First-Principles Identification. **2021**, 218, 2000723		
367	GaN buffer growth temperature and efficiency of InGaN/GaN quantum wells: The critical role of nitrogen vacancies at the GaN surface. *Applied Physics Letters*, **2021**, 118, 111102	3.4	7
366	Performance improvement of green QW LEDs, for the different doping in the barriers, using InAlN interlayer and strain compensated AlGaN interlayer at the InGaN/GaN interface. **2021**, 113, 110863		1
365	Passivation of III–V surfaces with crystalline oxidation. **2021**, 8, 011309		5
364	Characterization of a VLC system in real museum scenario using diffusive LED lighting of artworks. **2021**, 9, 548		7
363	Micro-Light Emitting Diode: From Chips to Applications. **2021**, 15, 2000133		31
362	Strain-induced yellow to blue emission tailoring of axial InGaN/GaN quantum wells in GaN nanorods synthesized by nanoimprint lithography. **2021**, 11, 6754		2

361	Effects of electrochemical potentiostatic activation on carrier transport in AlGaN-based deep-ultraviolet light-emitting diodes. **2021**, 39, 023410		
360	White light-emitting diodes from perovskites. **2021**, 42, 030202		10
359	Effect of quantum barrier width and quantum resonant tunneling through InGaN/GaN parabolic quantum well-LED structure on LED efficiency. **2021**, 22, 103943		4
358	Nanophotonic crystals on unpolished sapphire substrates for deep-UV light-emitting diodes. **2021**, 11, 4981		2
357	Nanoantenna-Enhanced Light-Emitting Diodes: Fundamental and Recent Progress. **2021**, 15, 2000367		4
356	Nanoscale Dopant Profiling of Individual Semiconductor Wires by Capacitance-Voltage Measurement. **2021**, 21, 3372-3378		1
355	An analysis of luminous mechanism of rare earth hybrid complex with Ce3+ ion by the DV-X□ method. 002072092110020		
354	Ultrafast hole transfer from monolayer ReS2 to thin-film F8ZnPc. *Applied Physics Letters*, **2021**, 118, 153104	3.4	2
353	Nanoscale InN clusters and compositional inhomogeneities in InGaN epitaxial layers quantified by tip-enhanced Raman scattering. *Applied Physics Letters*, **2021**, 118, 162107	3.4	1
352	Effect of Graded-Indium-Content Superlattice on the Optical and Structural Properties of Yellow-Emitting InGaN/GaN Quantum Wells. **2021**, 14,		1
351	Low-Defect-Density Aluminum Nitride (AlN) Thin Films Realized by Zigzag Macrostep-Induced Dislocation Redirection. **2021**, 21, 3394-3400		4
350	GaN surface sputter damage investigated using deep level transient spectroscopy. **2021**, 126, 105654		1
349	Phosphor converters for laser driven light sources. *Applied Physics Letters*, **2021**, 118, 210503	3.4	10
348	Solid-State Lighting. **2021**, 187-274		
347	High Q factor Electrically Injected Green Micro Cavity. **2021**, 39, 2895-2901		1
346	Dielectric and polar properties of aluminum nitride single crystals. **2021**, 576, 55-61		1
345	Activation of buried p-GaN through nanopipes in large-size GaN-based tunnel junction LEDs. **2021**, 32,		0
344	KTb(MoO) Green Phosphor with K-Ion Conductivity: Derived from Different Synthesis Routes. **2021**, 60, 9471-9483		3

343	Synthesis and luminescence studies of mixed phase LiCa3MgV3-XWXO12 phosphors for enhanced quantum yield. **2021**, 234, 117948	4
342	Temperature-dependent luminescent properties of dual-wavelength InGaN LEDs. **2021**, 234, 117957	2
341	Cathodoluminescence Investigation of Stacking Faults and Dislocations in the Edge Part of Seed-Grown m-Plane GaN Substrate. **2021**, 218, 2100175	1
340	Enhancement of optical characteristic of InGaN/GaN multiple quantum-well structures by self-growing air voids. **2021**, 64, 1583-1588	0
339	Research on material removal mechanism and radial cracks during scribing single crystal gallium nitride. **2021**, 47, 15155-15164	3
338	Investigation into water-induced surface oxidization of GaN lamella structure. **2021**, 36, 085009	
337	On-chip 3D confocal optical study of an InGaN/GaN microrod LED in the low excitation regime. **2021**, 130, 024505	0
336	Preparation and luminescent properties of a novel orange-red phosphor Sr2RE8(SiO4)6O2:Eu(2+,3+) (RE = Y, Gd, La) for LEDs. **2021**, 75, 5803-5811	0
335	Colour tuning of garnet phosphor through codoping. **2021**, 235, 118017	2
334	Dynamic piezo-phototronic effect in InGaN/GaN multiple quantum wells. **2021**, 155, 106926	1
333	GaN-nanopillar-based light-emitting diodes directly grown on multi-crystalline Si substrates. **2021**, 11, 075110	
332	In-doped LiCa2.98MgV3O12 rare-earth-free phosphor with a high photoluminescence quantum yield of 67.4%. **2021**, 104, 5837-5847	
331	Light recycling in LED-pumped Ce:YAG luminescent concentrators. **2021**, 29, 25302-25313	1
330	Enhanced light extraction efficiency of micropixel geometry AlGaN DUV light-emitting diodes. **2021** , 14, 084002	8
329	Assessment and prediction of band edge locations of nitrides using a self-consistent hybrid functional. **2021**, 155, 024120	1
328	Investigation of Ultrafast Carrier Dynamics in InGaN/GaN-Based Nanostructures Using Femtosecond PumpProbe Absorption Spectroscopy. **2021**, 258, 2100223	0
327	Band engineering in nitrogen-rich AlGaNAs quaternary alloys. **2021**, 189, 110240	
326	ReviewApplication of Photoluminescent and Electroluminescent Metal-Organic Frameworks in White Light-Emitting Diodes. **2021**, 10, 086009	1

325	Rapid Estimation of Removal Rate of Chemical Mechanical Polishing of Gallium Nitride Substrate by Quantitative Diagnosis of Cathodoluminescence Images.	
324	Effects of Eu3+ doping on the luminescence properties of novel Sr2CaLa(VO4)3 from partial substitution of Sr2+ by Ca2+ in Sr3La(VO4)3. **2021**, 47, 34323-34323	1
323	A novel blue-emitting phosphors (CsBaYB6O12:Ce3+): Potential applications in w-LEDs and X-ray phosphors. **2021**, 873, 159676	5
322	Low-Temperature Synthesis of High-Brightness Green-Emitting Silica-Coated CsPbBr3 and Its Application in Light-Emitting Diodes. **2021**, 50, 6337-6343	
321	Improving Ambient Contrast Ratio and Color Uniformity of Mini Full Color Light-Emitting Diodes Using an SiO2/Graphite Bilayered Packaging Structure. **2022**, 144,	5
320	Structure and luminescence properties of Eu3+ and Dy3+ implanted GaN films. **2021**, 156, 106974	1
319	Optimization of the Receiver in Visible Light Communications. **2021**,	
318	Two-dimensional heterostructures and their device applications: progress, challenges and opportunities□eview. **2021**, 54, 433001	6
317	Amorphous Molecular Materials for Directed Supercontinuum Generation.	2
316	Multicolor Emission from Ultraviolet GaN-Based Photonic Quasicrystal Nanopyramid Structure with Semipolar InGaN/GaN Multiple Quantum Wells. **2021**, 16, 145	
315	Investigation of a Separated Short-Wavelength Peak in InGaN Red Light-Emitting Diodes. **2021**, 11, 1123	0
314	Synthesis of GaN Crystals by Nitrogen Pressure-Controlled Recrystallization Technique in Na Alloy Melt. **2021**, 11, 1058	
313	Mid-infrared intersubband absorption in strain-balanced non-polar (In)AlGaN/InGaN multi-quantum wells. **2021**, 11, 3284	2
312	Efficiency Boosting by Thermal Harvesting in InGaN/GaN Light-Emitting Diodes. **2021**, 9,	1
311	Characterization of high-power white leds for VLC applications. **2021**, 18, 100215	
310	Introduction to phosphate phosphors. **2021**, 1-53	
309	White light emitting nanofibers constructed by electrospinning: advances and perspectives. **2021**, 9, 5036-5054	3
308	BaYBO based phosphor ceramic plates with excellent thermal stability for wLED applications. **2021**, 50, 5287-5300	2

307	All-MOCVD-grown gallium nitride diodes with ultra-low resistance tunnel junctions. **2021**, 54, 155103	3
306	Glass Ceramics for Solid State Lighting. **2006**, 19-25	7
305	Development of Cathodoluminescence (CL) for Semiconductor Research, Part I: TEM-CL Study of Microstructures and Defects in Semiconductor Epilayers. **2002**, 37-51	2
304	Cubic GaN on Nanopatterned 3C-SiC/Si (001) Substrates. **2013**, 381-405	5
303	Recombination Dynamics of Near-Bandedge Emission in Cubic GaN. **1996**, 259-263	2
302	LED Materials: Epitaxy and Quantum Well Structures. **2016**, 1-49	1
301	History of Solid-State Light Sources. **2017**, 1-30	1
300	A Brief Review of III-Nitride UV Emitter Technologies and Their Applications. **2016**, 1-25	46
299	Solid-State Lighting Based on Light Emitting Diode Technology. **2016**, 87-118	8
298	Commercial Light Emitting Diode Technology. **1996**, 323-331	21
297	Visible-Wavelength Laser Diodes. **1999**, 1-69	1
296	Hydrogen in Wide Bandgap Semiconductors. **2000**, 429-505	14
295	A review on photocatalytic remediation of environmental pollutants and H2 production through water splitting: A sustainable approach. **2020**, 19, 100893	24
294	Lateral and Vertical Heterostructures of h-GaN/h-AlN: Electron Confinement, Band Lineup, and Quantum Structures. **2017**, 121, 27098-27110	15
293	Observation of stimulated emission, line narrowing, and red shift of emission peak from optically-pumped rectangular cross-sectional GaN optical waveguides fabricated by selective growth. **1996**, 32, 34	3
292	Hydrogen-surfactant-assisted coherent growth of GaN on ZnO substrate. **2018**, 2,	11
291	Stability of wurtzite semipolar surfaces: Algorithms and practices. **2018**, 2,	7
290	Development of semiconducting ScN. **2019**, 3,	27

289	Thermodynamic model for metalorganic vapor-phase epitaxy of N-polar group-III nitrides in step-flow growth mode: Hydrogen, competitive adsorption, and configuration entropy. **2019**, 3,	2
288	Scattering Nanoparticles-Induced Reflection Effect for Enhancing Optical Efficiency of Inverted Quantum Dots-Light-Emitting Diodes Combined With the Centrifugation Technique. **2021**, 143,	3
287	Molecular beam epitaxial growth and scanning tunneling microscopy studies of the gallium rich trench line structure on N-polar w-GaN(0001□). **2015**, 33, 061404	1
286	Structure of InN and InGaN. **2009**, 515-540	2
285	Investigation of Carrier Transport in GaN Single Crystals and Radiation Detectors by Thermally Stimulated Methods. **2005**, 107, 340-345	3
284	Influence of Irradiation by High-Energy Protons on GaN Detectors. **2008**, 113, 1013-1016	1
283	An ab initio Study of a Model of Single Wall GaN Nanotubes with Oxygen and Zinc as Impurities: Structural and Electronic Properties. **2008**, 113, 713-722	7
282	Realization of phosphor-in-glass thin film on soda-lime silicate glass with low sintering temperature for high color rendering white LEDs. **2019**, 58, 2372-2381	4
281	Toward ultimate efficiency: progress and prospects on planar and 3D nanostructured nonpolar and semipolar InGaN light-emitting diodes. **2018**, 10, 246	82
280	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. **2020**, 28, 4489-4500	12
279	Simple prismatic patterning approach for nearly room-temperature processed planar remote phosphor layers for enhanced white luminescence efficiency. **2018**, 8, 3230	1
278	Fabrication of (Tb,Gd)3Al5O12:Ce3+ phosphor ceramics for warm white light-emitting diodes application. **2019**, 9, 3333	16
277	Epitaxial growth of ZnO crystal on the Si-terminated 6H-SiC(0001) surface using the first-principles calculation. **2006**, 4, 254-257	2
276	Nitride Semiconductor Surfaces. Effect of Low-temperature Deposited Layer on the Growth of Group-III Nitrides on Sapphire.. **2000**, 21, 126-133	1
275	Surface morphology on high-temperature plasma-etched gallium nitride. **2013**, 38, 325-328	3
274	Reflection coefficient and optical conductivity of gallium nitride GaN. **2012**, 15, 281-284	24
273	Rapid growth of bulk GaN crystal using GaN powder as source material. **2005**, 892, 684	2
272	New plasma chemistries for etching GaN and InN: BI3 and BBr3. **1998**, 3, 1	15

271	Optical properties of electron-irradiated GaN. **1998**, 3, 1	6
270	High quality GaN films - growth and properties. **1998**, 3, 1	8
269	Growth of GaN films on (001) and (111) GaAs surfaces by a modified MBE method. **1996**, 1, 1	6
268	Homo- and Hetero-Epitaxial Gallium Nitride Grown by Molecular Beam Epitaxy. **1999**, 4, 484-489	2
267	Interface Effects on the Persistent Photoconductivity in Thin GaN and AlGaN Films. **1999**, 4, 520-525	1
266	Characterization of Hot-Electron Effects on Flicker Noise in III-V Nitride Based Heterojunctions. **1999**, 4, 560-564	1
265	Inflammatory Effect of Light-Emitting Diodes Curing Light Irradiation on Raw264.7 Macrophage. **2019**, 19, 133-140	1
264	Analysis of Drain Current Transient Response of Gate Pulse Voltage in AlGaN / GaN High Electron Mobility Transistors. **2018**, 3, 216-219	1
263	Scanning tunneling microscopy studies of III-nitride thin film heteroepitaxial growth. **2004**, 174, 383	4
262	Background story of the invention of efficient blue InGaN light emitting diodes. **2016**, 186, 524-536	1
261	Vertical GaN-on-GaN Schottky Diodes as ▯Particle Radiation Sensors. **2020**, 11,	4
260	Tunable Dynamic Black Phosphorus/Insulator/Si Heterojunction Direct-Current Generator Based on the Hot Electron Transport. **2019**, 2019, 5832382	19
259	Formation of Vanadium-based Ohmic Contacts to n-GaN. **2003**, 13, 567-571	1
258	Optical Properties of White Light Sources Using Red, Green, Blue Emitting Phosphors and Violet Light Emitting Diodes. **2006**, 16, 145-150	3
257	Synthesis and Application of Bluish-Green BaSi2O2N2:Eu2+Phosphor for White LEDs. **2011**, 21, 250-254	3
256	Effect of Glass Composition on the Optical Properties of Color Conversion Glasses for White LED. **2012**, 22, 669-674	5
255	Effect of Titanium Dioxide in BaO-ZnO-B2O3-SiO2Glasses on the Optical Properties of Color Conversion Glass. **2014**, 24, 710-714	1
254	Effect of Lu3Al5O12:Ce3+ and (Sr,Ca)AlSiN3:Eu2+ Phosphor Content on Glass Conversion Lens for High-Power White LED. **2015**, 52, 229-233	2

253	The Effect of Different Light-Curing Methods on Temperature Changes of Dual Polymerizing Agents Cemented to Human Dentin. **2008**, 9, 57-64	3
252	Comparison of the Heat Generation of Light Curing Units. **2008**, 9, 65-72	12
251	Reduction of Current Crowding in InGaN-based Blue Light-Emitting Diodes by Modifying Metal Contact Geometry. **2014**, 14, 588-593	3
250	Design of a Two-Stage Driver for LED MR16 Retrofit Lamps Compatible with Electronic Transformers. **2016**, 16, 1-10	2
249	Upconversion luminescence of Tm3+/Ho3+/Yb3+ codoped tellurite glass used for white light emission. **2010**, 59, 6256	2
248	Research progress of substrate materials used for GaN-Based light emitting diodes. **2014**, 63, 068103	8
247	Effect of Initial Bow of Sapphire Substrate on Substrate Curvature during InGaN Growth Stage of Light Emitting Diode Epitaxy. **2012**, 51, 012102	5
246	IIINitride Epitaxy on Atomically Controlled Surface of Sapphire Substrate with Slight Misorientation. **2012**, 51, 025502	6
245	Defect Propagation from 3C-SiC Intermediate Layers to IIINitride Epilayers. **2012**, 51, 035603	3
244	White Light-Emitting Diodes for Wide-Color-Gamut Backlight Using Green-Emitting Sr-Sialon Phosphor. **2012**, 51, 122101	16
243	White Light-Emitting Diodes Using Sr-Containing Sialon Phosphors. **2012**, 51, 122103	10
242	Constrained Classification of Large Imbalanced Data by Logistic Regression and Genetic Algorithm. **2013**, 214-218	2
241	Socio-Economic Analysis of Wholesale Rice Marketers in Abia State, Nigeria. **2011**, 285-288	4
240	Physics and applications of semiconductor nanowire lasers. **2021**, 20, 389-438	
239	Assesment of a model to calculate the refractive index of AlXGa1-XN epilayers using the multi-oscillator model simulation of the infrared reflectance. **2021**, 625, 413484	
238	Research progress of full electroluminescent white light-emitting diodes based on a single emissive layer. **2021**, 10, 206	15
237	Optical and morphological features of poly(vinyl carbazole)/ferrite composites for potential opto-electronic applications. **2021**, 127, 1	0
236	Cascaded Ni hard mask to create chlorine-based ICP dry etched deep mesas for high-power devices.	2

235	III-Nitride Light-Emitting Devices. **2021**, 8, 430		2
234	The role of polarization in the threshold voltage of field effect transistors based on ZnO/MgO. *Applied Physics Letters*, **2021**, 119, 163502	3.4	0
233	Atomic Structures and Chemical States of Active and Inactive Dopant Sites in Si-Doped GaN. **2021**, 3, 4618-4622		1
232	Strategies for improving performance, lifetime, and stability in light-emitting diodes using liquid medium. **2021**, 2, 041302		1
231	Ion Implantation in Wide Bandgap Semiconductors. **2000**, 300-353		
230	Plasma Etching of IIIV Nitrides. **2000**, 250-299		0
229	Scanning Tunneling Microscopy of IIIV Compound Semiconductor (001) Surfaces. **2000**, 193-282		
228	GaN-AlN-InN Blue LightEmitting Devices. **2000**,		
227	Optical properties of InxGa1-xN/GaN epilayers. **2002**, 12, 54-57		
226	The Monte Carlo simulation of epitaxial growth of GaN(OOOl) with wurtzite structure. **2002**, 833-838		
225	Transient Capacitance Characterization of Deep Levels in Undoped and Si-Doped GaN. **2003**, 764, 1		
224	Semiconductor Nanowires. **2003**, 878-942		
223	Future of Laser Technology for Spectroscopy. **2003**, 165-211		
222	Combinatorial Computational Chemistry Approach in the Design of New Catalysts and Functional Materials. **2003**,		
221	Luminescent Properties of Four-Band White Light Emitting Diodes. **2003**, 47, 370-375		
220	Anomalous Photoluminescence and Persistent Photoconductivity of AlxGal-xN/GaN Epilayers. **2003**, 13, 673-676		
219	Atomic Resolution Electron Energy Loss Spectroscopy. **2004**, 1-9		
218	Nitride-Based Light Emitting Diodes and Laser Diodes: Optical Properties and Applications. **2004**, 289-320		

217	The Luminous Intensity and Luminaire Efficiency Analysis of White LED as Luminaire types for General Lighting. **2004**, 18, 20-26	1
216	The Study of the Most Suitable Location of Luminaire for Road Tunnel Lighting System. **2004**, 18, 1-7	1
215	Optic Characteristics Comparison and Analysis of SMD Type Y/G/W HB LED. **2004**, 18, 15-21	6
214	Study of pretreatment with ion implantation on substrate for GaN. **2004**, 14, 494-499	
213	High-Power Operation of Pure Blue GaN-Based Semiconductor Laser. **2005**, 33, 651-654	
212	Lasers for Frontier Spectroscopy. **2005**, 251-288	
211	Perspectives on Electronic and Optoelectronic Materials. **2006**, 3-15	
210	Phosphors for lamps. **2006**,	
209	Thermal Stability of Reflection Multilayers on p-AlGaN/GaN contact of deep-UV Light Emitting Diodes. **2007**,	1
208	Effect of Yellow Phosphor on Characteristics of White Light Emitting Diode. **2007**, 40, 103-106	1
207	Nitride Devices. **2007**, 22-1-22-15	
206	References. **2008**, 413-479	
205	Transmission electron microscopy techniques for imaging and compositional evaluation in semiconductor heterostructures. **2008**, 133-173	
204	Enhancement of Luminous Efficacy by Random Patterning of Phosphor Matrix. **2008**, 32, 111-114	1
203	Selected High-Impact Journal Articles on Defects in Microelectronic Materials and Devices. **2008**,	2
202	GaN and ZnO Light Emitters. **2009**, 415-457	
201	Highly Transparent Indium Oxide Doped ZnO Spreading Layer for GaN Based Light Emitting Diodes. **2009**, 19, 443-446	1
200	Multi-wavelength Blue Light Generation by Frequency Doubling of the Output of Stacked Grating Coupled Surface Emitting Lasers. **2010**,	

199	Effect of H_3BO_3 on preparation and luminescence properties of submicron green-emitting $Ca_3Sc_2Si_3O_{12}$:Ce phosphor. **2010**, 59, 8200	1
198	Analysis of Thermal Properties in LED Package by Via hole of FR4 PCB. **2010**, 24, 57-63	3
197	White Emission from InGaN Multi-quantum Wells on c-Planes and Nano-pyramids Hybrid Structure. **2011**,	
196	Light Emitting Diodes. **2011**, 61-95	1
195	A new method to measure the carrier concentration of p-GaN. **2011**, 60, 037804	
194	Tunable Light Emission from GaN-Based Photonic Crystal with Ultraviolet AlN/AlGaN Distributed Bragg Reflector. **2011**, 50, 04DG09	
193	In-situ Monitoring of GaN Epilayers by Spectral Reflectance. **2011**, 20, 361-366	
192	Controlling the Size and Position in Nanoscale. **2012**, 5-31	
191	Investigation of luminescent properties inherent to $SrTiO_3:Pr^{3+}$. **2011**, 14, 461-464	2
190	Influence of Fluxing Agents in $Sr_3SiO_5:Eu^{2+}$Phosphors for Fabrication of Warm White Light Emitting Diodes. **2012**, 49, 105-110	1
189	X-ray Photoemission Spectroscopy Study of Low-Temperature Nitridation of GaAs(001) Surface Using RF Radical Source. **2012**, 51, 015602	
188	The preparation and performance analysis of GaN-based high-voltage DC light emitting diode. **2012** , 61, 138502	2
187	Large Area of Ultraviolet GaN-Based Photonic Quasicrystal Laser. **2012**, 51, 04DG02	
186	Effect of Solution Properties on Luminance Characteristics of YAG:Ce Phosphors Prepared by Spray Pyrolysis. **2012**, 19, 220-225	
185	Individual Roles of Atoms and Ions during Hydrogen Plasma Passivation of Surface Defects on GaN Created by Plasma Etching. **2012**, 51, 111002	1
184	Optical properties of GaN:Tb nanoparticles synthesized by simple ammonification method. **2013**, 62, 037105	
183	6.4.6 Devices based on group III□itrides. **2013**, 128-129	
182	Optical Design of a White LED Performing High Spatial Color Uniformity. **2013**,	

181 Shear Bond Strength and Temperature Rise of Orthodontic Brackets Bonding by Using a New 3-Second LED Mode. **2013**, 26, 45-50

180 Luminescence properties of novel Sr-Y-Si-Oxynitride yellow phosphor for LED applications. **2013**, 23, 195-200

179 Lighting System Efficiency in the Industrial Plants. **2014**, 67-76

178 Thermal Characteristics of the Optimal Design on 15W COB LED Down Light Heat Sink. **2014**, 18, 401-407

177 Carbon Nanotube and GaN Hetero-Interface: Electrical Property and Band-Structure. **2014**, 1-4

176 Thermal Characteristics of the design on Residential 13.5W COB LED Down Light Heat Sink. **2014**, 7, 20-25

175 Wide Band Gap Electronic Devices. **1995**, 453-461 1

174 New Materials for Visible Light Emission. **1996**, 187-206

173 Compact blue-green laser sources. **1996**, 561-574

172 Weitere Entwicklungstendenzen. **1996**, 362-398

171 GaN m-i-n LED grown by MOVPE. **1996**, 1, 1

170 Light Generation by Semiconductors. **1997**, 421-443

169 Optical Fiber Components and Devices. **1997**, 267-318

168 A Hierarchical Bayesian Deconvolution with Positivity Constraints. **1998**, 1998, 195-200

167 Gan Nanotubes. **1999**, 4, 554-559

166 Behavior of W and WSix Contact Metallization on n- and p- Type GaN. **1999**, 4, 684-690

165 Thermal Characteristics of Designed Heat Sink for 13.5W COB LED Down Light. **2014**, 9, 561-566 4

164 CaxSr2-xSiO4:Eu2+Green-emitting Nano Phosphor for Ultraviolet Light Emitting Diodes. **2014**, 15, 249-252

163	GaN Film Growth Characteristics Comparison in according to the Type of Buffer Layers on PSS. **2014**, 24, 645-651	1
162	For Japanese Media after the Nobel Prize in Physics Announced. **2015**, 20, 11_24-11_29	
161	Nitrides of Boron and Group III Metals. **2015**, 347-427	
160	Current reflearch and future development of organic laser materials and devices. **2015**, 64, 094202	3
159	Research on emission transition mechanisms of InGaN/GaN multiple quantum well light-emitting diodes using low-frequency current noise. **2015**, 64, 050701	2
158	Development of white LEDs from UV-LEDs and RGB phosphors. **2015**, 1577-1578	
157	Effect of the Control of Bowing in Free-standing GaN by Mechanical Polishing. **2015**, 28, 776-780	
156	A new method to estimate the p-GaN carrier concentration by analyzing the reversed current-voltage characteristic curve of p-n+ junction diode. **2016**, 65, 197302	
155	History of Solid-State Light Sources. **2016**, 1-30	
154	Fascinated journeys into blue light. **2016**, 186, 504-517	
153	Synthesis Processing for Phosphor Materials. **2016**, 5, 350-357	
152	The effect of thickness on luminous properties of ceramic phosphor plate for high-power LD. **2016**, 26, 80-83	
151	GaN Nanowall Network: Laser Assisted Molecular Beam Epitaxy Growth and Properties. **2017**, 245-268	
150	Efficiency Droop of Nitride-Based Light-Emitting Diodes. **2017**, 99-122	
149	Bibliography. 243-265	
148	Low contact resistance of the MWCNTs ohmic contact to p-GaN and its application for high power LED. **2017**,	
147	III V Nitride-Based Photodetection. **2017**, 597-613	
146	Formation and characterization of porous SiC by anodic oxidation using potassium persulfate solution. **2018**,	1

145	Design of a Low-Cost Underwater LED Fishing Light Attractor. **2018**, 09, 67-73	1
144	High efficiency GaN-based near UV light emitting diodes with asymmetric triangular multiple quantum wells. **2018**,	
143	Measurement system for characterization of angular and spectral distribution of LED-based sources. **2018**,	
142	Recent progress on IV-VI compound semiconductor heterojunction two-dimensional electron gas. **2019**, 68, 166801	0
141	Tunable greenish-to-reddish light generation via energy transfer in Tb3+/Sm3+-codoped PbGeO3:PbF2:CdF2 glass under UV excitation. **2019**, 58, 1	
140	Homogenization of power intensity based on micro lens array in optical wireless communication systems. **2019**,	
139	Optical Properties of Y3Al5O12;Ce3+,Pr3+ Transparent Ceramic Phosphor for High Power White Lighting. **2019**, 29, 116-120	
138	Optical and Structural Analysis of BaSi2O2N2:Eu Green Phosphor for High-Color-Rendering Lighting. **2019**, 29, 437-442	0
137	. **2020**,	
136	Experimental studies and model analysis on potential fluctuation in InGaN quantum-well layers. **2020**, 59, 091003	1
135	Study of Electrothermal Characteristics and Emitted Light Characteristics of SSI-LED. **2020**, 9, 065017	1
134	Dilute-Se Ga2(O1-xSex)3 for Ultraviolet and Visible Photodetector. **2020**,	
133	Defect levels in d-electron containing systems: Comparative study of CdTe using LDA and LDA + U. **2020**, 41, 102701	
132	Effect of Heat Treatment of Al Substrate on GaN Film Electrodeposited in Aqueous Solution. **2020**, 10, 1-19	
131	Charge Transfer in Molecular Materials. **2020**, 227-257	1
130	Low-temperature annealing behavior of defects in Mg-ion-implanted GaN studied using MOS diodes and monoenergetic positron beam. **2021**, 60, 016502	5
129	Simulation of Nitride Semiconductor MOVPE. 1-20	1
128	Atomistic Level Process to Device Simulation of GaNFET Using TNL TCAD Tools. **2020**, 815-826	

127	A review of key technologies for epitaxy and chip process of micro light-emitting diodes in display application. **2020**, 69, 198501	1
126	Improvement of the crystallinity of GaN epitaxial films grown on sapphire substrates due to the use of AlN quantum dot buffer layers.	
125	Silizium-Carbid SiC und andere Materialien. **2006**, 661-705	
124	First stage of nucleation of GaN on (0001) sapphire. **2005**, 21-24	
123	Improvement of light quality by DBR structure in white LED. **2015**, 23, A24	
122	Fabrication and performance evaluation of GaN thermal neutron detectors with 6LiF conversion layer. **2020**, 29, 090401	0
121	Thermally stable laser-driven phosphor converted white light source using multilayer structured diffuser system. **2020**, 17, 126001	1
120	Temporally modulated energy shuffling in highly interconnected nanosystems. **2020**, 10, 851-876	3
119	Fermi Velocity and Effective Mass Variations in ZGaN Ribbons: Influence of Li-Passivation. **2021**, 9, 154857-154863	1
118	. **2021**,	
117	Toward Stable and Efficient Perovskite Light-Emitting Diodes. 2109495	17
116	p-type AlN based heteroepitaxial diodes with Schottky, Pin, and junction barrier Schottky character achieving significant breakdown performance. **2021**, 130, 195702	1
115	Modeling and Simulations of 4H-SiC/6H-SiC/4H-SiC Single Quantum-Well Light Emitting Diode Using Diffusion Bonding Technique.. **2021**, 12,	2
114	Strain Engineering to Release Trapped Hole Carriers in p-Type Haeckelite GaN.	1
113	Mechanism of Defects and Electrode Structure on the Performance of AlN-based Metal Semiconductor Metal Detectors.	0
112	Multifunctional Displays and Sensing Platforms for the Future: A Review on Flexible Alternating Current Electroluminescence Devices.	1
111	Perovskite White Light Emitting Diodes: Progress, Challenges, and Opportunities. **2021**,	18
110	Understanding the Luminescence Characteristics of Ultraviolet InGaN/AlGaN Multiple Quantum Wells with Different In Gradients. **2021**, 11, 1390	0

109	The deep red fluorescent transparent ceramics of Pr3+ doped BaZr0.16Mg0.28Ta0.56O3 based on 3P0->3F2 transition. **2021**, 148, 111667		
108	Understanding the Efficiency of Mn4+ Phosphors: Study of the Spinel Mg2Ti1▯MnxO4.		0
107	It▯ all too much. **2021**, 74, 8-8		0
106	Flexible and Stretchable Micro-LED Display. **2021**, 141-160		
105	Effect of different valence states point defects on carrier activity and lifetime and photocatalytic properties of GaN:Be/Mg/Ca system. **2022**, 57, 1134		0
104	Exploration of a large-scale reconstructed structure on GaN(0001) surface by Bayesian optimization. *Applied Physics Letters*, **2022**, 120, 021602	3.4	3
103	Crystal structure, luminescence properties and thermal stability of novel Sr2CaLa(VO4)3: Sm3+ phosphor synthesized by the combustion method. **2022**, 899, 163378		0
102	CQD-LEDs with High Colour Rendering Index. **2020**,		
101	Dilute-As InGaNAs/GaN Quantum Wells for High-Efficiency Red Emitters. **2022**, 58, 1-6		0
100	Modeling of the Point Defect Migration across the AlN/GaN Interfaces-Ab Initio Study.. **2022**, 15,		1
99	Effects of polarized-induced doping and graded composition in an advanced multiple quantum well InGaN/GaN UV-LED for enhanced light technology.		0
98	Rare earth▯doped semiconductor nanomaterials. **2022**, 291-338		0
97	An Enhanced Method for Dynamic Characterization of High-Power LEDs for Visible Light Communication Applications. **2022**, 11, 292		1
96	Wide multicolor tunability of blue-to-green up-conversion emission and white light generation in Pr3+/Yb3+ co-doped yttrium tantalates. **2022**, 245, 118761		0
95	From Fully Strained to Relaxed: Epitaxial Ferroelectric Al 1- x Sc x N for III-N Technology. 2109632		4
94	Enhanced quantum efficiency of a self-organized silica mixed red phosphor CaAlSiN3:Eu. **2022**, 309, 122968		
93	Optical spectroscopy of the Sr4Al14O25:Mn4+,Cr3+ phosphor: pressure and temperature dependences.		0
92	Perspectives on the Development of Metalorganic Vapor Phase Epitaxy for III-V Optoelectronic Devices. **2022**, 1-1		

91	Enhanced Quantum Efficiency of a Self-Organized Silica Mixed Phosphor Caalsin3:Eu.	
90	Cathodoluminescent Analysis of Sapphire Surface Etching Processes in a Medium-Energy Electron Beam.. **2022**, 15,	1
89	Effect of Flux Rate Variation at Fixed V/III Ratio on Semi-Polar (112□2) GaN: Crystal Quality and Surface Morphology Study. **2022**, 12, 247	1
88	Closing the yellow gap with Eu- and Tb-doped GaN: one luminescent host resulting in three colours.. **2022**, 12, 2503	1
87	Photothermal Optimization of Quantum Dot Converters for High-Power Solid-State Light Sources. 2102201	1
86	Cesium Lead Halide Perovskite Nanocrystals Assembled in Metal-Organic Frameworks for Stable Blue Light Emitting Diodes.. **2022**, e2105850	1
85	Growth and Characterization of GaN/InxGa1□N/InyAl1□N Quantum Wells by Plasma-Assisted Molecular Beam Epitaxy. **2022**, 12, 417	
84	A comprehensive review on LED-induced fluorescence in diagnostic pathology.. **2022**, 209, 114230	1
83	Sapphire nanophotonics: Fabrication challenges and optical properties. **2022**, 14, 100115	1
82	Neutron irradiation effects on gallium nitride-based blue LEDs. **2022**, 518, 37-40	2
81	Failure Analysis of Some Commercial Spotlights Based on Light Emitting Diodes. **2022**, 11, 48	1
80	Performance Enhancement of AlInGaN Quantum Well based UV-LED. **2021**,	
79	Gate dielectric material and process effects on distribution pattern of nano-resistors in solid-state incandescent light emitting devices.	
78	Uncovering the carrier dynamics of AlInGaN semiconductors using time-resolved cathodoluminescence. 1-14	
77	Trivalent rare-earth-codoped silicate phosphor materials (BaCaSiO:Dy/Eu) for solid-state lighting.. **2022**, 34,	1
76	Recent Progress and Prospects on Metal Halide Perovskite Nanocrystals as Color Converters in the Fabrication of White Light-Emitting Diodes. **2022**, 2,	1
75	Novel Emerging Materials: Introduction and Evolution. **2022**, 3-36	
74	Single-Phase Silicate Phosphors (Ba1.3Ca0.7□SiO4:xDy3+) Doped with Dysprosium for White Solid-State Lighting. **2022**, 2022, 1-11	1

73	Simple Approach to Mitigate the Emission Wavelength Instability of III-Nitride □ED Arrays.		0
72	High Temperature Etching for Threading Dislocation Investigation on GaN Epi-Layer. 1062, 18-22		
71	Structure Determination in a New Class of Amorphous Cluster Compounds with Extreme Nonlinear Optical Properties. **2022**, 91,		1
70	Phase-sensitive radioluminescent and photoluminescent features in Tm3+-doped yttrium tantalates for cyan and white light generation.		0
69	Perovskite Light-emitting Diodes. **2022**, 555-599		
68	Progress of Backlight Devices: Emergence of Halide Perovskite Quantum Dots/Nanomaterials. 4,		0
67	Optimization of InGaN quantum-dot based light-emitting diodes by means of cellular automata algorithms. **2022**, 54,		
66	Influence of Mn2+ doping on the emission spectrum of Sr2La8(SiO4)6O2:Eu(2+,3+) phosphor. **2022**, 142, 109625		0
65	Color controllable smart white lighting based on various device architectures of electrically driven quantum-dot light-emitting diodes.		
64	Electronic Structure, Optical and Thermoelectric Properties of Al1-Xinxn and Ga1-Xinxn Alloys.		
63	Ultralow-voltage operation of light-emitting diodes. **2022**, 13,		5
62	III-Nitride p-down green (520 nm) light emitting diodes with near-ideal voltage drop. *Applied Physics Letters*, **2022**, 121, 021102	3.4	1
61	Cluster-Glass for Low-Cost White-Light Emission. 2203351		1
60	Van der Waals heterostructures. **2022**, 2,		2
59	Investigation of Efficiency Enhancement in Tunnel Junction GaN Light Emitting Diodes. **2022**,		
58	Wavelength tune of InGaN based blue LEDs by changing indium percentage and operational voltage variables. **2022**, 10, 323-327		
57	Structural and optical properties of cubic GaN on U-grooved Si (100). **2022**, 121, 032101		1
56	Etching of the SiGaxNy Passivation Layer for Full Emissive Lateral Facet Coverage in InGaN/GaN Core□Shell Nanowires by MOVPE.		0

55	Lanthanide-Doped MAPbI3 Single Crystals: Fabrication, Optical and Electrical Properties, and Multi-mode Photodetection. **2022**, 34, 7412-7423	1
54	Impact of nitride and temperature treatment for AlGaN thin films. **2022**, 45,	
53	Surface plasmon resonance sensor for chemical and bio-sensing application: A review. **2022**,	1
52	Bespoke crystalline hybrids towards the next generation of white LEDs.	4
51	Resonant Lasing Emission in Undoped and Mg-Doped Gallium Nitride Thin Films on Interfacial Periodic Patterned Sapphire Substrates. **2022**, 12, 3238	0
50	System design: lighting. **2022**,	0
49	Metal halide perovskites-based white light-emitting diodes. **2022**, 4, 042001	0
48	Quantum Dot to Nanorod Transition for Efficient White-Light-Emitting Diodes with Suppressed Absorption Losses.	1
47	Semiconductor Photonic Devices. **2022**, 77-96	0
46	Structural Descriptors to Correlate Pb Ion Displacement and Broadband Emission in 2D Halide Perovskites.	2
45	Recent progress in Ce3+/Eu2+-activated LED and persistent phosphors: focusing on local structure and electronic structure.	6
44	Large-scale and high-quality III-nitride membranes through microcavity-assisted crack propagation by engineering tensile-stressed Ni layers. **2022**, 1, 220016-220016	0
43	Thermally robust Al2O3▯a3Si6N11:Ce3+ composite phosphor-in-glass (PiG) films for high-power and high-brightness laser-driven lighting.	0
42	Quality Improvement of GaN Epi-layers Grown with a Strain-Releasing Scheme on Suspended Ultrathin Si Nanofilm Substrate. **2022**, 17,	0
41	Compositional degradation of the electron blocking layers through solid-solution in GaN-based laser diodes. **2022**, 132, 145701	0
40	Milliwatt-power AlGaN Deep UV LEDs at 254nm emission as a clean alternative to Mercury-Deep UV Lamps.	0
39	Tuning the p-type doping of GaN over three orders of magnitude via efficient Mg doping during halide vapor phase epitaxy. **2022**, 132, 145703	2
38	Luminescent Materials Based on Aluminates: A Review. 2200346	0

(2023-2022)

37	One-step synthesis of multi-colored ZnO nanoparticles for white light-emitting diodes. **2022**, 252, 119425	0
36	On the Origin of the Yellow Luminescence Band in GaN.	0
35	Few-Layer Graphene as an Efficient Buffer for GaN/AlN Epitaxy on a SiO2/Si Substrate: A Joint Experimental and Theoretical Study. **2022**, 12, 11516	0
34	Full-scale exfoliation of InGaN-based light-eMitting diodes via Microcavity-assisted crack propagation by using tensile-stressed Ni layers. **2022**,	0
33	Effect of A-site deficiency on perovskite-type Mn4+-activated La5/3MgTaO6 red phosphor and green luminescence of the Mn2+ occupied six-coordinate site in Mg2LaTaO6. **2023**, 319, 123780	0
32	Effect of Different Light-tip Distances on Shear Bond Strength of Orthodontic Brackets Cured with Light-emitting Diode and High-intensity Light-emitting Diode. **2022**, 23, 775-780	0
31	Microstructure, Photoluminescence and Electrical Properties of SmxGd(1⊠): SrO Hybrid Nanomaterials Synthesized via Facile Coprecipitation Method.	0
30	Grain boundary-driven magnetism in aluminum nitride. **2022**, 121, 242102	0
29	Highly Luminescent Earth-Benign Organometallic Manganese Halide Crystals with Ultrahigh Thermal Stability of Emission from 4 to 623 K. 2205981	0
28	Performance Improvement of InGaN-Based LEDs via a Current-Blocking Region Prepared via Hydrogen Passivation. **2022**, 12, 1733	0
27	Toward High Efficiency at High Temperatures: Recent Progress and Prospects on InGaN-Based Solar Cells. **2022**, 101229	0
26	Electromechanically Coupled III-N Quantum Dots. **2023**, 13, 241	0
25	The Studies on Gallium Nitride-Based Materials: A Bibliometric Analysis. **2023**, 16, 401	1
24	Monolithically Integrating III-Nitride Quantum Structure for Full-Spectrum White LED via Bandgap Engineering Heteroepitaxial Growth. 2200455	2
23	Last 60th salute to the journal. **2023**, 122, 020401	0
22	Green synthesis strategy to construct strong zero-phonon line red emission phosphor Na2SiF6:Mn4+: Photoluminescence properties, thermal stability and application in warm white LEDs. **2023**, 257, 119684	0
21	On the Determination of Elastic Properties of Indium Nitride Nanosheets and Nanotubes by Numerical Simulation. **2023**, 13, 73	0
20	Mechanism, properties and applications of phosphors. **2023**, 33-45	0

19	Self-adjusting Light Source Based on a Dual-Function GaN Light-Emitting Diode. **2022**,	0
18	Topics. **2023**, 157-204	0
17	Synthesis, luminescence and photometric investigation of Sr2B2O5:Dy3+ phosphor for UV-based white LEDs. **2023**, 129,	0
16	Strong Green Photoluminescence in Zr3N4 Thin Films with an Orthorhombic Structure. **2023**, 127, 5561-5566	0
15	Eu2+/Ce3+-doped NaAlSiO4 selective occupation-induced emission structure unit evolution and its luminescence characteristics. **2023**, 139, 113762	0
14	Growth of p-type GaN – The role of oxygen in activation of Mg-doping. **2023**, 5, 100036	0
13	Impact of Local Composition on the Emission Spectra of InGaN Quantum-Dot LEDs. **2023**, 13, 1367	0
12	Intrinsic imperfect and zero thermal quenching property for a novel NaYF4:Eu3+,Tb3+ red-light emitting phosphor for NUV LEDs. **2023**, 940, 168923	0
11	Metal-Halide Perovskite Nanocrystal Superlattice: Self-Assembly and Optical Fingerprints. **2023**, 35,	0
10	Dual fluorescence properties and enhanced thermal stability of SrSi2O2N2:Eu2+ phosphors by coupling with g-C3N4. **2023**, 13, 6442-6452	0
9	Ce3+ in Complex Garnets – Towards Red-Shifted Luminescence and Challenges Therein. **2023**, 546-553	0
8	Impact of nanoscale fluctuations and cap-layer thickness in buried InGaN single quantum wells probed by tip-enhanced Raman scattering. **2023**, 133, 094303	0
7	Prediction of junction temperature of high-voltage white LED based on relative chromaticity parameters. **2023**,	0
6	Blue Transparent OLEDs with High Stability and Transmittance for Modulating Sleep Disorders. **2023**, 10,	0
5	Analyses of ultraviolet-excitable high-efficiency phosphorescent RGB phosphors with various Eu2O3 doping concentrations for fabricating white Light-Emitting diodes. **2023**, 138, 113624	0
4	Mechanism for self-compensation in heavily carbon doped GaN. **2023**, 13, 035026	0
3	Ce3+ Doped Al2O3-YAG Eutectic as an Efficient Light Converter for White LEDs. **2023**, 16, 2701	0
2	Nitrogen vacancies in GaN templates and their critical role on the luminescence efficiency of blue quantum wells. **2023**, 31, 14937	0

1	Application of nano-patterned InGaN fabricated by self-assembled Ni nano-masks in green InGaN/GaN multiple quantum wells. **2023**, 44, 042801	0